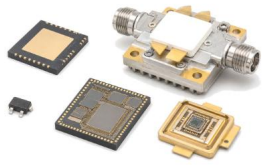
Product catalog

RF ICs, MMICs & Semiconductor Devices

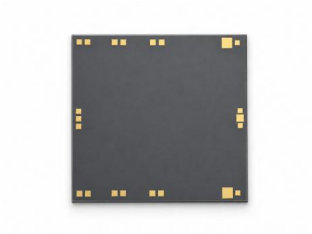
RF semiconductor building blocks for amplification, conversion, switching, detection, control and frequency generation, organized by device function while model-specific performance remains evidence-controlled.



Products: 315

Revision: 27 · Revision date: 2026-11-12

RF MMIC Amplifiers



LCI-PA-11500-18000-PS44p5T

11500–18000 MHz GaN MMIC Power Amplifier Die

A GaN MMIC power amplifier die for 11.5–18 GHz microwave transmit stages. It supports continuous-wave and pulsed operation and integrates DC blocking in both RF signal paths.

Operating frequency: Symbol: f; Minimum: 11500; Maximum: 18000; Value: 11500–18000; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 44; Typical: 44.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 19; Typical: 19.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.4 V; Pin = 25 dBm; τ = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-14000-18000-PS42p5T

14000–18000 MHz GaN MMIC Power Amplifier Die

Saturated output power: 42 dBm (minimum) / 42.5 dBm (typical); Power gain: 22 dB (minimum) / 22.5 dB (typical); Power-added efficiency: 35 % (minimum). Die dimensions: 3 × 2 × 0.1 mm.

Operating frequency: Minimum: 14000; Maximum: 18000; Value: 14000–18000; Unit: MHz

Saturated output power: Minimum: 42; Typical: 42.5; Unit: dBm

Power gain: Minimum: 22; Typical: 22.5; Unit: dB

Power-gain flatness: Typical: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-14200-16800-PS48T

14200–16800 MHz GaN MMIC Power Amplifier Die

pulsed: PSAT: 48 dBm (typical); Power gain: 20 dB (typical); PAE: 35 % (typical). Die dimensions: 3.6 × 5.9 × 0.08 mm.

Operating frequency: Symbol: f; Minimum: 14200; Maximum: 16800; Value: 14200–16800; Unit: MHz

Saturated output power: Symbol: Psat; Typical: 48; Unit: dBm

Power gain: Symbol: Gp; Typical: 20; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.35; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V; Pin = 28 dBm; τ = 100 µs; D = 5%; pulsed

Product details Product datasheet



LCI-PA-14500-17200-PS48T

14500–17200 MHz GaN MMIC Power Amplifier Die

pulsed: PSAT: 48 dBm (typical); Power gain: 20 dB (typical); PAE: 35 % (typical). Die dimensions: 3.6 × 5.9 × 0.08 mm.

Operating frequency: Symbol: f; Minimum: 14500; Maximum: 17200; Value: 14500–17200; Unit: MHz

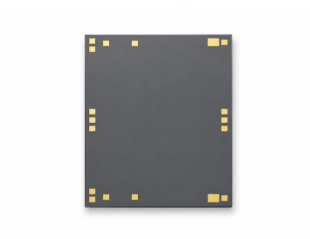
Saturated output power: Symbol: Psat; Typical: 48; Unit: dBm

Power gain: Symbol: Gp; Typical: 20; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.35; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 28 dBm; τ = 100 µs; D = 5%; pulsed

Product details Product datasheet



LCI-PA-13750-14500-PS45MIN

13750–14500 MHz GaN MMIC Power Amplifier Die

pulsed: PSAT: 45 dBm (minimum); Power gain: 20 dB (minimum); PAE: 37 % (minimum) / 38 % (typical). Die dimensions: 2.8 × 3.5 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 13750; Maximum: 14500; Value: 13750–14500; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 45; Unit: dBm

Power gain: Symbol: Gp; Minimum: 20; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±0.3; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -3.08 V; pulsed

Product details Product datasheet



LCI-PA-13750-15250-PS46T

13750–15250 MHz GaN MMIC Power Amplifier Die

Saturated output power: 46 dBm (typical); Power gain: 21 dB (typical); Power-added efficiency: 33 % (typical). Die dimensions: 5 × 6 × 0.08 mm.

Operating frequency: Minimum: 13750; Maximum: 15250; Value: 13750–15250; Unit: MHz

Saturated output power: Typical: 46; Unit: dBm

Power gain: Typical: 21; Unit: dB

Power-gain flatness: Maximum: ±0.3; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -3.05 V; CW

Product details Product datasheet



LCI-PA-8000-12000-PS48p5T

8000–12000 MHz GaN MMIC Power Amplifier Die

Saturated output power: 48 dBm (minimum) / 48.5 dBm (typical); Power gain: 23 dB (minimum) / 23.5 dB (typical); Power-added efficiency: 44 % (typical). Die dimensions: 4 × 5.8 × 0.1 mm.

Operating frequency: Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

Saturated output power: Minimum: 48; Typical: 48.5; Unit: dBm

Power gain: Minimum: 23; Typical: 23.5; Unit: dB

Power-gain flatness: Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V

Product details Product datasheet



LCI-PA-13800-18200-PS47p5T

13800–18200 MHz GaN MMIC Power Amplifier Die

PSAT: 47 dBm (minimum) / 47.5 dBm (typical); Power gain: 21 dB (minimum) / 21.5 dB (typical); PAE: 33 % (typical). Die dimensions: 3.6 × 5.9 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 13800; Maximum: 18200; Value: 13800–18200; Unit: MHz

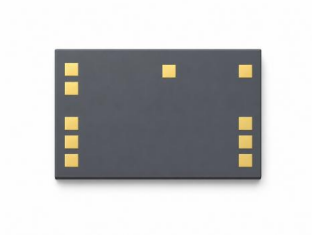
Saturated output power: Symbol: Psat; Minimum: 47; Typical: 47.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 21; Typical: 21.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V

Product details Product datasheet



LCI-PA-14000-18000-PS37p5T

14000–18000 MHz GaN MMIC Power Amplifier Die

PSAT: 37 dBm (minimum) / 37.5 dBm (typical); Power gain: 15 dB (minimum) / 15.5 dB (typical); PAE: 35 % (typical). Die dimensions: 1.5 × 1 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 14000; Maximum: 18000; Value: 14000–18000; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 37; Typical: 37.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 15; Typical: 15.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.4; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-12200-16000-PS46p5T

12200–16000 MHz GaN MMIC Power Amplifier Die

PSAT: 46 dBm (minimum) / 46.5 dBm (typical); Power gain: 19 dB (minimum) / 19.5 dB (typical); PAE: 33 % (typical). Die dimensions: 4.2 × 6.02 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 12200; Maximum: 16000; Value: 12200–16000; Unit: MHz

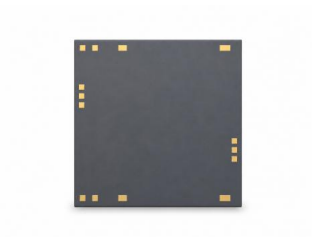
Saturated output power: Symbol: Psat; Minimum: 46; Typical: 46.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 19; Typical: 19.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -3.0 V

Product details Product datasheet



LCI-PA-26000-40000-PS40p5T

26000–40000 MHz GaN MMIC Power Amplifier Die

Power gain: 15 dB (typical); PSAT: 40.5 dBm (typical); PAE: 23 % (typical). Die dimensions: 3.4 × 3.4 × 0.08 mm.

Operating frequency: Symbol: f; Minimum: 26000; Maximum: 40000; Value: 26000–40000; Unit: MHz

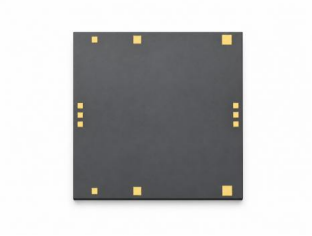
Small-signal gain: Symbol: S21; Typical: 22; Unit: dB

Power gain: Symbol: Gp; Typical: 15; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±0.5; Unit: dB

TA = +25 °C; Vd = +22 V; Id = 0.8 A

Product details Product datasheet



LCI-PA-31000-37000-PS41T

31000–37000 MHz MMIC Power Amplifier Die

PSAT: 41 dBm (typical); PAE: 26 % (typical); Small-signal gain: 21 dB (typical). Die dimensions: 3.6 × 3.6 × 0.08 mm.

Operating frequency: Symbol: f; Minimum: 31000; Maximum: 37000; Value: 31000–37000; Unit: MHz

Small-signal gain: Symbol: S21; Typical: 21; Unit: dB

Small-signal gain flatness: Symbol: ΔS21; Typical: ±1; Unit: dB

Saturated output power: Symbol: Psat; Typical: 41; Unit: dBm

TA = +25 °C; Vd = +22 V; Id = 1 A

Product details Product datasheet



LCI-PA-33000-37000-PS45T

33000–37000 MHz MMIC Power Amplifier Die

PSAT: 45 dBm (typical); PAE: 22 % (typical); Small-signal gain: 23 dB (typical). Die dimensions: 3.6 × 6.2 × 0.08 mm.

Operating frequency: Symbol: f; Minimum: 33000; Maximum: 37000; Value: 33000–37000; Unit: MHz

Small-signal gain: Symbol: S21; Typical: 23; Unit: dB

Small-signal gain flatness: Symbol: ΔS21; Typical: ±1; Unit: dB

Saturated output power: Symbol: Psat; Typical: 45; Unit: dBm

TA = +25 °C; Vd = +28 V; Id = 2.1 A

Product details Product datasheet



LCI-PA-18000-40000-PS40p5T

18000–40000 MHz GaN MMIC Power Amplifier Die

PSAT: 40.5 dBm (typical); PAE: 15 % (typical); Small-signal gain: 21 dB (typical). Die dimensions: 3.4 × 4.2 × 0.05 mm.

Operating frequency: Symbol: f; Minimum: 18000; Maximum: 40000; Value: 18000–40000; Unit: MHz

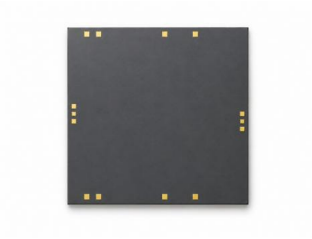
Small-signal gain: Symbol: S21; Typical: 21; Unit: dB

Small-signal gain flatness: Symbol: ΔS21; Typical: ±1; Unit: dB

Saturated output power: Symbol: Psat; Typical: 40.5; Unit: dBm

TA = +25 °C; Vd = +18 V; Id = 2.2 A

Product details Product datasheet



LCI-PA-92000-96000-PS36T

92000–96000 MHz MMIC Power Amplifier Die

PSAT: 36 dBm (typical); PAE: 9 % (typical); Small-signal gain: 19 dB (typical). Die dimensions: 5.1 × 5.1 × 0.05 mm.

Operating frequency: Symbol: f; Minimum: 92000; Maximum: 96000; Value: 92000–96000; Unit: MHz

Small-signal gain: Symbol: S21; Typical: 19; Unit: dB

Small-signal gain flatness: Symbol: ΔS21; Typical: ±1; Unit: dB

Saturated output power: Symbol: Psat; Typical: 36; Unit: dBm

TA = +25 °C; Vd = +18 V; Id = 1.2 A

Product details Product datasheet



LCI-PA-27000-31000-PS43T

27000–31000 MHz Power Amplifier Die

PSAT: 43 dBm (typical); PAE: 28 % (typical); Small-signal gain: 23 dB (typical). Die dimensions: 3.26 × 4.8 × 0.08 mm.

Operating frequency: Symbol: f; Minimum: 27000; Maximum: 31000; Value: 27000–31000; Unit: MHz

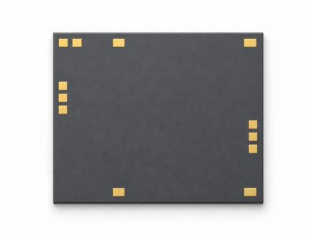
Small-signal gain: Symbol: S21; Typical: 23; Unit: dB

Small-signal gain flatness: Symbol: ΔS21; Typical: ±0.5; Unit: dB

Saturated output power: Symbol: Psat; Typical: 43; Unit: dBm

TA = +25 °C; Vd = +22 V; Id = 0.9 A

Product details Product datasheet



LCI-PA-50000-63000-PS37T

50000–63000 MHz GaN MMIC Power Amplifier Die

PSAT: 37 dBm (typical); PAE: 20 % (typical); Small-signal gain: 18 dB (typical). Die dimensions: 2.9 × 2.4 × 0.05 mm.

Operating frequency: Symbol: f; Minimum: 50000; Maximum: 63000; Value: 50000–63000; Unit: MHz

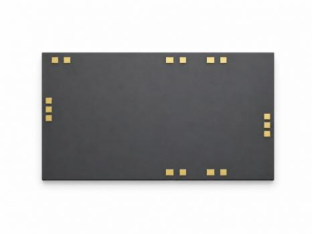
Small-signal gain: Symbol: S21; Typical: 18; Unit: dB

Small-signal gain flatness: Symbol: ΔS21; Typical: ±1.5; Unit: dB

Saturated output power: Symbol: Psat; Typical: 37; Unit: dBm

TA = +25 °C; Vd = +18 V; Id = 0.77 A

Product details Product datasheet



LCI-PA-92000-96000-PS34T

92000–96000 MHz MMIC Power Amplifier Die

PSAT: 34 dBm (typical); PAE: 10 % (typical); Small-signal gain: 19 dB (typical). Die dimensions: 4.5 × 2.6 × 0.05 mm.

Operating frequency: Symbol: f; Minimum: 92000; Maximum: 96000; Value: 92000–96000; Unit: MHz

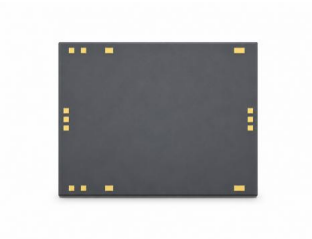
Small-signal gain: Symbol: S21; Typical: 19; Unit: dB

Small-signal gain flatness: Symbol: ΔS21; Typical: ±1; Unit: dB

Saturated output power: Symbol: Psat; Typical: 34; Unit: dBm

TA = +25 °C; Vd = +18 V; Id = 1.2 A

Product details Product datasheet



LCI-PA-18000-26500-PS41T

18000–26500 MHz GaN MMIC Power Amplifier Die

PSAT: 41 dBm (typical); PAE: 26 % (typical); Power gain: 19 dB (typical). Die dimensions: 4.1 × 3.2 × 0.08 mm.

Operating frequency: Symbol: f; Minimum: 18000; Maximum: 26500; Value: 18000–26500; Unit: MHz

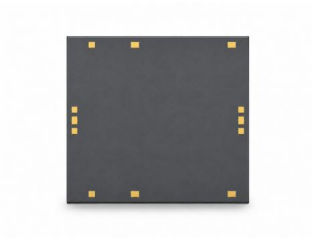
Small-signal gain: Symbol: S21; Typical: 25; Unit: dB

Small-signal gain flatness: Symbol: ΔS21; Typical: ±0.4; Unit: dB

Saturated output power: Symbol: Psat; Typical: 41; Unit: dBm

TA = +25 °C; Vd = +22 V; Id = 0.9 A

Product details Product datasheet



LCI-PA-27000-31000-PS42T

27000–31000 MHz GaN MMIC Power Amplifier Die

PSAT: 42 dBm (typical); PAE: 30 % (typical); Small-signal gain: 23 dB (typical). Die dimensions: 3.26 × 3 × 0.08 mm.

Operating frequency: Symbol: f; Minimum: 27000; Maximum: 31000; Value: 27000–31000; Unit: MHz

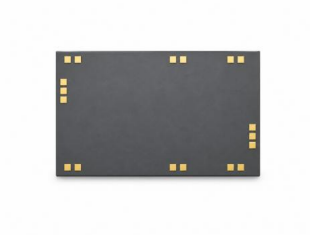
Small-signal gain: Symbol: S21; Typical: 23; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±0.5; Unit: dB

Saturated output power: Symbol: Psat; Typical: 42; Unit: dBm

TA = +25 °C; Vd = +22 V; Id = 0.5 A

Product details Product datasheet



LCI-PA-15000-43000-PS30T

15000–43000 MHz Power Amplifier Die

PSAT: 30 dBm (typical); PAE: 18 % (typical); Small-signal gain: 18 dB (minimum) / 20 dB (typical) / 22 dB (maximum). Die dimensions: 3.94 × 2.48 × 0.07 mm.

Operating frequency: Symbol: f; Minimum: 15000; Maximum: 43000; Value: 15000–43000; Unit: MHz

Small-signal gain: Symbol: S21; Minimum: 18; Typical: 20; Maximum: 22; Unit: dB

Small-signal gain flatness: Symbol: ΔS21; Typical: ±2; Unit: dB

Output power at 1 dB compression: Typical: 29.5; Unit: dBm

TA = +25 °C; Vd = +5 V; Id = 0.9 A

Product details Product datasheet



LCI-PA-92000-96000-PS26p5T

92000–96000 MHz Power Amplifier Die

PSAT: 26.5 dBm (typical); PAE: 12 % (typical) / 13 % (maximum); Small-signal gain: 18 dB (typical). Die dimensions: 3.25 × 1.15 × 0.05 mm.

Operating frequency: Symbol: f; Minimum: 92000; Maximum: 96000; Value: 92000–96000; Unit: MHz

Small-signal gain: Symbol: S21; Typical: 18; Unit: dB

Small-signal gain flatness: Symbol: ΔS21; Typical: ±0.5; Unit: dB

Saturated output power: Symbol: Psat; Typical: 26.5; Unit: dBm

TA = +25 °C; Vd = +18 V; Id = 0.11 A

Product details Product datasheet



LCI-PA-15000-17000-PS45T-PG21T

15000–17000 MHz GaN MMIC Power Amplifier Die

PSAT: 45 dBm (typical); Power gain: 21 dB (typical); PAE: 37 % (typical). Die dimensions: 3.45 × 3.95 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 15000; Maximum: 17000; Value: 15000–17000; Unit: MHz

Saturated output power: Symbol: Psat; Typical: 45; Unit: dBm

Power gain: Symbol: Gp; Typical: 21; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V

Product details Product datasheet



LCI-PA-12700-14500-PS47T

12700–14500 MHz GaN MMIC Power Amplifier Die

pulsed: PSAT: 46.8 dBm (minimum) / 47 dBm (typical); Power gain: 18.8 dB (minimum) / 19 dB (typical); PAE: 37 % (typical). Die dimensions: 3.7 × 5.9 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 12700; Maximum: 14500; Value: 12700–14500; Unit: MHz

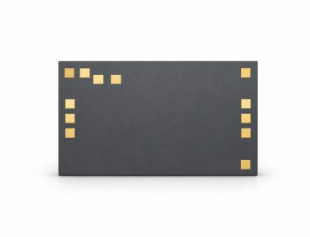
Saturated output power: Symbol: Psat; Minimum: 46.8; Typical: 47; Unit: dBm

Power gain: Symbol: Gp; Minimum: 18.8; Typical: 19; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±0.3; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.96 V; pulsed

Product details Product datasheet



LCI-PA-15000-18000-PS38T

15000–18000 MHz GaN MMIC Power Amplifier Die

pulsed: PSAT: 38 dBm (typical); Power gain: 20 dB (typical); PAE: 40 % (typical). Die dimensions: 2.3 × 1.35 × 0.08 mm.

Operating frequency: Symbol: f; Minimum: 15000; Maximum: 18000; Value: 15000–18000; Unit: MHz

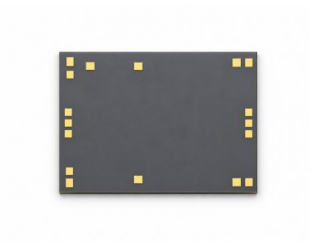
Saturated output power: Symbol: Psat; Typical: 38; Unit: dBm

Power gain: Symbol: Gp; Typical: 20; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.35; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 19 dBm; τ = 100 µs; D = 10%; pulsed

Product details Product datasheet



LCI-PA-13000-15000-PS42T

13000–15000 MHz GaN MMIC Power Amplifier Die

pulsed: PSAT: 42 dBm (typical); Power gain: 21 dB (typical); PAE: 35 % (minimum) / 37 % (typical). Die dimensions: 2.8 × 2 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 13000; Maximum: 15000; Value: 13000–15000; Unit: MHz

Saturated output power: Symbol: Psat; Typical: 42; Unit: dBm

Power gain: Symbol: Gp; Typical: 21; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±0.35; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -3.05 V; pulsed

Product details Product datasheet



LCI-PA-12000-15000-PS47p5T

12000–15000 MHz GaN MMIC Power Amplifier Die

pulsed: PSAT: 47 dBm (minimum) / 47.5 dBm (typical); Power gain: 22 dB (minimum) / 22.5 dB (typical); PAE: 30 % (minimum) / 34 % (typical). Die dimensions: 4.1 × 5 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 12000; Maximum: 15000; Value: 12000–15000; Unit: MHz

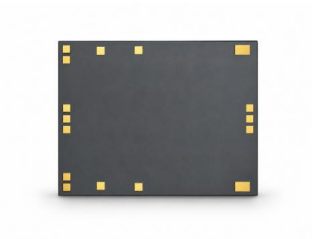
Saturated output power: Symbol: Psat; Minimum: 47; Typical: 47.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 22; Typical: 22.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±0.3; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V; pulsed

Product details Product datasheet



LCI-PA-15000-17000-PS45T-PG24T

15000–17000 MHz GaN MMIC Power Amplifier Die

pulsed: PSAT: 45 dBm (typical); Power gain: 24 dB (typical); PAE: 43 % (typical). Die dimensions: 3.1 × 2.45 × 0.08 mm.

Operating frequency: Symbol: f; Minimum: 15000; Maximum: 17000; Value: 15000–17000; Unit: MHz

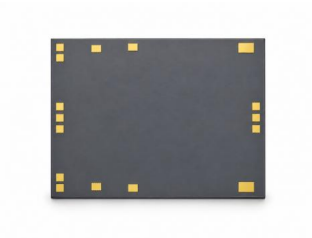
Saturated output power: Symbol: Psat; Typical: 45; Unit: dBm

Power gain: Symbol: Gp; Typical: 24; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±0.3; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.2 V; pulsed

Product details Product datasheet



LCI-PA-14000-18000-PS45T

14000–18000 MHz GaN MMIC Power Amplifier Die

pulsed: PSAT: 45 dBm (typical); Power gain: 24 dB (typical); PAE: 41 % (typical). Die dimensions: 3.1 × 2.45 × 0.08 mm.

Operating frequency: Symbol: f; Minimum: 14000; Maximum: 18000; Value: 14000–18000; Unit: MHz

Saturated output power: Symbol: Psat; Typical: 45; Unit: dBm

Power gain: Symbol: Gp; Typical: 24; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±0.3; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.2 V; pulsed

Product details Product datasheet



LCI-PA-15000-18500-PS48T

15000–18500 MHz GaN MMIC Power Amplifier Die

pulsed: PSAT: 48 dBm (typical); Power gain: 22 dB (typical); PAE: 38 % (typical). Die dimensions: 3.34 × 4.95 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 15000; Maximum: 18500; Value: 15000–18500; Unit: MHz

Saturated output power: Symbol: Psat; Typical: 48; Unit: dBm

Power gain: Symbol: Gp; Typical: 22; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±0.3; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.2 V; pulsed

Product details Product datasheet



LCI-PA-13750-15350-PS48T

13750–15350 MHz GaN MMIC Power Amplifier Die

pulsed: PSAT: 47 dBm (minimum) / 48 dBm (typical); Power gain: 19 dB (minimum) / 20 dB (typical); PAE: 35 % (typical). Die dimensions: 3.7 × 5.9 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 13750; Maximum: 15350; Value: 13750–15350; Unit: MHz

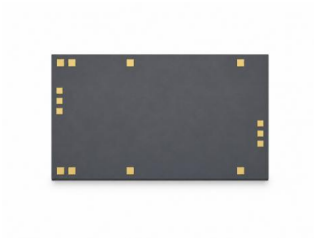
Saturated output power: Symbol: Psat; Minimum: 47; Typical: 48; Unit: dBm

Power gain: Symbol: Gp; Minimum: 19; Typical: 20; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Id = 0.5 A; pulsed

Product details Product datasheet



LCI-PA-34000-64000-PS30T

34000–64000 MHz GaN MMIC Power Amplifier Die

PSAT: 30 dBm (typical); PAE: 17 % (typical); Power gain: 17 dB (typical). Die dimensions: 3.9 × 2.3 × 0.07 mm.

Operating frequency: Symbol: f; Minimum: 34000; Maximum: 64000; Value: 34000–64000; Unit: MHz

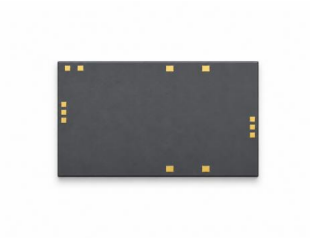
Small-signal gain: Symbol: S21; Typical: 19; Unit: dB

Output power at 1 dB compression: Typical: 27; Unit: dBm

Saturated output power: Symbol: Psat; Typical: 30; Unit: dBm

TA = +25 °C; Vd = +4 V; Id = 0.81 A

Product details Product datasheet



LCI-PA-92000-96000-PS34p5T

92000–96000 MHz MMIC Power Amplifier Die

PSAT: 34.5 dBm (typical); PAE: 14 % (typical); Small-signal gain: 22 dB (typical). Die dimensions: 4.5 × 2.6 × 0.05 mm.

Operating frequency: Symbol: f; Minimum: 92000; Maximum: 96000; Value: 92000–96000; Unit: MHz

Small-signal gain: Symbol: S21; Typical: 22; Unit: dB

Small-signal gain flatness: Symbol: ΔS21; Typical: ±1; Unit: dB

Saturated output power: Symbol: Psat; Typical: 34.5; Unit: dBm

TA = +25 °C; Vd = +15 V; Id = 0.28 A

Product details Product datasheet



LCI-LNA-8000-12000-NF0p7T-SG28T

8000–12000 MHz GaAs MMIC Low-Noise Amplifier Die

Noise figure: 0.7 dB (typical) / 0.75 dB (maximum); Small-signal gain: 26.5 dB (minimum) / 28 dB (typical); Output 1 dB compression power: 10 dBm (typical). Die dimensions: 1.4 × 0.9 × 0.1 mm.

Operating frequency: Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

Output 1 dB compression power: Typical: 10; Unit: dBm

Small-signal gain: Minimum: 26.5; Typical: 28; Unit: dB

Small-signal gain flatness: Typical: ±1.3; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-8000-12000-NF0p7T-SG28T-M

8000–12000 MHz GaAs MMIC Low-Noise Amplifier Die

Noise figure: 0.7 dB (typical) / 0.75 dB (maximum); Small-signal gain: 26.5 dB (minimum) / 28 dB (typical); Output 1 dB compression power: 10 dBm (typical). Die dimensions: 1.4 × 0.9 × 0.1 mm.

Operating frequency: Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

Output 1 dB compression power: Typical: 10; Unit: dBm

Small-signal gain: Minimum: 26.5; Typical: 28; Unit: dB

Small-signal gain flatness: Typical: ±1.3; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-14000-15000-NF1p1T

14000–15000 MHz GaAs MMIC Low-Noise Amplifier Die

Noise figure: 1.1 dB (typical); Small-signal gain: 32 dB (typical); Output 1 dB compression power: 5 dBm (typical). Die dimensions: 1.8 × 1.4 × 0.1 mm.

Operating frequency: Minimum: 14000; Maximum: 15000; Value: 14000–15000; Unit: MHz

Output 1 dB compression power: Typical: 5; Unit: dBm

Small-signal gain: Typical: 32; Unit: dB

Small-signal gain flatness: Typical: ±0.5; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-14000-15000-NF1p1T-M

14000–15000 MHz GaAs MMIC Low-Noise Amplifier Die

Noise figure: 1.1 dB (typical); Small-signal gain: 32 dB (typical); Output 1 dB compression power: 5 dBm (typical). Die dimensions: 1.8 × 1.4 × 0.1 mm.

Operating frequency: Minimum: 14000; Maximum: 15000; Value: 14000–15000; Unit: MHz

Output 1 dB compression power: Typical: 5; Unit: dBm

Small-signal gain: Typical: 32; Unit: dB

Small-signal gain flatness: Typical: ±0.5; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-800-4000-NF0p4T

800–4000 MHz GaAs MMIC Low-Noise Amplifier Die

Noise figure: 0.4 dB (typical); Small-signal gain: 32 dB (typical) (Vd = +5 V); Output 1 dB compression power: 15 dBm (typical) (Vd = +5 V). Die dimensions: 1.8 × 1.7 × 0.1 mm.

Operating frequency: Minimum: 800; Maximum: 4000; Value: 800–4000; Unit: MHz

Output 1 dB compression power: Typical: 15; Value: Vd = +5 V; Unit: dBm

Small-signal gain: Typical: 32; Value: Vd = +5 V; Unit: dB

Small-signal gain flatness: Typical: ±1.5; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-800-4000-NF0p4T-M

800–4000 MHz GaAs MMIC Low-Noise Amplifier Die

Noise figure: 0.4 dB (typical); Small-signal gain: 32 dB (typical) (Vd = +5 V); Output 1 dB compression power: 15 dBm (typical) (Vd = +5 V). Die dimensions: 1.8 × 1.7 × 0.1 mm.

Operating frequency: Minimum: 800; Maximum: 4000; Value: 800–4000; Unit: MHz

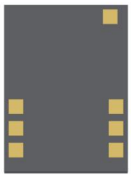
Output 1 dB compression power: Typical: 15; Value: Vd = +5 V; Unit: dBm

Small-signal gain: Typical: 32; Value: Vd = +5 V; Unit: dB

Small-signal gain flatness: Typical: ±1.5; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-30-600-NF0p6T

30–600 MHz GaAs MMIC Low-Noise Amplifier Die

Noise figure: 0.6 dB (typical); Small-signal gain: 32.3 dB (typical); Input VSWR: 1.2 (typical). Die dimensions: 0.85 × 1.15 × 0.1 mm.

Operating frequency: Minimum: 30; Maximum: 600; Value: 30–600; Unit: MHz

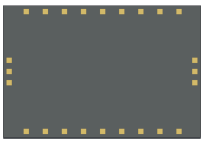
Small-signal gain: Typical: 32.3; Unit: dB

Small-signal gain flatness: Typical: ±0.3; Unit: dB

Input VSWR: Typical: 1.2

TA = +25 °C; Vd = +4 V

Product details Product datasheet



LCI-LNA-75000-110000-NF3p3MAX

75000–110000 MHz GaAs MMIC Low-Noise Amplifier Die

Noise figure: 2.8 dB (typical) (f = 90000 MHz); Noise figure: 3.3 dB (maximum); Small-signal gain: 25 dB (typical) (f = 75000–90000 MHz); Small-signal gain: 22 dB (typical) (f = 90000–110000 MHz). Die dimensions: 2 × 3 × 0.1 mm.

Operating frequency: Minimum: 75000; Maximum: 110000; Value: 75000–110000; Unit: MHz

Small-signal gain: Typical: 25; Unit: dB; Notes: f = 75000–90000 MHz

Small-signal gain: Typical: 22; Unit: dB; Notes: f = 90000–110000 MHz

Input return loss: Typical: 6; Unit: dB

TA = +25 °C; VD1–VD4 = +1 V; VG1–VG4 = 0 V; IDtotal = 0.033 A

Product details Product datasheet



LCI-LNA-17000-22000-NF1p3T

17000–22000 MHz GaAs MMIC Low-Noise Amplifier Die

Noise figure: 1.3 dB (typical); Small-signal gain: 26 dB (typical); Output 1 dB compression power: 4 dBm (typical). Die dimensions: 1.5 × 0.75 × 0.07 mm.

Operating frequency: Minimum: 17000; Maximum: 22000; Value: 17000–22000; Unit: MHz

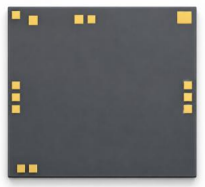
Small-signal gain: Typical: 26; Unit: dB

Small-signal gain flatness: Typical: ±0.5; Unit: dB

Noise figure: Typical: 1.3; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-PA-2700-3900-PS31T

2700–3900 MHz GaAs MMIC Power Amplifier Die

pulsed: PSAT: 30.5 dBm (minimum) / 31 dBm (typical); Power gain: 35.5 dB (minimum) / 36 dB (typical); PAE: 45 % (minimum) / 48 % (typical). Plan-view die dimensions: 2.5 × 2.262 mm.

Operating frequency: Symbol: f; Minimum: 2700; Maximum: 3900; Value: 2700–3900; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 30.5; Typical: 31; Unit: dBm

Power gain: Symbol: Gp; Minimum: 35.5; Typical: 36; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: 1.5; Unit: dB

TA = +25 °C; Vd = +8 V; Vg = -0.8 V; Pin = -5 dBm; τ = 100 µs; D = 10%; pulsed

Product details Product datasheet



LCI-PA-2700-3900-PS34p5T

2700–3900 MHz GaAs MMIC Power Amplifier Die

pulsed: PSAT: 34 dBm (minimum) / 34.5 dBm (typical); Power gain: 29 dB (minimum) / 29.5 dB (typical); PAE: 47 % (minimum) / 49 % (typical). Plan-view die dimensions: 2.2 × 3.092 mm.

Operating frequency: Symbol: f; Minimum: 2700; Maximum: 3900; Value: 2700–3900; Unit: MHz

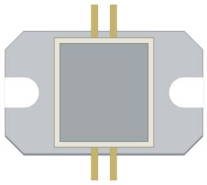
Saturated output power: Symbol: Psat; Minimum: 34; Typical: 34.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 29; Typical: 29.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: 1; Unit: dB

TA = +25 °C; Vd = +8 V; Vg = -0.7 V; Pin = 5 dBm; τ = 100 µs; D = 10%; pulsed

Product details Product datasheet



LCI-PA-200-2200-PS41T

200–2200 MHz Metal-ceramic packaged GaN MMIC power amplifier

Saturated output power: 39.5 dBm (minimum) / 41 dBm (typical); Power gain: 23.5 dB (minimum) / 25 dB (typical); Power-added efficiency: 40 % (minimum) / 50 % (typical).

Operating frequency: Minimum: 200; Maximum: 2200; Value: 200–2200; Unit: MHz

Saturated output power: Minimum: 39.5; Typical: 41; Unit: dBm

Power gain: Minimum: 23.5; Typical: 25; Unit: dB

Power-gain flatness: Maximum: ±1; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V; Pin = +16 dBm

Product details Product datasheet



LCI-LNA-8000-12000-NF0p9T-SG28T

8000–12000 MHz QFN low-noise amplifier IC

Noise figure: 0.9 dB (typical); Small-signal gain: 28 dB (typical); Output 1 dB compression power: 10 dBm (typical). Package dimensions: 2.5 × 2.5 × 0.75 mm.

Operating frequency: Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

Output 1 dB compression power: Typical: 10; Unit: dBm

Small-signal gain: Typical: 28; Unit: dB

Noise figure: Typical: 0.9; Unit: dB

TA = +25 °C; Vd = +5 V; Pin = -35 dBm

Product details Product datasheet



LCI-LNA-8000-12000-NF0p9T-SG28T-M

8000–12000 MHz QFN low-noise amplifier IC

Noise figure: 0.9 dB (typical); Small-signal gain: 28 dB (typical); Output 1 dB compression power: 10 dBm (typical). Package dimensions: 2.5 × 2.5 × 0.75 mm.

Operating frequency: Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

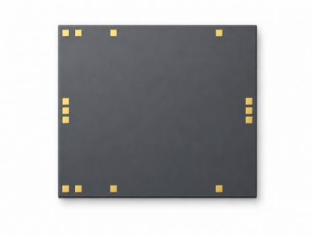
Output 1 dB compression power: Typical: 10; Unit: dBm

Small-signal gain: Typical: 28; Unit: dB

Noise figure: Typical: 0.9; Unit: dB

TA = +25 °C; Vd = +5 V; Pin = -35 dBm

Product details Product datasheet



LCI-PA-6000-18000-PS42T

6000–18000 MHz GaN MMIC Power Amplifier Die

6000–18000 MHz; Saturated output power: 42 dBm (typical); Power gain: 17 dB (typical); Power-added efficiency: 20 % (typical); Die dimensions: 3.9 × 3.4 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 6000; Maximum: 18000; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 41.2; Typical: 42; Unit: dBm

Power gain: Symbol: Gp; Minimum: 16.2; Typical: 17; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±1.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.2 V

Product details Product datasheet



LCI-PA-8000-12000-PS29T

8000–12000 MHz GaN MMIC Power Amplifier Die

8000–12000 MHz; Saturated output power: 29 dBm (typical); Power gain: 14 dB (typical); Power-added efficiency: 15 % (typical); Die dimensions: 1.95 × 1.35 × 0.08 mm.

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 12000; Unit: MHz

Power gain: Symbol: Gp; Minimum: 13; Typical: 14; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±0.5; Unit: dB

Saturated output power: Symbol: Psat; Typical: 29; Unit: dBm

TA = +25 °C; Vd = +28 V

Product details Product datasheet



LCI-PA-4000-8000-PS43p5T

4000–8000 MHz GaN MMIC Power Amplifier Die

4000–8000 MHz; PSAT 43.5 dBm (typical); Power gain 20.5 dB (typical); PAE 40% (typical).

Operating frequency: Symbol: f; Minimum: 4000; Maximum: 8000; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 43; Typical: 43.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 20; Typical: 20.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.2 V

Product details Product datasheet



LCI-PA-2000-6000-PS40p5T

2000–6000 MHz GaN MMIC Power Amplifier Die

2000–6000 MHz; Saturated output power: 40.5 dBm (typical); Power gain: 22.5 dB (typical); Power-added efficiency: 38 % (typical); Die dimensions: 2.8 × 2.1 mm.

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 6000; Unit: MHz

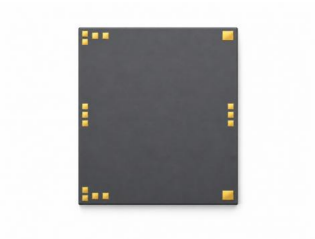
Saturated output power: Symbol: Psat; Minimum: 39.5; Typical: 40.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 21.5; Typical: 22.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.8; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.4 V; Pin = 18 dBm; CW

Product details Product datasheet



LCI-PA-2000-6000-PS45p8T

2000–6000 MHz GaN MMIC Power Amplifier Die

2000–6000 MHz; Saturated output power: 45.8 dBm (typical); Power gain: 18.8 dB (typical); Power-added efficiency: 42 % (typical); Die dimensions: 3.17 × 3.58 mm.

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 6000; Unit: MHz

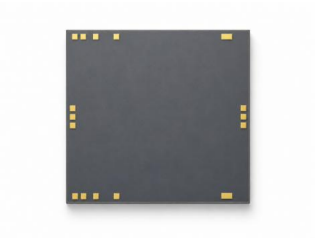
Saturated output power: Symbol: Psat; Minimum: 44.8; Typical: 45.8; Unit: dBm

Power gain: Symbol: Gp; Minimum: 17.8; Typical: 18.8; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: 1.8; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 27 dBm; τ = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-4000-10000-PS45T

4000–10000 MHz GaN MMIC Power Amplifier Die

4000–10000 MHz; Saturated output power: 45 dBm (typical); Power gain: 17 dB (typical); Power-added efficiency: 30 % (typical); Die dimensions: 4.1 × 3.9 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 4000; Maximum: 10000; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 43.8; Typical: 45; Unit: dBm

Power gain: Symbol: Gp; Minimum: 15.8; Typical: 17; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±0.8; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-2500-6200-PS45p5T

2500–6200 MHz GaN MMIC Power Amplifier Die

2500–6200 MHz; PSAT 45.5 dBm (typical); Power gain 17.5 dB (typical); PAE 40% (typical).

Operating frequency: Symbol: f; Minimum: 2500; Maximum: 6200; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 45; Typical: 45.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 17; Typical: 17.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V

Product details Product datasheet



LCI-PA-8500-10500-PS47p8T

8500–10500 MHz GaN MMIC Power Amplifier Die

8500–10500 MHz; Saturated output power: 47.8 dBm (typical); Power gain: 21.8 dB (typical); Power-added efficiency: 47 % (typical); Die dimensions: 4 × 5.1 × 0.08 mm.

Operating frequency: Symbol: f; Minimum: 8500; Maximum: 10500; Unit: MHz

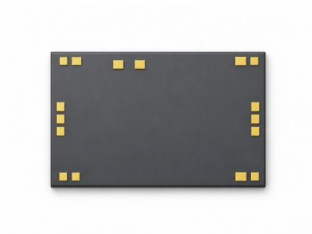
Saturated output power: Symbol: Psat; Minimum: 47; Typical: 47.8; Unit: dBm

Power gain: Symbol: Gp; Minimum: 21; Typical: 21.8; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-8000-12000-PS42T-D

8000–12000 MHz GaN MMIC Power Amplifier Die

8000–12000 MHz; Saturated output power: 42 dBm (typical); Power gain: 22 dB (typical); Power-added efficiency: 43 % (typical); Die dimensions: 3.04 × 1.91 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 12000; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 41.2; Typical: 42; Unit: dBm

Power gain: Symbol: Gp; Minimum: 21.2; Typical: 22; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V

Product details Product datasheet



LCI-PA-2000-18000-PS40T

2000–18000 MHz GaN MMIC Power Amplifier Die

2000–18000 MHz; PSAT 40 dBm (typical); Power gain 12 dB (typical); PAE 20% (typical).

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 18000; Unit: MHz

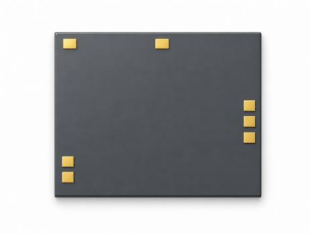
Saturated output power: Symbol: Psat; Typical: 40; Unit: dBm

Power gain: Symbol: Gp; Typical: 12; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±1.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -1.8 V

Product details Product datasheet



LCI-PA-6000-18000-PS33p5T

6000–18000 MHz GaN MMIC Power Amplifier Die

6000–18000 MHz; Saturated output power: 33.5 dBm (typical); Power gain: 12 dB (typical); Power-added efficiency: 20 % (typical); Die dimensions: 2.1 × 1.7 × 0.08 mm.

Operating frequency: Symbol: f; Minimum: 6000; Maximum: 18000; Unit: MHz

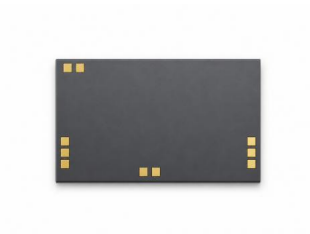
Saturated output power: Symbol: Psat; Minimum: 33; Typical: 33.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 11; Typical: 12; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±1.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2 V

Product details Product datasheet



LCI-PA-2000-18000-PS35T

2000–18000 MHz GaN MMIC Power Amplifier Die

2000–18000 MHz; PSAT 35 dBm (typical); Power gain 7 dB (typical); PAE 20% (typical).

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 18000; Unit: MHz

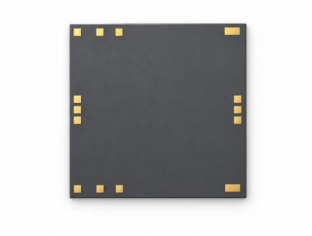
Saturated output power: Symbol: Psat; Typical: 35; Unit: dBm

Power gain: Symbol: Gp; Typical: 7; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±1; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.5 V

Product details Product datasheet



LCI-PA-9200-10400-PS46p2T

9200–10400 MHz GaN MMIC Power Amplifier Die

9200–10400 MHz; Saturated output power: 46.2 dBm (typical); Power gain: 24.2 dB (typical); Power-added efficiency: 50 % (typical); Die dimensions: 3 × 3.03 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 9200; Maximum: 10400; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 46; Typical: 46.2; Maximum: 46.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 24; Typical: 24.2; Maximum: 24.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.3; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-7500-10500-PS49T

7500–10500 MHz GaN MMIC Power Amplifier Die

7500–10500 MHz; Saturated output power: 49 dBm (typical); Power gain: 25 dB (typical); Power-added efficiency: 40 % (typical); Die dimensions: 3.7 × 6 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 7500; Maximum: 10500; Unit: MHz

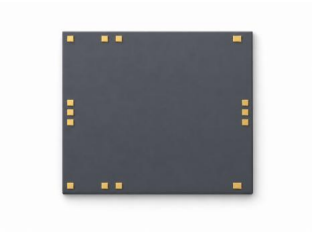
Saturated output power: Symbol: Psat; Minimum: 48.6; Typical: 49; Unit: dBm

Power gain: Symbol: Gp; Minimum: 24.6; Typical: 25; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-7000-13000-PS45T

7000–13000 MHz GaN MMIC Power Amplifier Die

7000–13000 MHz; Saturated output power: 45 dBm (typical); Power gain: 22 dB (typical); Power-added efficiency: 40 % (typical); Die dimensions: 3.5 × 3.2 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 7000; Maximum: 13000; Unit: MHz

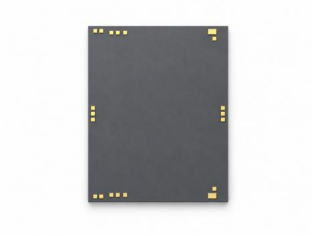
Saturated output power: Symbol: Psat; Minimum: 44; Typical: 45; Unit: dBm

Power gain: Symbol: Gp; Minimum: 21; Typical: 22; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-6000-18000-PS45T

6000–18000 MHz GaN MMIC Power Amplifier Die

6000–18000 MHz; Saturated output power: 45 dBm (typical); Power gain: 20 dB (typical); Power-added efficiency: 23 % (typical); Die dimensions: 4.52 × 5.82 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 6000; Maximum: 18000; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 44.5; Typical: 45; Unit: dBm

Power gain: Symbol: Gp; Minimum: 19.5; Typical: 20; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±1; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.2 V

Product details Product datasheet



LCI-PA-5000-6000-PS49p5T

5000–6000 MHz GaN MMIC Power Amplifier Die

5000–6000 MHz; Saturated output power: 49.5 dBm (typical); Power gain: 26.5 dB (typical); Power-added efficiency: 50 % (typical); Die dimensions: 3.5 × 5.8 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 5000; Maximum: 6000; Unit: MHz

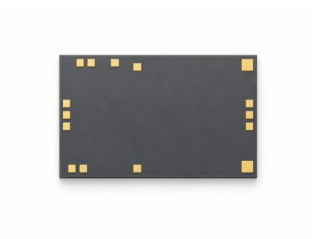
Saturated output power: Symbol: Psat; Minimum: 49; Typical: 49.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 26; Typical: 26.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.2; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V

Product details Product datasheet



LCI-PA-6000-18000-PS40T

6000–18000 MHz GaN MMIC Power Amplifier Die

6000–18000 MHz; Saturated output power: 40 dBm (typical); Power gain: 19 dB (typical); Power-added efficiency: 23 % (typical); Die dimensions: 3 × 1.8 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 6000; Maximum: 18000; Unit: MHz

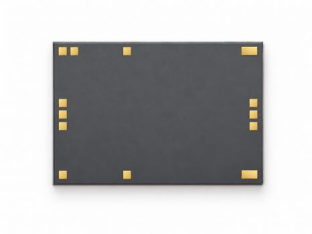
Saturated output power: Symbol: Psat; Minimum: 39; Typical: 40; Unit: dBm

Power gain: Symbol: Gp; Minimum: 18; Typical: 19; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.8; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.2 V; Pin = 21 dBm; τ = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-10000-18000-PS41T

10000–18000 MHz GaN MMIC Power Amplifier Die

10000–18000 MHz; Saturated output power: 41 dBm (typical); Power gain: 19 dB (typical); Power-added efficiency: 30 % (typical); Die dimensions: 3.2 × 2.25 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 10000; Maximum: 18000; Unit: MHz

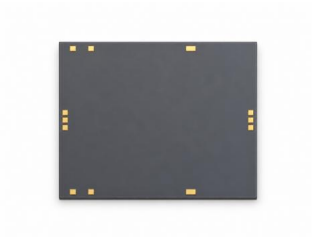
Saturated output power: Symbol: Psat; Minimum: 40.9; Typical: 41; Unit: dBm

Power gain: Symbol: Gp; Minimum: 18.9; Typical: 19; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-950-1250-PS47p5T

950–1250 MHz GaN MMIC Power Amplifier Die

950–1250 MHz; Saturated output power: 47.5 dBm (typical); Power gain: 22.5 dB (typical); Power-added efficiency: 60 % (typical); Die dimensions: 4.35 × 3.43 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 950; Maximum: 1250; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 47; Typical: 47.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 22; Typical: 22.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.3; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V

Product details Product datasheet



LCI-PA-5000-6000-PS47p5T

5000–6000 MHz GaN MMIC Power Amplifier Die

5000–6000 MHz; Saturated output power: 47.5 dBm (typical); Power gain: 24.5 dB (typical); Power-added efficiency: 53 % (typical); Die dimensions: 3.1 × 3.5 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 5000; Maximum: 6000; Unit: MHz

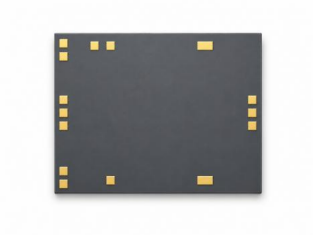
Saturated output power: Symbol: Psat; Minimum: 47; Typical: 47.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 24; Typical: 24.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.4; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-8000-12000-PS43p5T

8000–12000 MHz GaN MMIC Power Amplifier Die

8000–12000 MHz; Saturated output power: 43.5 dBm (typical); Power gain: 22.5 dB (typical); Power-added efficiency: 45 % (typical); Die dimensions: 2.7 × 2.08 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 12000; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 43; Typical: 43.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 22; Typical: 22.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V

Product details Product datasheet



LCI-PA-8000-12000-PS39T-D

8000–12000 MHz GaN MMIC Power Amplifier Die

8000–12000 MHz; Saturated output power: 39 dBm (typical); Power gain: 18 dB (typical); Power-added efficiency: 43 % (typical); Die dimensions: 2.3 × 1.15 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 12000; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 38; Typical: 39; Unit: dBm

Power gain: Symbol: Gp; Minimum: 17; Typical: 18; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.7; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-8500-10500-PS52T

8500–10500 MHz GaN MMIC Power Amplifier Die

8500–10500 MHz; Saturated output power: 52 dBm (typical); Power gain: 24 dB (typical); Power-added efficiency: 45 % (typical); Die dimensions: 3.9 × 6.5 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 8500; Maximum: 10500; Unit: MHz

Saturated output power: Symbol: Psat; Typical: 52; Unit: dBm

Power gain: Symbol: Gp; Typical: 24; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +48 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-4000-8000-PS47p5T

4000–8000 MHz GaN MMIC Power Amplifier Die

4000–8000 MHz; PSAT 47.5 dBm (typical); Power gain 17.5 dB (typical); PAE 40% (typical).

Operating frequency: Symbol: f; Minimum: 4000; Maximum: 8000; Unit: MHz

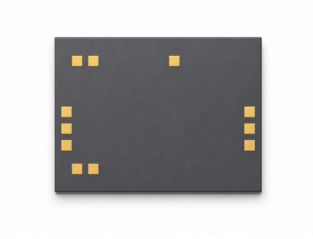
Saturated output power: Symbol: Psat; Minimum: 47; Typical: 47.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 17; Typical: 17.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.8; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-4000-8000-PS37T

4000–8000 MHz GaN MMIC Power Amplifier Die

4000–8000 MHz; PSAT 37 dBm (typical); Power gain 20 dB (typical); PAE 35% (typical).

Operating frequency: Symbol: f; Minimum: 4000; Maximum: 8000; Unit: MHz

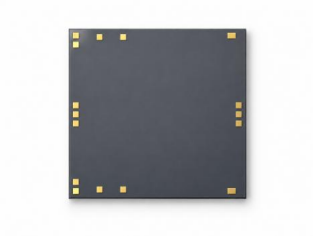
Saturated output power: Symbol: Psat; Minimum: 36.5; Typical: 37; Unit: dBm

Power gain: Symbol: Gp; Minimum: 19.5; Typical: 20; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.4 V

Product details Product datasheet



LCI-PA-8000-12000-PS47T

8000–12000 MHz GaN MMIC Power Amplifier Die

8000–12000 MHz; Saturated output power: 47 dBm (typical); Power gain: 25 dB (typical); Power-added efficiency: 45 % (typical); Die dimensions: 3.5 × 3.6 × 0.1 mm. RF test conditions: Vd = +28 V; Vg = -2.6 V.

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 12000; Unit: MHz

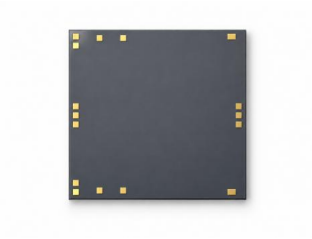
Saturated output power: Symbol: Psat; Minimum: 46.5; Typical: 47; Unit: dBm

Power gain: Symbol: Gp; Minimum: 24.5; Typical: 25; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-8000-12000-PS47T-B

8000–12000 MHz GaN MMIC Power Amplifier Die

8000–12000 MHz; Saturated output power: 47 dBm (typical); Power gain: 25 dB (typical); Power-added efficiency: 45 % (typical); Die dimensions: 3.5 × 3.6 × 0.1 mm. RF test conditions: Vd = +28 V; Vg = -1.8 V.

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 12000; Unit: MHz

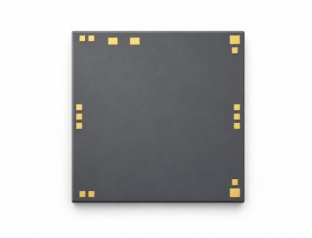
Saturated output power: Symbol: Psat; Minimum: 46.5; Typical: 47; Unit: dBm

Power gain: Symbol: Gp; Minimum: 24.5; Typical: 25; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -1.8 V

Product details Product datasheet



LCI-PA-3600-5000-PS44p5T

3600–5000 MHz GaN MMIC Power Amplifier Die

3600–5000 MHz; PSAT 44.5 dBm (typical); Power gain 23.5 dB (typical); PAE 43% (typical); τ = 100 µs; D = 10%.

Operating frequency: Symbol: f; Minimum: 3600; Maximum: 5000; Unit: MHz

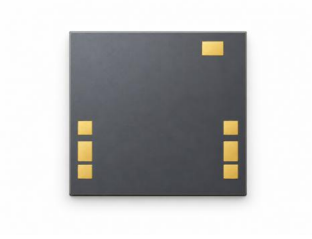
Saturated output power: Symbol: Psat; Minimum: 44; Typical: 44.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 23; Typical: 23.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: 1; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 21 dBm; τ = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-5000-13000-PS25T

5000–13000 MHz GaN MMIC Power Amplifier Die

5000–13000 MHz; Saturated output power: 25 dBm (typical); Power gain: 10 dB (typical); Die dimensions: 1.3 × 1.25 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 5000; Maximum: 13000; Unit: MHz

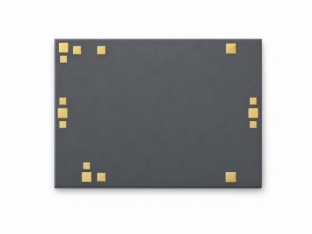
Saturated output power: Symbol: Psat; Typical: 25; Unit: dBm

Power gain: Symbol: Gp; Typical: 10; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Pin = 15 dBm; °CW

Product details Product datasheet



LCI-PA-5000-13000-PS42T

5000–13000 MHz GaN MMIC Power Amplifier Die

5000–13000 MHz; Saturated output power: 42 dBm (typical); Power gain: 20 dB (typical); Power-added efficiency: 35 % (typical); Die dimensions: 3.1 × 2.26 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 5000; Maximum: 13000; Unit: MHz

Saturated output power: Symbol: Psat; Typical: 42; Unit: dBm

Power gain: Symbol: Gp; Typical: 20; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-4200-7000-PS42T

4200–7000 MHz GaN MMIC Power Amplifier Die

4200–7000 MHz; PSAT 42 dBm (typical); Power gain 22 dB (typical); PAE 45% (typical); τ = 100 µs; D = 10%.

Operating frequency: Symbol: f; Minimum: 4200; Maximum: 7000; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 41.8; Typical: 42; Unit: dBm

Power gain: Symbol: Gp; Minimum: 21.8; Typical: 22; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 20 dBm; τ = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-2000-6000-PS45p5T

2000–6000 MHz GaN MMIC Power Amplifier Die

2000–6000 MHz; PSAT 45.5 dBm (typical); Power gain 20.5 dB (typical); PAE 35% (typical); CW; Vd = +24 V.

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 6000; Unit: MHz

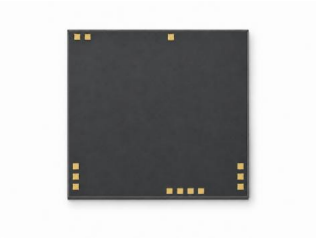
Saturated output power: Symbol: Psat; Minimum: 45; Typical: 45.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 20; Typical: 20.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: 1.5; Unit: dB

TA = +25 °C; Vd = +24 V; Vg = -2.4 V; Pin = 25 dBm; CW

Product details Product datasheet



LCI-PA-200-2200-PS41p5T

200–2200 MHz GaN MMIC Power Amplifier Die

GaN-on-SiC power amplifier die for 200–2200 MHz, with 41.5 dBm typical saturated output, 25.5 dB typical power gain and a 3.00 × 3.00 × 0.10 mm outline.

Operating frequency: Symbol: f; Minimum: 200; Maximum: 2200; Unit: MHz

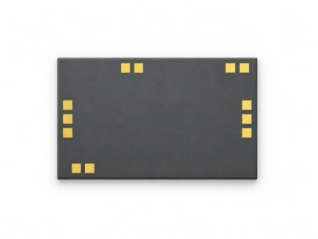
Saturated output power: Symbol: Psat; Minimum: 41.0; Typical: 41.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 25.0; Typical: 25.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±1.0; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = −2.6 V

Product details Product datasheet



LCI-PA-3400-5600-PS40T

3400–5600 MHz GaN MMIC Power Amplifier Die

3400–5600 MHz; PSAT 40 dBm (typical); Power gain 17 dB (typical); PAE 46% (typical); CW.

Operating frequency: Symbol: f; Minimum: 3400; Maximum: 5600; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 39; Typical: 40; Unit: dBm

Power gain: Symbol: Gp; Minimum: 16; Typical: 17; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: 1; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 23 dBm; CW

Product details Product datasheet



LCI-PA-5800-6800-PS47T

5800–6800 MHz GaN MMIC Power Amplifier Die

5800–6800 MHz; Saturated output power: 47 dBm (typical); Power gain: 21 dB (typical); Power-added efficiency: 46 % (typical); Die dimensions: 3.5 × 5.5 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 5800; Maximum: 6800; Unit: MHz

Saturated output power: Symbol: Psat; Typical: 47; Unit: dBm

Power gain: Symbol: Gp; Typical: 21; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-2700-3500-PS45p5T-D

2700–3500 MHz GaN MMIC Power Amplifier Die

2700–3500 MHz; PSAT 45.5 dBm (typical); Power gain 25.5 dB (typical); PAE 58% (typical); CW.

Operating frequency: Symbol: f; Minimum: 2700; Maximum: 3500; Unit: MHz

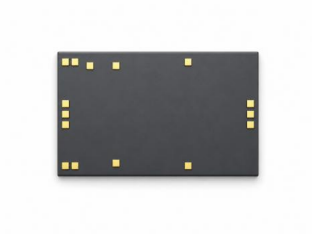
Saturated output power: Symbol: Psat; Minimum: 45; Typical: 45.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 25; Typical: 25.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: 1; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 20 dBm; CW

Product details Product datasheet



LCI-PA-6700-7400-PS41T

6700–7400 MHz GaN MMIC Power Amplifier Die

6700–7400 MHz; Saturated output power: 41 dBm (typical); Power gain: 22 dB (typical); Power-added efficiency: 55 % (typical); Die dimensions: 3.2 × 2 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 6700; Maximum: 7400; Unit: MHz

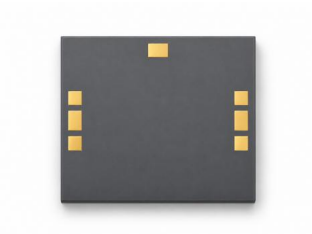
Saturated output power: Symbol: Psat; Typical: 41; Unit: dBm

Power gain: Symbol: Gp; Typical: 22; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-6000-18000-PS27T

6000–18000 MHz GaN MMIC Power Amplifier Die

6000–18000 MHz; Saturated output power: 27 dBm (typical); Power gain: 9 dB (typical); Die dimensions: 1.5 × 1.3 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 6000; Maximum: 18000; Unit: MHz

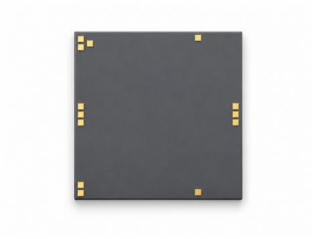
Saturated output power: Symbol: Psat; Minimum: 26; Typical: 27; Maximum: 29; Unit: dBm

Power gain: Symbol: Gp; Minimum: 8; Typical: 9; Maximum: 11; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±1.5; Unit: dB

TA = +25 °C; Vd = +28 V; Pin = 18 dBm; °CW

Product details Product datasheet



LCI-PA-2000-8000-PS42T

2000–8000 MHz GaN MMIC Power Amplifier Die

2000–8000 MHz; PSAT 42 dBm (typical); Power gain 15 dB (typical); PAE 30% (typical).

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 8000; Unit: MHz

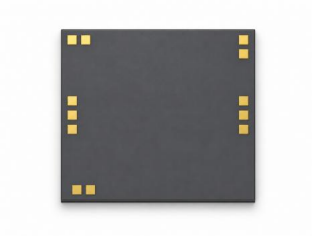
Saturated output power: Symbol: Psat; Minimum: 41; Typical: 42; Unit: dBm

Power gain: Symbol: Gp; Minimum: 14; Typical: 15; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±1.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.2 V

Product details Product datasheet



LCI-PA-2500-3700-PS41p5T

2500–3700 MHz GaN MMIC Power Amplifier Die

2500–3700 MHz; PSAT 41.5 dBm (typical); Power gain 22.5 dB (typical); PAE 50% (typical); τ = 100 µs; D = 10%.

Operating frequency: Symbol: f; Minimum: 2500; Maximum: 3700; Unit: MHz

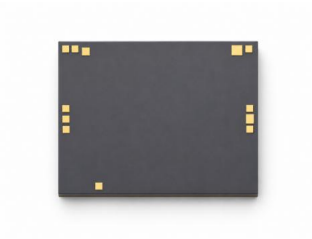
Saturated output power: Symbol: Psat; Minimum: 41; Typical: 41.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 22; Typical: 22.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: 1; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 19 dBm; τ = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-2600-3300-PS45p5T

2600–3300 MHz GaN MMIC Power Amplifier Die

2600–3300 MHz; PSAT 45.5 dBm (typical); Power gain 25.5 dB (typical); PAE 60% (typical); τ = 100 µs; D = 10%.

Operating frequency: Symbol: f; Minimum: 2600; Maximum: 3300; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 45; Typical: 45.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 25; Typical: 25.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: 1; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 20 dBm; τ = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-2400-3800-PS46p5T

2400–3800 MHz GaN MMIC Power Amplifier Die

2400–3800 MHz; PSAT 46.5 dBm (typical); Power gain 27.5 dB (typical); PAE 56% (typical); τ = 100 µs; D = 10%.

Operating frequency: Symbol: f; Minimum: 2400; Maximum: 3800; Unit: MHz

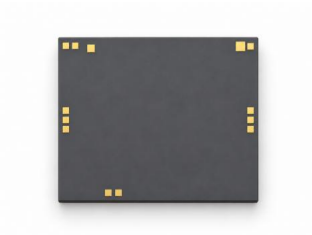
Saturated output power: Symbol: Psat; Minimum: 46; Typical: 46.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 27; Typical: 27.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: 1; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 19 dBm; τ = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-2500-4000-PS47T

2500–4000 MHz GaN MMIC Power Amplifier Die

2500–4000 MHz; PSAT 47 dBm (typical); Power gain 26 dB (typical); PAE 52% (typical); τ = 100 µs; D = 10%.

Operating frequency: Symbol: f; Minimum: 2500; Maximum: 4000; Unit: MHz

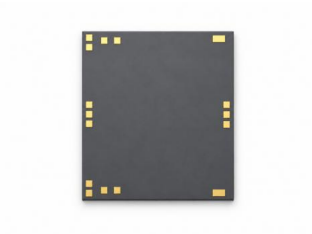
Saturated output power: Symbol: Psat; Minimum: 46.2; Typical: 47; Unit: dBm

Power gain: Symbol: Gp; Minimum: 25.2; Typical: 26; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.3 V; Pin = 21 dBm; τ = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-8000-9400-PS45T

8000–9400 MHz GaN MMIC Power Amplifier Die

8000–9400 MHz; Saturated output power: 45 dBm (typical); Power gain: 31 dB (typical); Power-added efficiency: 52 % (typical); Die dimensions: 3 × 3.2 × 0.1 mm. RF test conditions: Vd = +28 V; Vg = -2.8 V.

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 9400; Unit: MHz

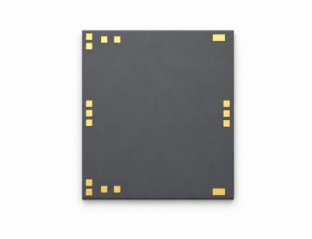
Saturated output power: Symbol: Psat; Typical: 45; Unit: dBm

Power gain: Symbol: Gp; Typical: 31; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V

Product details Product datasheet



LCI-PA-8000-9400-PS45T-A

8000–9400 MHz GaN MMIC Power Amplifier Die

8000–9400 MHz; Saturated output power: 45 dBm (typical); Power gain: 31 dB (typical); Power-added efficiency: 52 % (typical); Die dimensions: 3 × 3.2 × 0.1 mm. RF test conditions: Vd = +28 V; Vg = -1.8 V.

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 9400; Unit: MHz

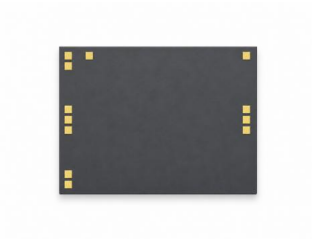
Saturated output power: Symbol: Psat; Typical: 45; Unit: dBm

Power gain: Symbol: Gp; Typical: 31; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -1.8 V

Product details Product datasheet



LCI-PA-1200-1600-PS43p5T

1200–1600 MHz GaN MMIC Power Amplifier Die

1200–1600 MHz; Saturated output power: 43.5 dBm (typical); Power gain: 17 dB (typical); Power-added efficiency: 60 % (typical); Die dimensions: 2.7 × 2 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 1200; Maximum: 1600; Unit: MHz

Saturated output power: Symbol: Psat; Typical: 43.5; Unit: dBm

Power gain: Symbol: Gp; Typical: 17; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V

Product details Product datasheet



LCI-PA-8000-18000-PS46p5T

8000–18000 MHz GaN MMIC Power Amplifier Die

8000–18000 MHz; Saturated output power: 46.5 dBm (typical); Power gain: 18 dB (typical); Power-added efficiency: 28 % (typical); Die dimensions: 4 × 5.6 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 18000; Unit: MHz

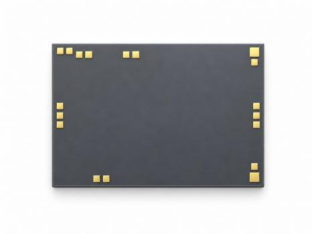
Saturated output power: Symbol: Psat; Minimum: 46; Typical: 46.5; Maximum: 47.5; Unit: dBm

Power gain: Symbol: Gp; Typical: 18; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±1; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.2 V

Product details Product datasheet



LCI-PA-4400-6500-PS44T

4400–6500 MHz GaN MMIC Power Amplifier Die

4400–6500 MHz; Saturated output power: 44 dBm (typical); Power gain: 27 dB (typical); Power-added efficiency: 47 % (typical); Die dimensions: 3.51 × 2.44 mm.

Operating frequency: Symbol: f; Minimum: 4400; Maximum: 6500; Unit: MHz

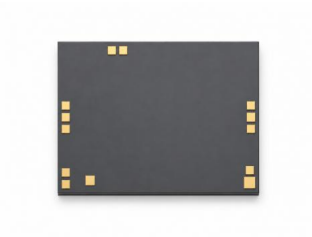
Saturated output power: Symbol: Psat; Minimum: 43.5; Typical: 44; Unit: dBm

Power gain: Symbol: Gp; Minimum: 26.5; Typical: 27; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: 1; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 17 dBm; τ = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-2700-3500-PS43p5T

2700–3500 MHz GaN MMIC Power Amplifier Die

2700–3500 MHz; PSAT 43.5 dBm (typical); Power gain 26.5 dB (typical); PAE 61% (typical); τ = 100 µs; D = 10%.

Operating frequency: Symbol: f; Minimum: 2700; Maximum: 3500; Unit: MHz

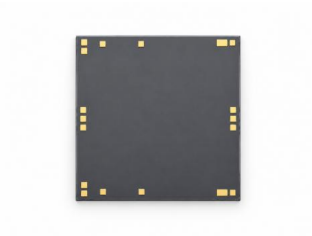
Saturated output power: Symbol: Psat; Minimum: 43; Typical: 43.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 26; Typical: 26.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: 0.6; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 17 dBm; τ = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-10800-13000-PS45T

10800–13000 MHz GaN MMIC Power Amplifier Die

10800–13000 MHz; Saturated output power: 45 dBm (typical); Power gain: 21 dB (typical); Power-added efficiency: 38 % (typical); Die dimensions: 3.4 × 3.52 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 10800; Maximum: 13000; Unit: MHz

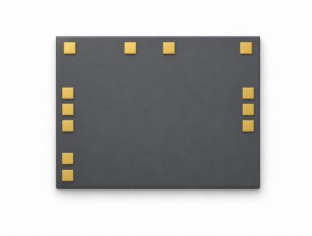
Saturated output power: Symbol: Psat; Typical: 45; Unit: dBm

Power gain: Symbol: Gp; Typical: 21; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±0.3; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V

Product details Product datasheet



LCI-PA-9000-11000-PS37T

9000–11000 MHz GaN MMIC Power Amplifier Die

9000–11000 MHz; Saturated output power: 37 dBm (typical); Power gain: 22 dB (typical); Power-added efficiency: 38 % (typical); Die dimensions: 2.04 × 1.54 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 9000; Maximum: 11000; Unit: MHz

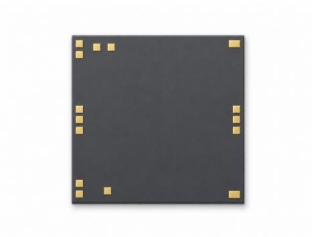
Saturated output power: Symbol: Psat; Typical: 37; Unit: dBm

Power gain: Symbol: Gp; Typical: 22; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±0.2; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V

Product details Product datasheet



LCI-PA-8000-8400-PS45T

8000–8400 MHz GaN MMIC Power Amplifier Die

8000–8400 MHz; Saturated output power: 45 dBm (typical); Power gain: 23 dB (typical); Power-added efficiency: 55 % (typical); Die dimensions: 2.9 × 2.8 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 8400; Unit: MHz

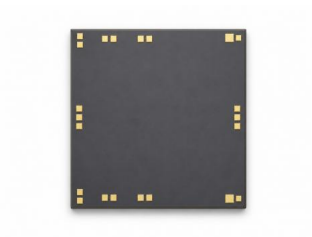
Saturated output power: Symbol: Psat; Typical: 45; Unit: dBm

Power gain: Symbol: Gp; Typical: 23; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -3 V

Product details Product datasheet



LCI-PA-3700-5000-PS45p2T

3700–5000 MHz GaN MMIC Power Amplifier Die

3700–5000 MHz; PSAT 45.2 dBm (typical); Power gain 27 dB (typical); PAE 48% (typical); τ = 100 µs; D = 10%.

Operating frequency: Symbol: f; Minimum: 3700; Maximum: 5000; Unit: MHz

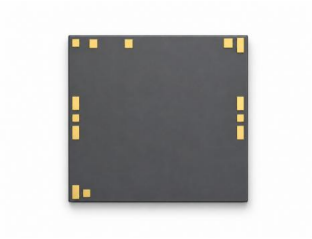
Saturated output power: Symbol: Psat; Minimum: 45; Typical: 45.2; Unit: dBm

Power gain: Symbol: Gp; Minimum: 26.8; Typical: 27; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: 0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 18 dBm; τ = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-2000-6000-PS43T-D

2000–6000 MHz GaN MMIC Power Amplifier Die

2000–6000 MHz; Saturated output power: 43 dBm (typical); Power gain: 26.5 dB (typical); Power-added efficiency: 50 % (typical); Die dimensions: 3.1 × 2.9 mm.

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 6000; Unit: MHz

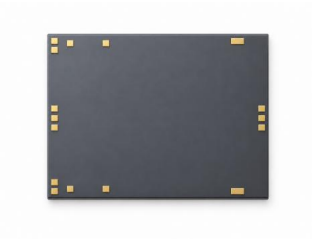
Saturated output power: Symbol: Psat; Minimum: 42.5; Typical: 43; Unit: dBm

Power gain: Symbol: Gp; Minimum: 25.5; Typical: 26.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: 0.6; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.4 V; Pin = 17 dBm; τ = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-6000-18000-PS44T

6000–18000 MHz GaN MMIC Power Amplifier Die

6000–18000 MHz; Saturated output power: 44 dBm (typical); Power gain: 20 dB (typical); Power-added efficiency: 30 % (typical); Die dimensions: 4 × 3.3 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 6000; Maximum: 18000; Unit: MHz

Saturated output power: Symbol: Psat; Typical: 44; Unit: dBm

Power gain: Symbol: Gp; Typical: 20; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.2 V

Product details Product datasheet



LCI-PA-8000-18000-PS44T

8000–18000 MHz GaN MMIC Power Amplifier Die

8000–18000 MHz; Saturated output power: 44 dBm (typical); Power gain: 19 dB (typical); Power-added efficiency: 30 % (typical); Die dimensions: 3.5 × 4 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 18000; Unit: MHz

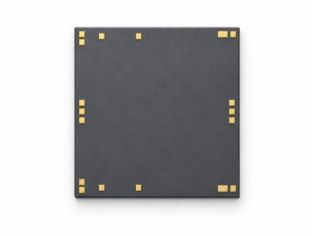
Saturated output power: Symbol: Psat; Typical: 44; Unit: dBm

Power gain: Symbol: Gp; Typical: 19; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.2 V

Product details Product datasheet



LCI-PA-10000-13000-PS45T

10000–13000 MHz GaN MMIC Power Amplifier Die

10000–13000 MHz; Saturated output power: 45 dBm (typical); Power gain: 20 dB (typical); Power-added efficiency: 40 % (typical); Die dimensions: 3.3 × 3.5 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 10000; Maximum: 13000; Unit: MHz

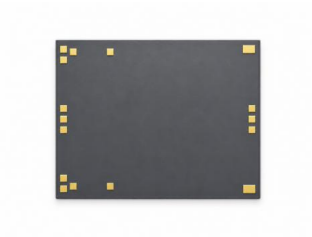
Saturated output power: Symbol: Psat; Typical: 45; Unit: dBm

Power gain: Symbol: Gp; Typical: 20; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±0.3; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-8000-18000-PS43p5T

8000–18000 MHz GaN MMIC Power Amplifier Die

8000–18000 MHz; Saturated output power: 43.5 dBm (typical); Power gain: 19.5 dB (typical); Power-added efficiency: 30 % (typical); Die dimensions: 3.2 × 2.5 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 18000; Unit: MHz

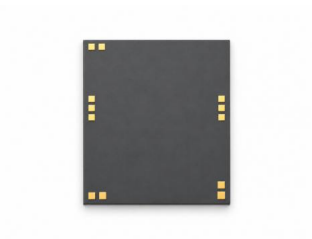
Saturated output power: Symbol: Psat; Typical: 43.5; Unit: dBm

Power gain: Symbol: Gp; Typical: 19.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.4 V

Product details Product datasheet



LCI-PA-2000-2800-PS41T

2000–2800 MHz GaN MMIC Power Amplifier Die

2000–2800 MHz; Saturated output power: 41 dBm (typical); Power gain: 24 dB (typical); Power-added efficiency: 56 % (typical); Die dimensions: 2.4 × 2.7 mm.

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 2800; Unit: MHz

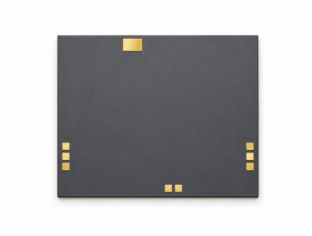
Saturated output power: Symbol: Psat; Minimum: 40.7; Typical: 41; Unit: dBm

Power gain: Symbol: Gp; Minimum: 23.7; Typical: 24; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: 1; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V; Pin = 17 dBm; τ = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-300-6000-PS40p8T

300–6000 MHz GaN MMIC Power Amplifier Die

300–6000 MHz; Saturated output power: 40.8 dBm (typical); Power gain: 12.8 dB (typical); Power-added efficiency: 40 % (typical); Die dimensions: 2.95 × 2.4 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 300; Maximum: 6000; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 40; Typical: 40.8; Maximum: 41.6; Unit: dBm

Power gain: Symbol: Gp; Minimum: 12; Typical: 12.8; Maximum: 13.6; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±0.8; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.4 V

Product details Product datasheet



LCI-PA-2000-18500-PS43T

2000–18500 MHz GaN MMIC Power Amplifier Die

2000–18500 MHz; PSAT 43 dBm (typical); Power gain 13 dB (typical); PAE 20% (typical).

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 18500; Unit: MHz

Saturated output power: Symbol: Psat; Typical: 43; Unit: dBm

Power gain: Symbol: Gp; Typical: 13; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±1; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2 V

Product details Product datasheet



LCI-PA-1950-4050-PS46p5T

1950–4050 MHz GaN MMIC Power Amplifier Die

1950–4050 MHz; Saturated output power: 46.5 dBm (typical); Power gain: 24.5 dB (typical); Power-added efficiency: 52 % (typical); Die dimensions: 3.56 × 3.78 mm.

Operating frequency: Symbol: f; Minimum: 1950; Maximum: 4050; Unit: MHz

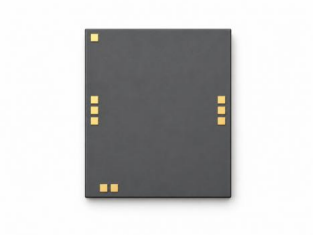
Saturated output power: Symbol: Psat; Minimum: 46; Typical: 46.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 24; Typical: 24.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V; Pin = 22 dBm; τ = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-300-6000-PS30T

300–6000 MHz GaN MMIC Power Amplifier Die

300–6000 MHz; Saturated output power: 30 dBm (typical); Power gain: 15 dB (typical); Power-added efficiency: 15 % (typical); Die dimensions: 2.15 × 2.46 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 300; Maximum: 6000; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 28; Typical: 30; Maximum: 32.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 13; Typical: 15; Maximum: 17.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±2.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-2700-3900-PS48T

2700–3900 MHz GaN MMIC Power Amplifier Die

2700–3900 MHz; PSAT 48 dBm (typical); Power gain 24 dB (typical); PAE 56% (typical); τ = 100 µs; D = 10%.

Operating frequency: Symbol: f; Minimum: 2700; Maximum: 3900; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 47.6; Typical: 48; Unit: dBm

Power gain: Symbol: Gp; Minimum: 23.6; Typical: 24; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.6; Unit: dB

Vd = +28 V; Vg = -2.7 V; Pin = 24 dBm; τ = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-10000-13000-PS30p5T

10000–13000 MHz GaN MMIC Power Amplifier Die

10000–13000 MHz; Saturated output power: 30.5 dBm (typical); Power gain: 30 dB (typical); Power-added efficiency: 22 % (typical); Die dimensions: 2.22 × 1.16 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 10000; Maximum: 13000; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 30; Typical: 30.5; Unit: dBm

Power gain: Symbol: Gp; Typical: 30; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.4 V

Product details Product datasheet



LCI-PA-10000-13000-PS48T

10000–13000 MHz GaN MMIC Power Amplifier Die

10000–13000 MHz; Saturated output power: 48 dBm (typical); Power gain: 20 dB (typical); Power-added efficiency: 37 % (typical); Die dimensions: 3.4 × 5.74 × 0.08 mm.

Operating frequency: Symbol: f; Minimum: 10000; Maximum: 13000; Unit: MHz

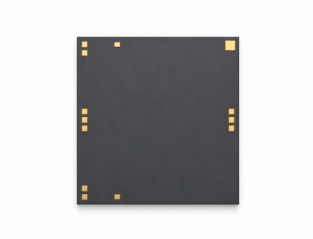
Saturated output power: Symbol: Psat; Minimum: 47; Typical: 48; Unit: dBm

Power gain: Symbol: Gp; Minimum: 19; Typical: 20; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±1; Unit: dB

TA = +25 °C; Vd = +28 V; Id = 2.2 A

Product details Product datasheet



LCI-PA-1200-2400-PS45T

1200–2400 MHz GaN MMIC Power Amplifier Die

1200–2400 MHz; Saturated output power: 45 dBm (typical); Power gain: 25 dB (typical); Power-added efficiency: 53 % (typical); Die dimensions: 3.1 × 3.2 × 0.08 mm.

Operating frequency: Symbol: f; Minimum: 1200; Maximum: 2400; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 44.5; Typical: 45; Maximum: 45.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 24.5; Typical: 25; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-6000-12000-PS48T

6000–12000 MHz GaN MMIC Power Amplifier Die

6000–12000 MHz; Saturated output power: 48 dBm (typical); Power gain: 24 dB (typical); Power-added efficiency: 40 % (typical); Die dimensions: 3.85 × 5.82 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 6000; Maximum: 12000; Unit: MHz

Saturated output power: Symbol: Psat; Typical: 48; Unit: dBm

Power gain: Symbol: Gp; Typical: 24; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±1; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-PA-7000-13000-PS48T

7000–13000 MHz GaN MMIC Power Amplifier Die

7000–13000 MHz; Saturated output power: 48 dBm (typical); Power gain: 24 dB (typical); Power-added efficiency: 40 % (typical); Die dimensions: 3.83 × 5.82 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 7000; Maximum: 13000; Unit: MHz

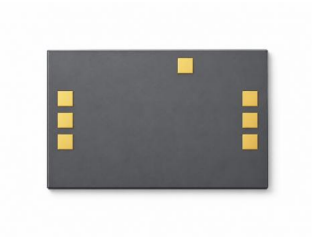
Saturated output power: Symbol: Psat; Typical: 48; Unit: dBm

Power gain: Symbol: Gp; Typical: 24; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±1; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-LNA-5000-6000-NF0p6T

5000–6000 MHz GaAs MMIC Low-Noise Amplifier Die — NF 0.6 dB (typical)

5000–6000 MHz; NF 0.6 dB (typical); Small-signal gain 28 dB (typical); P1dB 6 dBm (typical).

Operating frequency: Symbol: f; Minimum: 5000; Maximum: 6000; Value: 5000–6000; Unit: MHz

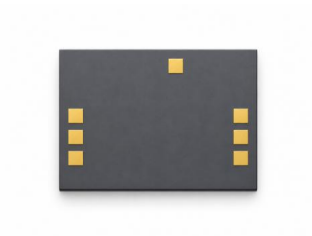
Output 1 dB compression power: Symbol: P1dB; Typical: 6; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 28; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-7000-13000-NF0p9T

7000–13000 MHz GaAs MMIC Low-Noise Amplifier Die — NF 0.9 dB (typical)

7000–13000 MHz; NF 0.9 dB (typical); Small-signal gain 22 dB (typical); P1dB 14 dBm (typical).

Operating frequency: Symbol: f; Minimum: 7000; Maximum: 13000; Value: 7000–13000; Unit: MHz

Output 1 dB compression power: Symbol: P1dB; Typical: 14; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 22; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Maximum: ±0.4; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-7000-13000-NF1T

7000–13000 MHz GaAs MMIC Low-Noise Amplifier Die — NF 1 dB (typical)

7000–13000 MHz; NF 1 dB (typical); Small-signal gain ≥ 28 dB; P1dB 6 dBm (typical).

Operating frequency: Symbol: f; Minimum: 7000; Maximum: 13000; Value: 7000–13000; Unit: MHz

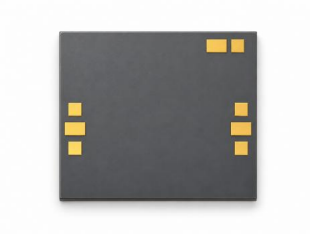
Output 1 dB compression power: Symbol: P1dB; Typical: 6; Unit: dBm

Small-signal gain: Symbol: Gain; Minimum: 28; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Typical: ±2; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-2000-6000-NF0p8T

2000–6000 MHz GaAs MMIC Low-Noise Amplifier Die — NF 0.8 dB (typical)

2000–6000 MHz; NF 0.8 dB (typical); Small-signal gain ≥ 29 dB; P1dB 10 dBm (typical).

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 6000; Value: 2000–6000; Unit: MHz

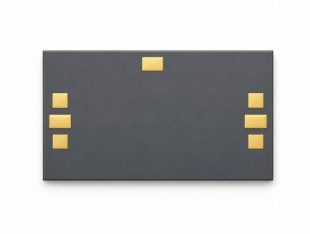
Output 1 dB compression power: Symbol: P1dB; Typical: 10; Unit: dBm

Small-signal gain: Symbol: Gain; Minimum: 29; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Typical: ±0.2; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-6000-18000-NF1p2T

6000–18000 MHz GaAs MMIC Low-Noise Amplifier Die — NF 1.2 dB (typical)

6000–18000 MHz; NF 1.2 dB (typical); Small-signal gain 22 dB (typical); P1dB 8 dBm (typical).

Operating frequency: Symbol: f; Minimum: 6000; Maximum: 18000; Value: 6000–18000; Unit: MHz

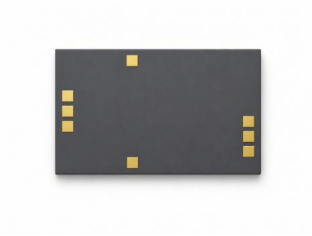
Output 1 dB compression power: Symbol: P1dB; Typical: 8; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 22; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Typical: ±2; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-24000-40000-NF2p5T

24000–40000 MHz GaAs MMIC Low-Noise Amplifier Die — NF 2.5 dB (typical)

24000–40000 MHz; NF 2.5 dB (typical); Small-signal gain 23 dB (typical); P1dB ≥ 11 dBm.

Operating frequency: Symbol: f; Minimum: 24000; Maximum: 40000; Value: 24000–40000; Unit: MHz

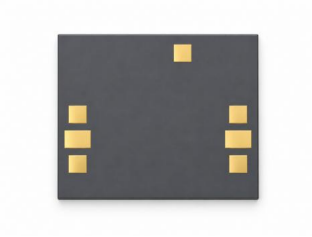
Output 1 dB compression power: Symbol: P1dB; Minimum: 11; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 23; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Typical: ±1; Unit: dB

TA = +25 °C; Vd = +5 V; Vg = 0 V

Product details Product datasheet



LCI-LNA-8000-12000-NF0p7T-SG26T

8000–12000 MHz GaAs MMIC Low-Noise Amplifier Die — NF 0.7 dB (typical)

8000–12000 MHz; NF 0.7 dB (typical); Small-signal gain 26 dB (typical); P1dB 8 dBm (typical).

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

Output 1 dB compression power: Symbol: P1dB; Minimum: 7; Typical: 8; Unit: dBm

Small-signal gain: Symbol: Gain; Minimum: 25; Typical: 26; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Maximum: ±1; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-2000-20000-NF2T

2000–20000 MHz GaAs MMIC Low-Noise Amplifier Die — NF 2 dB (typical)

2000–20000 MHz; NF 2 dB (typical); Small-signal gain 17 dB (typical); P1dB 14 dBm (typical).

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 20000; Value: 2000–20000; Unit: MHz

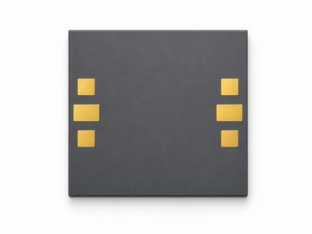
Output 1 dB compression power: Symbol: P1dB; Typical: 14; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 17; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Typical: ±0.5; Unit: dB

TA = +25 °C; Vd = +5 V; Vg = 0 V

Product details Product datasheet



LCI-LNA-100-2000-NF1p1T

100–2000 MHz GaAs MMIC Low-Noise Amplifier Die — NF 1.1 dB (typical)

100–2000 MHz; NF 1.1 dB (typical); Small-signal gain 17.5 dB (typical); P1dB 19.5 dBm (typical).

Operating frequency: Symbol: f; Minimum: 100; Maximum: 2000; Value: 100–2000; Unit: MHz

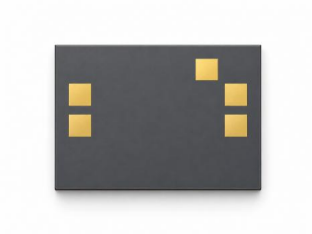
Output 1 dB compression power: Symbol: P1dB; Typical: 19.5; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 17.5; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Typical: ±1; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-800-2000-NF0p45T

800–2000 MHz GaAs MMIC Low-Noise Amplifier Die — NF 0.45 dB (typical)

800–2000 MHz; NF 0.45 dB (typical); Small-signal gain 23 dB (typical); P1dB 20.5 dBm (typical).

Operating frequency: Symbol: f; Minimum: 800; Maximum: 2000; Value: 800–2000; Unit: MHz

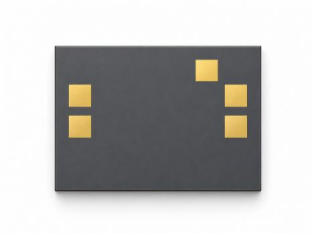
Output 1 dB compression power: Symbol: P1dB; Typical: 20.5; Unit: dBm

Saturated output power: Symbol: Psat; Value: 22; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 23; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-200-600-NF0p4T

200–600 MHz GaAs MMIC Low-Noise Amplifier Die — NF 0.4 dB (typical)

200–600 MHz; NF 0.4 dB (typical); Small-signal gain 28 dB (typical); P1dB 21 dBm (typical).

Operating frequency: Symbol: f; Minimum: 200; Maximum: 600; Value: 200–600; Unit: MHz

Output 1 dB compression power: Symbol: P1dB; Typical: 21; Unit: dBm

Saturated output power: Symbol: Psat; Value: 22.5; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 28; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-2000-5000-NF0p45T-P1DB14T

2000–5000 MHz GaAs MMIC Low-Noise Amplifier Die — NF 0.45 dB (typical); P1dB 14 dBm (typical)

2000–5000 MHz; NF 0.45 dB (typical); Small-signal gain 30 dB (typical); P1dB 14 dBm (typical).

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 5000; Value: 2000–5000; Unit: MHz

Output 1 dB compression power: Symbol: P1dB; Typical: 14; Unit: dBm

Saturated output power: Symbol: Psat; Value: 15; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 30; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-7000-9000-NF0p6U

7000–9000 MHz GaAs MMIC Low-Noise Amplifier Die — NF 0.6 dB

7000–9000 MHz; NF 0.6 dB; Small-signal gain 31 dB (typical); P1dB 15 dBm (typical).

Operating frequency: Symbol: f; Minimum: 7000; Maximum: 9000; Value: 7000–9000; Unit: MHz

Output 1 dB compression power: Symbol: P1dB; Typical: 15; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 31; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Typical: ±0.5; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-6000-20000-NF1p2T

6000–20000 MHz GaAs MMIC Low-Noise Amplifier Die — NF 1.2 dB (typical)

6000–20000 MHz; NF 1.2 dB (typical); Small-signal gain 26 dB (typical); P1dB -2 dBm (typical).

Operating frequency: Symbol: f; Minimum: 6000; Maximum: 20000; Value: 6000–20000; Unit: MHz

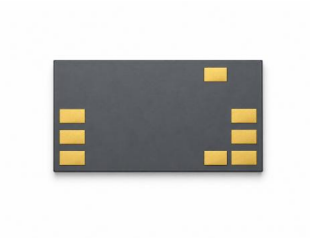
Output 1 dB compression power: Symbol: P1dB; Minimum: -4; Typical: -2; Maximum: 0; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 26; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Typical: ±1; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-4000-12000-NF0p6T

4000–12000 MHz GaAs MMIC Low-Noise Amplifier Die — NF 0.6 dB (typical)

4000–12000 MHz; NF 0.6 dB (typical); Small-signal gain 34.5 dB (typical); P1dB 7 dBm (typical).

Operating frequency: Symbol: f; Minimum: 4000; Maximum: 12000; Value: 4000–12000; Unit: MHz

Output 1 dB compression power: Symbol: P1dB; Minimum: 6.5; Typical: 7; Maximum: 8.5; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 34.5; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Typical: ±0.2; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-2000-5000-NF0p45T-P1DB11T

2000–5000 MHz GaAs MMIC Low-Noise Amplifier Die — NF 0.45 dB (typical); P1dB 11 dBm (typical)

2000–5000 MHz; NF 0.45 dB (typical); Small-signal gain 30 dB (typical); P1dB 11 dBm (typical).

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 5000; Value: 2000–5000; Unit: MHz

Output 1 dB compression power: Symbol: P1dB; Typical: 11; Unit: dBm

Saturated output power: Symbol: Psat; Value: 12; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 30; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-LNA-32000-52000-NF1p8T

32000–52000 MHz GaAs MMIC Low-Noise Amplifier Die — NF 1.8 dB (typical)

32000–52000 MHz; NF 1.8 dB (typical); Small-signal gain 26 dB (typical); P1dB 5 dBm (typical).

Operating frequency: Symbol: f; Minimum: 32000; Maximum: 52000; Value: 32000–52000; Unit: MHz

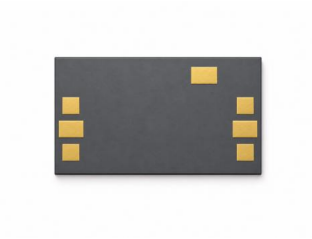
Output 1 dB compression power: Symbol: P1dB; Typical: 5; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 26; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Typical: ±1; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-AMP-8000-12000-P1DB16T

8000–12000 MHz GaAs MMIC Amplifier Die — P1dB 16 dBm (typical)

8000–12000 MHz; P1dB 16 dBm (typical); Small-signal gain 24 dB (typical); NF 1.7 dB (typical).

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

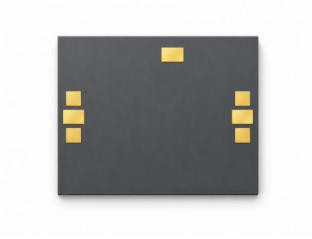
Output 1 dB compression power: Symbol: P1dB; Typical: 16; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 24; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Typical: ±0.5; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-AMP-700-5000-P1DB19T

700–5000 MHz GaAs MMIC Amplifier Die — P1dB 19 dBm (typical)

700–5000 MHz; P1dB 19 dBm (typical); Small-signal gain 14 dB (typical); NF 2.5 dB (typical).

Operating frequency: Symbol: f; Minimum: 700; Maximum: 5000; Value: 700–5000; Unit: MHz

Output 1 dB compression power: Symbol: P1dB; Typical: 19; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 14; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Typical: ±1; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-AMP-2700-3500-P1DB23p5T

2700–3500 MHz GaAs MMIC Amplifier Die — P1dB 23.5 dBm (typical)

2700–3500 MHz; P1dB 23.5 dBm (typical); Small-signal gain 28 dB (typical); NF 3.5 dB (typical).

Operating frequency: Symbol: f; Minimum: 2700; Maximum: 3500; Value: 2700–3500; Unit: MHz

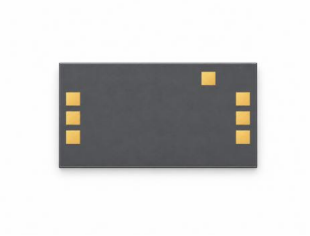
Output 1 dB compression power: Symbol: P1dB; Typical: 23.5; Unit: dBm

Saturated output power: Symbol: Psat; Value: 25; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 28; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-AMP-14000-18000-P1DB23T-D

14000–18000 MHz GaAs MMIC Amplifier Die — P1dB 23 dBm (typical)

14000–18000 MHz; P1dB 23 dBm (typical); Small-signal gain 19 dB (typical); NF 5.5 dB (typical).

Operating frequency: Symbol: f; Minimum: 14000; Maximum: 18000; Value: 14000–18000; Unit: MHz

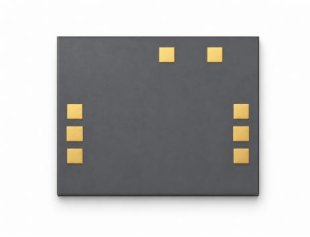
Output 1 dB compression power: Symbol: P1dB; Typical: 23; Unit: dBm

Saturated output power: Symbol: Psat; Value: 24; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 19; Maximum: 23; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-AMP-5000-20000-P1DB20T

5000–20000 MHz GaAs MMIC Amplifier Die — P1dB 20 dBm (typical)

5000–20000 MHz; P1dB 20 dBm (typical); Small-signal gain 21 dB (typical); NF 6.5 dB (typical).

Operating frequency: Symbol: f; Minimum: 5000; Maximum: 20000; Value: 5000–20000; Unit: MHz

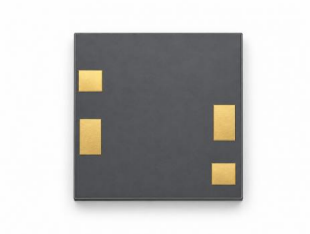
Output 1 dB compression power: Symbol: P1dB; Typical: 20; Unit: dBm

Saturated output power: Symbol: Psat; Value: 21; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 21; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-AMP-DC-6000-P1DB22p8T

DC–6000 MHz GaAs MMIC Amplifier Die — P1dB 22.8 dBm (typical)

DC–6000 MHz; P1dB 22.8 dBm (typical); Small-signal gain 21 dB (typical); NF 1.8 dB (typical).

Operating frequency: Symbol: f; Minimum: DC; Maximum: 6000; Value: DC–6000; Unit: MHz

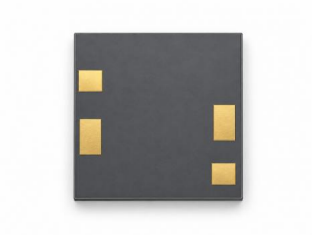
Output 1 dB compression power: Symbol: P1dB; Typical: 22.8; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 21; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Typical: ±1; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-AMP-DC-6000-P1DB21T

DC–6000 MHz GaAs MMIC Amplifier Die — P1dB 21 dBm (typical)

DC–6000 MHz; P1dB 21 dBm (typical); Small-signal gain 20 dB (typical); NF 1 dB (typical).

Operating frequency: Symbol: f; Minimum: DC; Maximum: 6000; Value: DC–6000; Unit: MHz

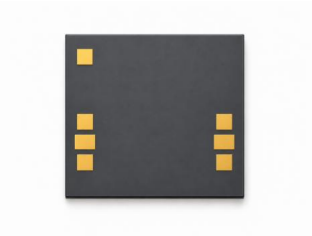
Output 1 dB compression power: Symbol: P1dB; Typical: 21; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 20; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Typical: ±1; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-AMP-800-2000-P1DB15T

800–2000 MHz GaAs MMIC Amplifier Die — P1dB 15 dBm (typical)

800–2000 MHz; P1dB 15 dBm (typical); Small-signal gain 17 dB (typical); NF 1.4 dB (typical).

Operating frequency: Symbol: f; Minimum: 800; Maximum: 2000; Value: 800–2000; Unit: MHz

Output 1 dB compression power: Symbol: P1dB; Typical: 15; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 17; Unit: dB

Small-signal gain flatness: Symbol: ΔGain; Typical: ±0.3; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-AMP-2000-7000-P1DB23p5T

2000–7000 MHz GaAs MMIC Amplifier Die — P1dB 23.5 dBm (typical)

2000–7000 MHz; P1dB 23.5 dBm (typical); Small-signal gain 21 dB (typical); NF 5 dB (typical).

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 7000; Value: 2000–7000; Unit: MHz

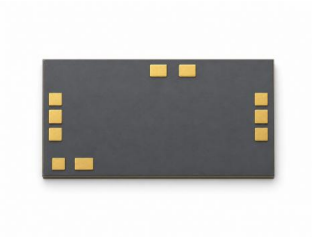
Output 1 dB compression power: Symbol: P1dB; Typical: 23.5; Unit: dBm

Saturated output power: Symbol: Psat; Value: 24.5; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 21; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-AMP-8000-12000-PS28T

8000–12000 MHz GaAs MMIC Amplifier Die — PSAT 28 dBm (typical)

8000–12000 MHz; PSAT 28 dBm (typical); Small-signal gain 21 dB (typical).

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

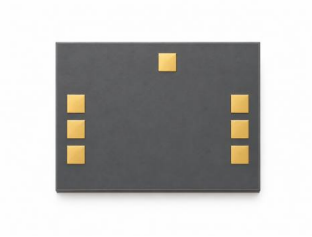
Saturated output power: Minimum: 27.8; Typical: 28; Unit: dBm

Power gain: Typical: 19; Unit: dB

Power-added efficiency: Typical: 40; Unit: %

TA = +25 °C; Vd = +5 V; Vg = -0.6 V

Product details Product datasheet



LCI-AMP-4000-9000-P1DB17T

4000–9000 MHz GaAs MMIC Amplifier Die — P1dB 17 dBm (typical)

4000–9000 MHz; P1dB 17 dBm (typical); Small-signal gain 13 dB (typical); NF 3.5 dB (typical).

Operating frequency: Symbol: f; Minimum: 4000; Maximum: 9000; Value: 4000–9000; Unit: MHz

Output 1 dB compression power: Symbol: P1dB; Typical: 17; Unit: dBm

Saturated output power: Symbol: Psat; Value: 18; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 13; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-AMP-2000-18000-P1DB16T

2000–18000 MHz GaAs MMIC Amplifier Die — P1dB 16 dBm (typical)

2000–18000 MHz; P1dB 16 dBm (typical); Small-signal gain 21 dB (typical); NF 3 dB (typical).

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 18000; Value: 2000–18000; Unit: MHz

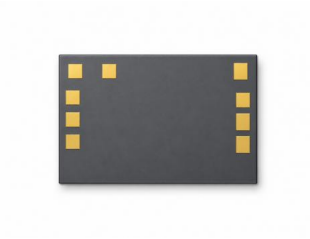
Output 1 dB compression power: Symbol: P1dB; Typical: 16; Unit: dBm

Saturated output power: Symbol: Psat; Value: 17; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 21; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-AMP-6000-12000-P1DB23T

6000–12000 MHz GaAs MMIC Amplifier Die — P1dB 23 dBm (typical)

6000–12000 MHz; P1dB 23 dBm (typical); Small-signal gain 23 dB (typical); NF 5 dB (typical).

Operating frequency: Symbol: f; Minimum: 6000; Maximum: 12000; Value: 6000–12000; Unit: MHz

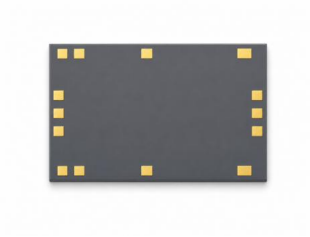
Output 1 dB compression power: Symbol: P1dB; Typical: 23; Unit: dBm

Saturated output power: Symbol: Psat; Value: 23.8; Unit: dBm

Small-signal gain: Symbol: Gain; Typical: 23; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-AMP-24000-31000-PS25T

24000–31000 MHz GaAs MMIC Amplifier Die — PSAT 25 dBm (typical)

24000–31000 MHz; PSAT 25 dBm (typical); Small-signal gain 22 dB (typical).

Operating frequency: Symbol: f; Minimum: 24000; Maximum: 31000; Value: 24000–31000; Unit: MHz

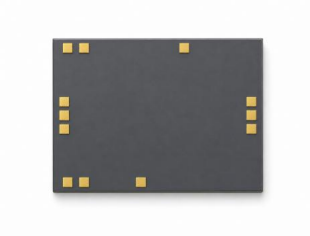
Small-signal gain: Typical: 22; Unit: dB

Saturated output power: Typical: 25; Unit: dBm

Power gain: Typical: 20; Unit: dB

TA = +25 °C; Vd = +5 V; Id = 160 mA

Product details Product datasheet



LCI-BDA-8000-18000-RXP1DB24T

8000–18000 MHz GaAs MMIC Bidirectional Amplifier Die — Rx / Tx P1dB 24 dBm (typical)

8000–18000 MHz; Rx / Tx: Rx / Tx P1dB 24 dBm (typical); Small-signal gain 21 dB (typical).

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 18000; Value: 8000–18000; Unit: MHz

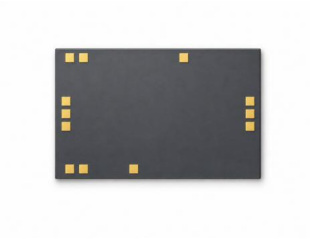
Output 1 dB compression power (Rx): Typical: 24; Unit: dBm

Saturated output power (Rx): Typical: 24.5; Unit: dBm

Small-signal gain (Rx): Typical: 21; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-BDA-6000-18000-RXP1DB21T

6000–18000 MHz GaAs MMIC Bidirectional Amplifier Die — Rx / Tx P1dB 21 dBm (typical)

6000–18000 MHz; Rx / Tx: Rx / Tx P1dB 21 dBm (typical); Small-signal gain 19 dB (typical).

Operating frequency: Symbol: f; Minimum: 6000; Maximum: 18000; Value: 6000–18000; Unit: MHz

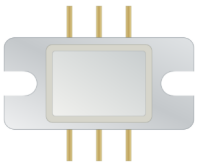
Output 1 dB compression power (Rx): Typical: 21; Unit: dBm

Saturated output power (Rx): Typical: 22; Unit: dBm

Small-signal gain (Rx): Typical: 19; Unit: dB

TA = +25 °C; Vd = +5 V

Product details Product datasheet



LCI-PA-2000-6000-PS40T

2000–6000 MHz GaN Packaged Power Amplifier — PSAT 40 dBm (typical)

2000–6000 MHz; PSAT 40 dBm (typical); Power gain 22 dB (typical); PAE 38 % (typical).

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 6000; Value: 2000–6000; Unit: MHz

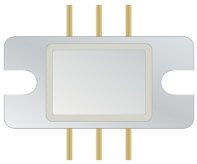
Saturated output power: Minimum: 39.5; Typical: 40; Unit: dBm

Power gain: Minimum: 21.5; Typical: 22; Unit: dB

Power-added efficiency: Minimum: 32; Typical: 38; Unit: %

TA = +25 °C; Vd = +28 V; Vg = -2.4 V; Pin = 18 dBm; CW

Product details Product datasheet



LCI-PA-7500-10500-PS48T

7500–10500 MHz GaN Packaged Power Amplifier — PSAT 48 dBm (typical)

7500–10500 MHz; PSAT 48 dBm (typical); Power gain 24 dB (typical); PAE 40 % (typical).

Operating frequency: Symbol: f; Minimum: 7500; Maximum: 10500; Value: 7500–10500; Unit: MHz

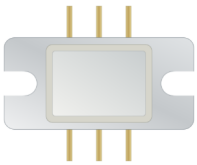
Saturated output power: Minimum: 47.5; Typical: 48; Unit: dBm

Power gain: Minimum: 23.5; Typical: 24; Unit: dB

Power-added efficiency: Minimum: 32; Typical: 40; Unit: %

Vd = +28 V; Vg = -2.6 V; D = 10%; Pin = 24 dBm

Product details Product datasheet



LCI-PA-2000-8500-PS41T

2000–8500 MHz GaN Packaged Power Amplifier — PSAT 41 dBm (typical)

2000–8500 MHz; PSAT 41 dBm (typical); Power gain 15 dB (typical); PAE 35 % (typical).

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 8500; Value: 2000–8500; Unit: MHz

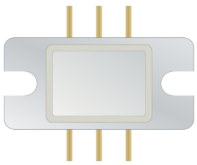
Saturated output power: Minimum: 40.3; Typical: 41; Unit: dBm

Power gain: Minimum: 14.3; Typical: 15; Unit: dB

Power-added efficiency: Minimum: 25; Typical: 35; Unit: %

TA = +25 °C; Vd = +28 V; Vg = -2.6 V; Pin = 26 dBm; PW = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-2500-6200-PS44p5T

2500–6200 MHz GaN Packaged Power Amplifier — PSAT 44.5 dBm (typical)

2500–6200 MHz; PSAT 44.5 dBm (typical); Power gain 16.5 dB (typical); PAE 40 % (typical).

Operating frequency: Symbol: f; Minimum: 2500; Maximum: 6200; Value: 2500–6200; Unit: MHz

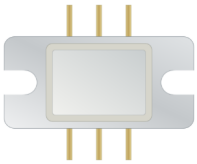
Saturated output power: Minimum: 44; Typical: 44.5; Unit: dBm

Power gain: Minimum: 16; Typical: 16.5; Unit: dB

Power-added efficiency: Minimum: 35; Typical: 40; Unit: %

TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 28 dBm; PW = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-5000-6000-PS47T

5000–6000 MHz GaN Packaged Power Amplifier — PSAT 47 dBm (typical)

5000–6000 MHz; PSAT 47 dBm (typical); Power gain 24 dB (typical); PAE 56 % (typical).

Operating frequency: Symbol: f; Minimum: 5000; Maximum: 6000; Value: 5000–6000; Unit: MHz

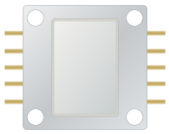
Saturated output power: Minimum: 46.2; Typical: 47; Unit: dBm

Power gain: Minimum: 23.2; Typical: 24; Unit: dB

Power-added efficiency: Minimum: 50; Typical: 56; Unit: %

TA = +25 °C; Vd = +28 V; Vg = -2.6 V; Pin = 23 dBm; PW = 100 µs; D = 5%

Product details Product datasheet



LCI-PA-13400-14600-PS44p5T

13400–14600 MHz GaN Packaged Power Amplifier — PSAT 44.5 dBm (typical)

13400–14600 MHz; PSAT 44.5 dBm (typical); Power gain 19.5 dB (typical); PAE 32 % (typical).

Operating frequency: Symbol: f; Minimum: 13400; Maximum: 14600; Value: 13400–14600; Unit: MHz

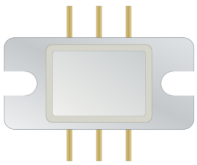
Saturated output power: Minimum: 43.7; Typical: 44.5; Unit: dBm

Power gain: Typical: 19.5; Unit: dB

Power-added efficiency: Minimum: 28; Typical: 32; Unit: %

TA = +25 °C; VDS = 28 V; VGS ∈ [-3.2, -2.4] V; Pin = 25 dBm; CW

Product details Product datasheet



LCI-PA-5000-6000-PS49T

5000–6000 MHz GaN Packaged Power Amplifier — PSAT 49 dBm (typical)

5000–6000 MHz; PSAT 49 dBm (typical); Power gain 26 dB (typical); PAE 53 % (typical).

Operating frequency: Symbol: f; Minimum: 5000; Maximum: 6000; Value: 5000–6000; Unit: MHz

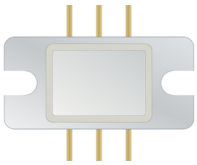
Saturated output power: Minimum: 48.5; Typical: 49; Unit: dBm

Power gain: Minimum: 25.5; Typical: 26; Unit: dB

Power-added efficiency: Minimum: 51; Typical: 53; Unit: %

TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 23 dBm; PW = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-2500-3700-PS41T

2500–3700 MHz GaN Packaged Power Amplifier — PSAT 41 dBm (typical)

2500–3700 MHz; PSAT 41 dBm (typical); Power gain 22 dB (typical); PAE 47 % (typical).

Operating frequency: Symbol: f; Minimum: 2500; Maximum: 3700; Value: 2500–3700; Unit: MHz

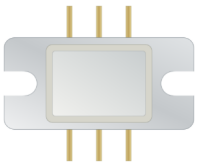
Saturated output power: Minimum: 40.5; Typical: 41; Unit: dBm

Power gain: Minimum: 21.5; Typical: 22; Unit: dB

Power-added efficiency: Minimum: 42; Typical: 47; Unit: %

TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 19 dBm; PW = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-13600-14500-PS41MIN

13600–14500 MHz GaN Packaged Power Amplifier — PSAT ≥ 41 dBm

13600–14500 MHz; PSAT ≥ 41 dBm; Power gain ≥ 20 dB; PAE 37 % (typical).

Operating frequency: Symbol: f; Minimum: 13600; Maximum: 14500; Value: 13600–14500; Unit: MHz

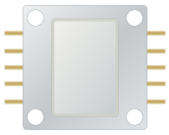
Saturated output power: Minimum: 41; Unit: dBm

Power gain: Minimum: 20; Unit: dB

Power-added efficiency: Minimum: 32; Typical: 37; Unit: %

Vd = +28 V; Vg = -3.05 V; Pin = 21 dBm; CW

Product details Product datasheet



LCI-PA-6000-12000-PS46T

6000–12000 MHz GaN Packaged Power Amplifier — PSAT 46 dBm (typical)

6000–12000 MHz; PSAT 46 dBm (typical); Power gain 22 dB (typical); PAE 30 % (typical).

Operating frequency: Symbol: f; Minimum: 6000; Maximum: 12000; Value: 6000–12000; Unit: MHz

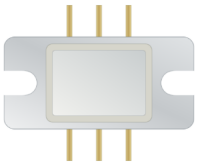
Saturated output power: Typical: 46; Unit: dBm

Power gain: Typical: 22; Unit: dB

Power-added efficiency: Typical: 30; Unit: %

TA = +25 °C; VDS = 28 V; VGS ∈ [-3.2, -2.4] V; Pin = 25 dBm; D = 10%; PW = 100 µs

Product details Product datasheet



LCI-PA-4200-7000-PS41MIN

4200–7000 MHz GaN Packaged Power Amplifier — PSAT ≥ 41 dBm

4200–7000 MHz; PSAT ≥ 41 dBm; Power gain ≥ 21 dB; PAE 40 % (typical).

Operating frequency: Symbol: f; Minimum: 4200; Maximum: 7000; Value: 4200–7000; Unit: MHz

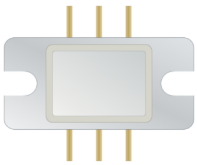
Saturated output power: Minimum: 41; Unit: dBm

Power gain: Minimum: 21; Unit: dB

Power-added efficiency: Typical: 40; Unit: %

Vd = +28 V; Vg = -2.6 V; Pin = 20 dBm; CW

Product details Product datasheet



LCI-PA-4000-5000-PS45MIN

4000–5000 MHz GaN Packaged Power Amplifier — PSAT ≥ 45 dBm

4000–5000 MHz; PSAT ≥ 45 dBm; Power gain ≥ 26 dB; PAE 50 % (typical).

Operating frequency: Symbol: f; Minimum: 4000; Maximum: 5000; Value: 4000–5000; Unit: MHz

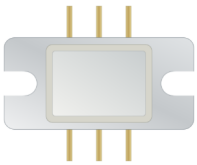
Saturated output power: Minimum: 45; Unit: dBm

Power gain: Minimum: 26; Unit: dB

Power-added efficiency: Minimum: 40; Typical: 50; Unit: %

Vd = +28 V; Vg = -3.05 V; D = 10%; Pin = 19 dBm

Product details Product datasheet



LCI-PA-1200-1600-PS42MIN

1200–1600 MHz GaN Packaged Power Amplifier — PSAT ≥ 42 dBm

1200–1600 MHz; PSAT ≥ 42 dBm; Power gain ≥ 16 dB; PAE 55 % (typical).

Operating frequency: Symbol: f; Minimum: 1200; Maximum: 1600; Value: 1200–1600; Unit: MHz

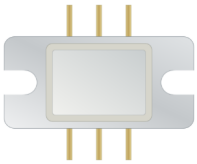
Saturated output power: Minimum: 42; Unit: dBm

Power gain: Minimum: 16; Unit: dB

Power-added efficiency: Minimum: 45; Typical: 55; Unit: %

Vd = +28 V; Vg = -1.8; D = 10%; Pin = 26 dBm

Product details Product datasheet



LCI-PA-2500-4000-PS46p5T

2500–4000 MHz GaN Packaged Power Amplifier — PSAT 46.5 dBm (typical)

2500–4000 MHz; PSAT 46.5 dBm (typical); Power gain 26.5 dB (typical); PAE 50 % (typical).

Operating frequency: Symbol: f; Minimum: 2500; Maximum: 4000; Value: 2500–4000; Unit: MHz

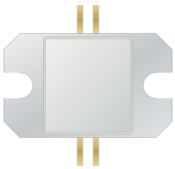
Saturated output power: Minimum: 46; Typical: 46.5; Unit: dBm

Power gain: Minimum: 25; Typical: 26.5; Unit: dB

Power-added efficiency: Minimum: 45; Typical: 50; Unit: %

Vd = +28 V; Vg = -2.3 V; D = 10%; Pin = 20 dBm

Product details Product datasheet



LCI-PA-2700-3500-PS45p5T-C

2700–3500 MHz GaN Packaged Power Amplifier — PSAT 45.5 dBm (typical)

2700–3500 MHz; PSAT 45.5 dBm (typical); Power gain 26.5 dB (typical); PAE 55 % (typical).

Operating frequency: Symbol: f; Minimum: 2700; Maximum: 3500; Value: 2700–3500; Unit: MHz

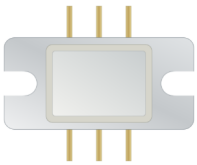
Saturated output power: Minimum: 44.5; Typical: 45.5; Unit: dBm

Power gain: Minimum: 25.5; Typical: 26.5; Unit: dB

Power-added efficiency: Minimum: 50; Typical: 55; Unit: %

Vd = +28 V; Vg = -2.8 V; D = 10%; Pin = 19 dBm

Product details Product datasheet



LCI-PA-4000-8000-PS43T

4000–8000 MHz GaN Packaged Power Amplifier — PSAT 43 dBm (typical)

4000–8000 MHz; PSAT 43 dBm (typical); Power gain 20 dB (typical); PAE 35 % (typical).

Operating frequency: Symbol: f; Minimum: 4000; Maximum: 8000; Value: 4000–8000; Unit: MHz

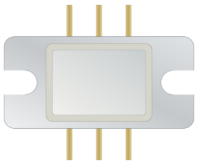
Saturated output power: Minimum: 42; Typical: 43; Unit: dBm

Power gain: Minimum: 19; Typical: 20; Unit: dB

Power-added efficiency: Minimum: 30; Typical: 35; Unit: %

Vd = +28 V; Vg = -2.2 V; PW = 100 µs; D = 10%; Pin = 23 dBm

Product details Product datasheet



LCI-PA-3400-4800-PS43T

3400–4800 MHz GaN Packaged Power Amplifier — PSAT 43 dBm (typical)

3400–4800 MHz; PSAT 43 dBm (typical); Power gain 23 dB (typical); PAE 45 % (typical).

Operating frequency: Symbol: f; Minimum: 3400; Maximum: 4800; Value: 3400–4800; Unit: MHz

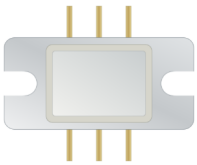
Saturated output power: Minimum: 42; Typical: 43; Unit: dBm

Power gain: Minimum: 22; Typical: 23; Unit: dB

Power-added efficiency: Minimum: 35; Typical: 45; Unit: %

Vd = +28 V; Vg = -2.8 V; Pin = 20 dBm; CW

Product details Product datasheet



LCI-PA-9200-10400-PS45T

9200–10400 MHz GaN Packaged Power Amplifier — PSAT 45 dBm (typical)

9200–10400 MHz; PSAT 45 dBm (typical); Power gain 23 dB (typical); PAE 38 % (typical).

Operating frequency: Symbol: f; Minimum: 9200; Maximum: 10400; Value: 9200–10400; Unit: MHz

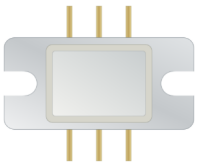
Saturated output power: Minimum: 44.7; Typical: 45; Unit: dBm

Power gain: Minimum: 22.7; Typical: 23; Unit: dB

Power-added efficiency: Minimum: 35; Typical: 38; Unit: %

Vd = +28 V; Vg = -2.4 V; PW = 100 µs; D = 10%; Pin = 22 dBm

Product details Product datasheet



LCI-PA-2000-8000-PS42p5T

2000–8000 MHz GaN Packaged Power Amplifier — PSAT 42.5 dBm (typical)

2000–8000 MHz; PSAT 42.5 dBm (typical); Power gain 15.5 dB (typical); PAE 28 % (typical).

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 8000; Value: 2000–8000; Unit: MHz

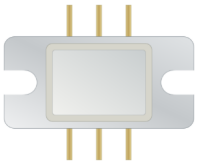
Saturated output power: Minimum: 40; Typical: 42.5; Unit: dBm

Power gain: Minimum: 13; Typical: 15.5; Unit: dB

Power-added efficiency: Minimum: 25; Typical: 28; Unit: %

TA = +25 °C; Vd = +28 V; Vg = -2.4 V; Pin = 27 dBm; CW

Product details Product datasheet



LCI-PA-5800-6800-PS46p5T

5800–6800 MHz GaN Packaged Power Amplifier — PSAT 46.5 dBm (typical)

5800–6800 MHz; PSAT 46.5 dBm (typical); Power gain 21 dB (typical); PAE 40 % (typical).

Operating frequency: Symbol: f; Minimum: 5800; Maximum: 6800; Value: 5800–6800; Unit: MHz

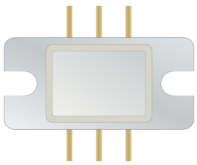
Saturated output power: Minimum: 45.5; Typical: 46.5; Unit: dBm

Power gain: Minimum: 20; Typical: 21; Unit: dB

Power-added efficiency: Typical: 40; Unit: %

TA = +25 °C; VDS = 28 V; VGS ∈ [-3.2, -2.4] V; Pin = 26 dBm; CW

Product details Product datasheet



LCI-PA-2000-6000-PS44p5T

2000–6000 MHz GaN Packaged Power Amplifier — PSAT 44.5 dBm (typical)

2000–6000 MHz; PSAT 44.5 dBm (typical); Power gain 17.5 dB (typical); PAE 35 % (typical).

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 6000; Value: 2000–6000; Unit: MHz

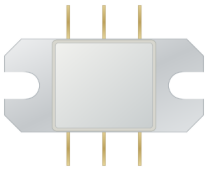
Saturated output power: Minimum: 44; Typical: 44.5; Unit: dBm

Power gain: Minimum: 17; Typical: 17.5; Unit: dB

Power-added efficiency: Minimum: 30; Typical: 35; Unit: %

TA = +25 °C; VDS = +28 V; VGS ∈ [-3.2, -2.4] V; Pin = 27 dBm; CW

Product details Product datasheet



LCI-PA-8000-12000-PS42T-C

8000–12000 MHz GaN Packaged Power Amplifier — PSAT 42 dBm (typical)

8000–12000 MHz; PSAT 42 dBm (typical); Power gain 21 dB (typical); PAE 38 % (typical).

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

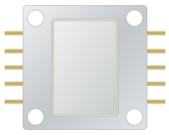
Saturated output power: Typical: 42; Unit: dBm

Power gain: Typical: 21; Unit: dB

Power-added efficiency: Typical: 38; Unit: %

TA = +25 °C; VDS = 28 V; VGS ∈ [-3.2, -2.4] V; Pin = 21 dBm; PW = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-8000-12000-PS46T

8000–12000 MHz GaN Packaged Power Amplifier — PSAT 46 dBm (typical)

8000–12000 MHz; PSAT 46 dBm (typical); Power gain 24 dB (typical); PAE 37 % (typical).

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

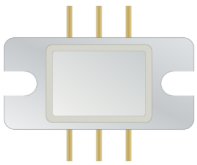
Saturated output power: Typical: 46; Unit: dBm

Power gain: Typical: 24; Unit: dB

Power-added efficiency: Typical: 37; Unit: %

TA = +25 °C; VDS = 28 V; VGS ∈ [-3.2, -2.2] V; Pin = 22 dBm; PW = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-4000-8000-PS36p5T

4000–8000 MHz GaN Packaged Power Amplifier — PSAT 36.5 dBm (typical)

4000–8000 MHz; PSAT 36.5 dBm (typical); Power gain 19.5 dB (typical); PAE 35 % (typical).

Operating frequency: Symbol: f; Minimum: 4000; Maximum: 8000; Value: 4000–8000; Unit: MHz

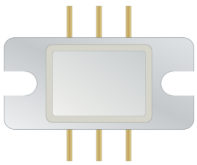
Saturated output power: Minimum: 36; Typical: 36.5; Unit: dBm

Power gain: Minimum: 19; Typical: 19.5; Unit: dB

Power-added efficiency: Minimum: 30; Typical: 35; Unit: %

TA = +25 °C; VDS = 28 V; VGS ∈ [-3.2, -2.2] V; Pin = 17 dBm; CW

Product details Product datasheet



LCI-PA-4000-8000-PS47T

4000–8000 MHz GaN Packaged Power Amplifier — PSAT 47 dBm (typical)

4000–8000 MHz; PSAT 47 dBm (typical); Power gain 19 dB (typical); PAE 40 % (typical).

Operating frequency: Symbol: f; Minimum: 4000; Maximum: 8000; Value: 4000–8000; Unit: MHz

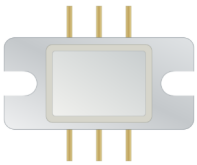
Saturated output power: Minimum: 46.5; Typical: 47; Unit: dBm

Power gain: Minimum: 18.5; Typical: 19; Unit: dB

Power-added efficiency: Minimum: 32; Typical: 40; Unit: %

TA = +25 °C; VDS = 28 V; VGS ∈ [-3.2, -2.2] V; Pin = 28 dBm; D = 10%; PW = 100 µs

Product details Product datasheet



LCI-PA-2000-6000-PS43T-C

2000–6000 MHz GaN Packaged Power Amplifier — PSAT 43 dBm (typical)

2000–6000 MHz; PSAT 43 dBm (typical); Power gain 26 dB (typical); PAE 45 % (typical).

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 6000; Value: 2000–6000; Unit: MHz

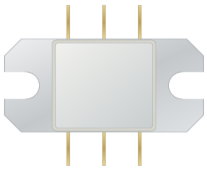
Saturated output power: Minimum: 42.5; Typical: 43; Unit: dBm

Power gain: Minimum: 25.5; Typical: 26; Unit: dB

Power-added efficiency: Minimum: 35; Typical: 45; Unit: %

TA = +25 °C; VDS = +28 V; VGS ∈ [-3.2, -2.2] V; Pin = 17 dBm; D = 10%; PW = 100 µs

Product details Product datasheet



LCI-PA-8000-12000-PS39T-C

8000–12000 MHz GaN Packaged Power Amplifier — PSAT 39 dBm (typical)

8000–12000 MHz; PSAT 39 dBm (typical); Power gain 18 dB (typical); PAE 40 % (typical).

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

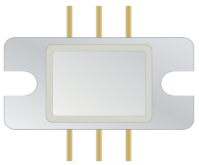
Saturated output power: Minimum: 37; Typical: 39; Unit: dBm

Power gain: Minimum: 17; Typical: 18; Unit: dB

Power-added efficiency: Typical: 40; Unit: %

TA = +25 °C; VDS = 28 V; VGS ∈ [-3.4, -2.4] V; Pin = 26 dBm; PW = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-9000-11000-PS36MIN

9000–11000 MHz GaN Packaged Power Amplifier — PSAT ≥ 36 dBm

9000–11000 MHz; PSAT ≥ 36 dBm; Power gain ≥ 23 dB; PAE 40 % (typical).

Operating frequency: Symbol: f; Minimum: 9000; Maximum: 11000; Value: 9000–11000; Unit: MHz

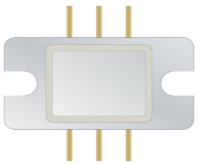
Saturated output power: Minimum: 36; Unit: dBm

Power gain: Minimum: 23; Unit: dB

Power-added efficiency: Minimum: 33; Typical: 40; Unit: %

TA = +25 °C; VDS = 28 V; VGS ∈ [-3.4, -2.4] V; Pin = 13 dBm; CW

Product details Product datasheet



LCI-PA-2700-3500-PS31p5T

2700–3500 MHz GaAs Packaged Power Amplifier — PSAT 31.5 dBm (typical)

2700–3500 MHz; PSAT 31.5 dBm (typical); Power gain 36.5 dB (typical); PAE 40 % (typical).

Operating frequency: Symbol: f; Minimum: 2700; Maximum: 3500; Value: 2700–3500; Unit: MHz

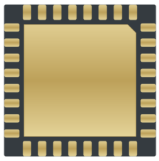
Saturated output power: Minimum: 31; Typical: 31.5; Unit: dBm

Power gain: Minimum: 36; Typical: 36.5; Unit: dB

Power-added efficiency: Minimum: 37; Typical: 40; Unit: %

TA = +25 °C; VDS = 8 V; VGS ∈ [-0.8, -0.6] V; Pin = -5 dBm; PW = 100 µs; D = 10%

Product details Product datasheet



LCI-PA-10-1100-PS40MIN

10–1100 MHz GaN Packaged Power Amplifier — PSAT ≥ 40 dBm

10–1100 MHz; PSAT ≥ 40 dBm; Power gain ≥ 13 dB; PAE ≥ 60 %.

Operating frequency: Symbol: f; Minimum: 10; Maximum: 1100; Value: 10–1100; Unit: MHz

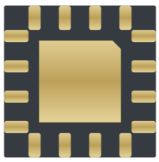
Saturated output power: Minimum: 40; Unit: dBm

Power gain: Minimum: 13; Unit: dB

Power-added efficiency: Minimum: 60; Unit: %

TA = +25 °C; VDS = +28 V; VGS ∈ [-3.2, -2.4] V; Pin = 23 dBm; CW

Product details Product datasheet



LCI-LNA-4000-12000-NF0p8T

4000–12000 MHz Packaged Low-Noise Amplifier — NF 0.8 dB (typical)

4000–12000 MHz; Small-signal gain 34 dB (typical); Noise figure 0.8 dB (typical); Output 1 dB compression power 7 dBm (typical).

Operating frequency: Symbol: f; Minimum: 4000; Maximum: 12000; Value: 4000–12000; Unit: MHz

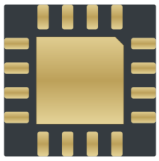
Small-signal gain: Symbol: Gain; Typical: 34; Unit: dB

Noise figure: Symbol: NF; Typical: 0.8; Unit: dB

Output 1 dB compression power: Symbol: P_1; Typical: 7; Unit: dBm

TA = +25 °C; VD = +5 V; Pin = -40 dBm

Product details Product datasheet



LCI-LNA-2000-5000-NF0p65T-P1DB10p5T

2000–5000 MHz Packaged Low-Noise Amplifier — NF 0.65 dB (typical)

2000–5000 MHz; Small-signal gain 29 dB (typical); Noise figure 0.65 dB (typical); Output 1 dB compression power 10.5 dBm (typical).

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 5000; Value: 2000–5000; Unit: MHz

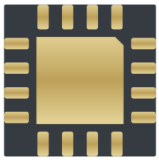
Small-signal gain: Symbol: Gain; Typical: 29; Unit: dB

Noise figure: Symbol: NF; Typical: 0.65; Unit: dB

Output 1 dB compression power: Symbol: P_1; Typical: 10.5; Unit: dBm

TA = +25 °C; VD = +5 V; Pin = -40 dBm

Product details Product datasheet



LCI-LNA-2000-5000-NF0p65T-P1DB14T

2000–5000 MHz Packaged Low-Noise Amplifier — NF 0.65 dB (typical)

2000–5000 MHz; Small-signal gain 29 dB (typical); Noise figure 0.65 dB (typical); Output 1 dB compression power 14 dBm (typical).

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 5000; Value: 2000–5000; Unit: MHz

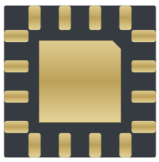
Small-signal gain: Symbol: Gain; Typical: 29; Unit: dB

Noise figure: Symbol: NF; Typical: 0.65; Unit: dB

Output 1 dB compression power: Symbol: P_1; Typical: 14; Unit: dBm

TA = +25 °C; VD = +5 V; Pin = -40 dBm

Product details Product datasheet



LCI-LNA-8000-12000-NF0p9T-SG26T

8000–12000 MHz Packaged Low-Noise Amplifier — NF 0.9 dB (typical)

8000–12000 MHz; Small-signal gain 26 dB (typical); Noise figure 0.9 dB (typical); Output 1 dB compression power ≥ 7 dBm.

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

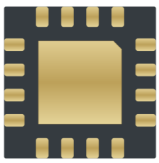
Small-signal gain: Symbol: Gain; Typical: 26; Unit: dB

Noise figure: Symbol: NF; Typical: 0.9; Unit: dB

Output 1 dB compression power: Symbol: P_1; Minimum: 7; Unit: dBm

TA = +25 °C; VD = +5 V; Pin = -30 dBm

Product details Product datasheet



LCI-LNA-6000-20000-NF1p5T

6000–20000 MHz Packaged Low-Noise Amplifier — NF 1.5 dB (typical)

6000–20000 MHz; Small-signal gain 26 dB (typical); Noise figure 1.5 dB (typical); Output 1 dB compression power -2 dBm (typical).

Operating frequency: Symbol: f; Minimum: 6000; Maximum: 20000; Value: 6000–20000; Unit: MHz

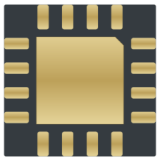
Small-signal gain: Symbol: Gain; Typical: 26; Unit: dB

Noise figure: Symbol: NF; Typical: 1.5; Unit: dB

Output 1 dB compression power: Symbol: P_1; Typical: -2; Unit: dBm

TA = +25 °C; VD = +5 V; Pin = -40 dBm

Product details Product datasheet



LCI-AMP-2000-7000-P1DB23T

2000–7000 MHz Packaged RF Gain Amplifier — P1dB 23 dBm (typical)

2000–7000 MHz; Small-signal gain 20 dB (typical); Noise figure 6 dB (typical); Output 1 dB compression power 23 dBm (typical).

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 7000; Value: 2000–7000; Unit: MHz

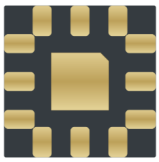
Small-signal gain: Symbol: Gain; Typical: 20; Unit: dB

Noise figure: Symbol: NF; Typical: 6; Unit: dB

Output 1 dB compression power: Symbol: P_1; Typical: 23; Unit: dBm

TA = +25 °C; VD = +5 V; Pin = -20 dBm

Product details Product datasheet



LCI-AMP-100-6000-P1DB20T

100–6000 MHz Packaged RF Gain Amplifier — P1dB 20 dBm (typical)

100–6000 MHz; Small-signal gain 17 dB (typical); Noise figure 1.2 dB (typical); Output 1 dB compression power 20 dBm (typical).

Operating frequency: Symbol: f; Minimum: 100; Maximum: 6000; Value: 100–6000; Unit: MHz

Small-signal gain: Symbol: Gain; Typical: 17; Unit: dB

Noise figure: Symbol: NF; Typical: 1.2; Unit: dB

Output 1 dB compression power: Symbol: P_1; Typical: 20; Unit: dBm

TA = +25 °C; VD = +5 V; Pin = -20 dBm

Product details Product datasheet



LCI-AMP-100-6000-P1DB22T

100–6000 MHz Packaged RF Gain Amplifier — P1dB 22 dBm (typical)

100–6000 MHz; Small-signal gain 20 dB (typical); Noise figure 2 dB (typical); Output 1 dB compression power 22 dBm (typical).

Operating frequency: Symbol: f; Minimum: 100; Maximum: 6000; Value: 100–6000; Unit: MHz

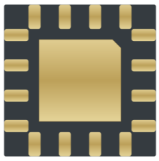
Small-signal gain: Symbol: Gain; Typical: 20; Unit: dB

Noise figure: Symbol: NF; Typical: 2; Unit: dB

Output 1 dB compression power: Symbol: P_1; Typical: 22; Unit: dBm

TA = +25 °C; VD = +5 V; Pin = -20 dBm

Product details Product datasheet



LCI-AMP-800-2000-P1DB14p5T

800–2000 MHz Packaged RF Gain Amplifier — P1dB 14.5 dBm (typical)

800–2000 MHz; Small-signal gain 16.5 dB (typical); Noise figure 1.6 dB (typical); Output 1 dB compression power 14.5 dBm (typical).

Operating frequency: Symbol: f; Minimum: 800; Maximum: 2000; Value: 800–2000; Unit: MHz

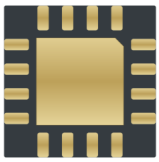
Small-signal gain: Symbol: Gain; Typical: 16.5; Unit: dB

Noise figure: Symbol: NF; Typical: 1.6; Unit: dB

Output 1 dB compression power: Symbol: P_1; Typical: 14.5; Unit: dBm

TA = +25 °C; VD = +5 V; Pin = -20 dBm

Product details Product datasheet



LCI-AMP-2700-3500-P1DB23T

2700–3500 MHz Packaged RF Gain Amplifier — P1dB 23 dBm (typical)

2700–3500 MHz; Small-signal gain 27 dB (typical); Noise figure 4 dB (typical); Output 1 dB compression power 23 dBm (typical).

Operating frequency: Symbol: f; Minimum: 2700; Maximum: 3500; Value: 2700–3500; Unit: MHz

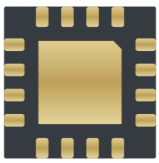
Small-signal gain: Symbol: Gain; Typical: 27; Unit: dB

Noise figure: Symbol: NF; Typical: 4; Unit: dB

Output 1 dB compression power: Symbol: P_1; Typical: 23; Unit: dBm

TA = +25 °C; VD = +5 V; Pin = -20 dBm

Product details Product datasheet



LCI-AMP-5000-20000-P1DB19p5T

5000–20000 MHz Packaged RF Gain Amplifier — P1dB 19.5 dBm (typical)

5000–20000 MHz; Small-signal gain 20 dB (typical); Noise figure 6 dB (typical); Output 1 dB compression power 19.5 dBm (typical).

Operating frequency: Symbol: f; Minimum: 5000; Maximum: 20000; Value: 5000–20000; Unit: MHz

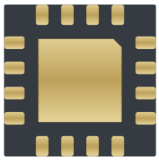
Small-signal gain: Symbol: Gain; Typical: 20; Unit: dB

Noise figure: Symbol: NF; Typical: 6; Unit: dB

Output 1 dB compression power: Symbol: P_1; Typical: 19.5; Unit: dBm

TA = +25 °C; VD = +5 V; Pin = -20 dBm

Product details Product datasheet



LCI-AMP-14000-18000-P1DB23T-C

14000–18000 MHz Packaged RF Gain Amplifier — P1dB 23 dBm (typical)

14000–18000 MHz; Small-signal gain 18 dB (typical); Noise figure 6 dB (typical); Output 1 dB compression power 23 dBm (typical).

Operating frequency: Symbol: f; Minimum: 14000; Maximum: 18000; Value: 14000–18000; Unit: MHz

Small-signal gain: Symbol: Gain; Typical: 18; Unit: dB

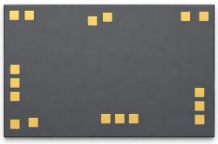
Noise figure: Symbol: NF; Typical: 6; Unit: dB

Output 1 dB compression power: Symbol: P_1; Typical: 23; Unit: dBm

TA = +25 °C; VD = +5 V; Pin = -20 dBm

Product details Product datasheet

RF Front-End ICs



LCI-TRPA-5000-13000-PS31T

5000–13000 MHz GaN T/R MMIC Power Amplifier Die

PSAT: 31 dBm (typical); Power gain: 18 dB (typical); PAE: 30 % (typical). Die dimensions: 2.35 × 1.5 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 5000; Maximum: 13000; Value: 5000–13000; Unit: MHz

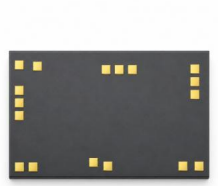
Saturated output power: Symbol: Psat; Typical: 31; Unit: dBm

Power gain: Symbol: Gp; Typical: 18; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±1.5; Unit: dB

TA = +25 °C; Vd = +16 V; Vg = -2.8 V

Product details Product datasheet



LCI-TRPA-5000-13000-PS31T-M

5000–13000 MHz GaN T/R MMIC Power Amplifier Die

PSAT: 31 dBm (typical); Power gain: 18 dB (typical); PAE: 30 % (typical). Die dimensions: 2.35 × 1.5 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 5000; Maximum: 13000; Value: 5000–13000; Unit: MHz

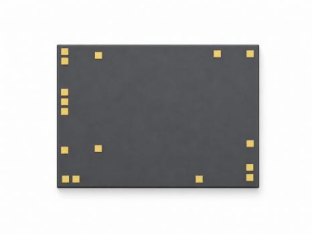
Saturated output power: Symbol: Psat; Typical: 31; Unit: dBm

Power gain: Symbol: Gp; Typical: 18; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±1.5; Unit: dB

TA = +25 °C; Vd = +16 V; Vg = -2.8 V

Product details Product datasheet



LCI-TRPA-8000-12000-PS41T

8000–12000 MHz GaN T/R MMIC Power Amplifier Die

PSAT: 41 dBm (typical); Power gain: 25 dB (typical); PAE: 38 % (typical). Die dimensions: 3.2 × 2.3 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

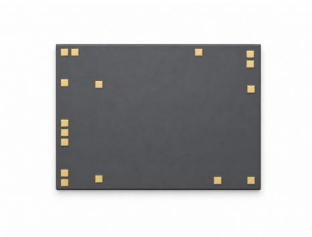
Saturated output power: Symbol: Psat; Typical: 41; Unit: dBm

Power gain: Symbol: Gp; Typical: 25; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-TRPA-8000-12000-PS41T-M

8000–12000 MHz GaN T/R MMIC Power Amplifier Die

PSAT: 41 dBm (typical); Power gain: 25 dB (typical); PAE: 38 % (typical). Die dimensions: 3.2 × 2.3 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

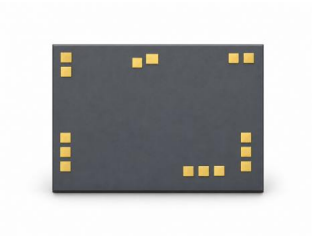
Saturated output power: Symbol: Psat; Typical: 41; Unit: dBm

Power gain: Symbol: Gp; Typical: 25; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.5; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-TRPA-9000-10000-PS35T

9000–10000 MHz GaN T/R MMIC Power Amplifier Die

PSAT: 35 dBm (typical); Power gain: 21 dB (typical); PAE: 35 % (typical). Die dimensions: 2.1 × 1.5 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 9000; Maximum: 10000; Value: 9000–10000; Unit: MHz

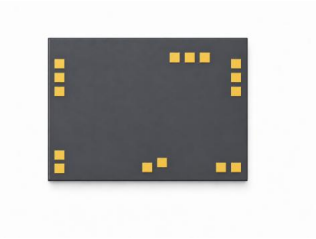
Saturated output power: Symbol: Psat; Typical: 35; Unit: dBm

Power gain: Symbol: Gp; Typical: 21; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.2; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-TRPA-9000-10000-PS35T-M

9000–10000 MHz GaN T/R MMIC Power Amplifier Die

PSAT: 35 dBm (typical); Power gain: 21 dB (typical); PAE: 35 % (typical). Die dimensions: 2.1 × 1.5 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 9000; Maximum: 10000; Value: 9000–10000; Unit: MHz

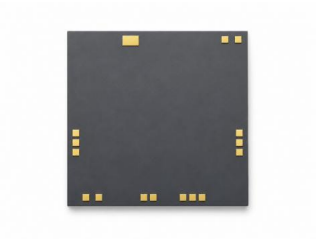
Saturated output power: Symbol: Psat; Typical: 35; Unit: dBm

Power gain: Symbol: Gp; Typical: 21; Unit: dB

Power-gain flatness: Symbol: ΔGp; Maximum: ±0.2; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V

Product details Product datasheet



LCI-TRPA-300-6000-PS39T

300–6000 MHz GaN T/R MMIC Power Amplifier Die

pulsed: PSAT: 38.7 dBm (minimum) / 39 dBm (typical) / 40.5 dBm (maximum); Power gain: 10.7 dB (minimum) / 11 dB (typical) / 12.5 dB (maximum); PAE: 30 % (minimum) / 35 % (typical) / 53 % (maximum). Die dimensions: 3.1 × 3.1 × 0.1 mm.

Operating frequency: Symbol: f; Minimum: 300; Maximum: 6000; Value: 300–6000; Unit: MHz

Saturated output power: Symbol: Psat; Minimum: 38.7; Typical: 39; Maximum: 40.5; Unit: dBm

Power gain: Symbol: Gp; Minimum: 10.7; Typical: 11; Maximum: 12.5; Unit: dB

Power-gain flatness: Symbol: ΔGp; Typical: ±0.9; Unit: dB

TA = +25 °C; Vd = +28 V; Vg = -2.6 V; pulsed

Product details Product datasheet



LCI-APC-8000-12000-D-G7p5MIN

8000–12000 MHz GaAs MMIC Amplitude and Phase Control RF Front-End Die

Phase step: 5.625 °; Attenuation range: 0–31.5 dB; Output 1 dB compression power: 11 dBm (minimum) / 13 dBm (typical). Die dimensions: 3.8 × 4.7 × 0.1 mm.

Operating frequency: Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

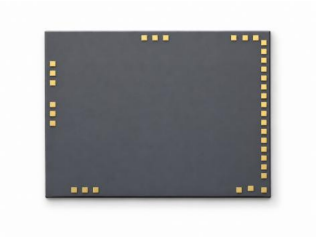
Small-signal gain: Minimum: 7.5; Maximum: 10; Value: TX / RX; Unit: dB

Isolation: Minimum: 35; Unit: dB

Attenuation range: Value: 0–31.5; Unit: dB

TA = +25 °C; f(Typ) = 10000 MHz; f(Min/Max) = 8000–12000 MHz

Product details Product datasheet



LCI-APC-7000-13000

7000–13000 MHz GaAs MMIC Amplitude and Phase Control RF Front-End Die

Phase step: 5.625 ° (typical); Attenuation range: 0.5 dB (minimum) / 31.5 dB (maximum); Small-signal gain: 12 dB (typical) (RX). Die dimensions: 4.55 × 3.54 × 0.1 mm.

Operating frequency: Minimum: 7000; Maximum: 13000; Value: 7000–13000; Unit: MHz

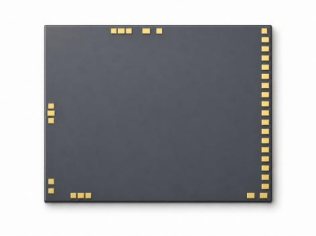
Small-signal gain: Typical: 12; Value: RX; Unit: dB

Output 1 dB compression power: Typical: 11; Value: RX; Unit: dBm

Saturated output power: Typical: 24; Value: TX; Unit: dBm

TA = +25 °C

Product details Product datasheet



LCI-APC-5000-6000

5000–6000 MHz GaAs MMIC Amplitude and Phase Control RF Front-End Die — Rx 13 dB / Tx 27 dB (typical)

5000–6000 MHz; Rx 13 dB / Tx 27 dB (typical); Rx P1dB ≥ 10 dBm; Tx PSAT ≥ 23 dBm.

Operating frequency: Symbol: f; Minimum: 5000; Maximum: 6000; Value: 5000–6000; Unit: MHz

Phase shift range: Minimum: 5.625; Maximum: 354.375; Unit: °

Attenuation range: Minimum: 0.5; Maximum: 31.5; Unit: dB

Small-signal gain (Rx): Typical: 13; Unit: dB

TA = +25 °C; VS = -5 V; Vd1 = Vd2 = +5 V

Product details Product datasheet



LCI-APC-8000-12000-D-RXG10T

8000–12000 MHz GaAs MMIC Amplitude and Phase Control RF Front-End Die — Rx 10 dB / Tx 26 dB (typical)

8000–12000 MHz; Rx 10 dB / Tx 26 dB (typical); Rx P1dB ≥ 13.5 dBm; Tx PSAT ≥ 25 dBm.

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

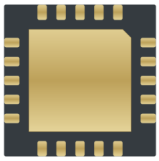
Phase shift range: Minimum: 5.625; Maximum: 354.375; Unit: °

Attenuation range: Minimum: 0.5; Maximum: 31.5; Unit: dB

Small-signal gain (Rx): Typical: 10; Unit: dB

TA = +25 °C; VS = -5 V; Vd1 = Vd2 = +5 V

Product details Product datasheet



LCI-BDA-8000-18000-RXP1DB23T

8000–18000 MHz Bidirectional RF Front-End IC — RX / TX P1dB 23 dBm (typical)

8000–18000 MHz; Small-signal gain (Rx) 20 dB (typical); Small-signal gain (Tx) 20 dB (typical); Output 1 dB compression power (Rx) 23 dBm (typical); Output 1 dB compression power (Tx) 23 dBm (typical).

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 18000; Value: 8000–18000; Unit: MHz

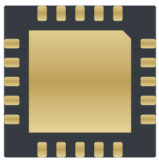
Small-signal gain (Rx): Symbol: Gain; Typical: 20; Unit: dB; Notes: RX

Small-signal gain (Tx): Symbol: Gain; Typical: 20; Unit: dB; Notes: TX

Output 1 dB compression power (Rx): Symbol: P_1; Typical: 23; Unit: dBm; Notes: RX

TA = +25 °C; VD = +5 V; Pin = -20 dBm

Product details Product datasheet



LCI-BDA-6000-18000-RXP1DB20T

6000–18000 MHz Bidirectional RF Front-End IC — RX / TX P1dB 20 dBm (typical)

6000–18000 MHz; Small-signal gain (Rx) 18 dB (typical); Small-signal gain (Tx) 18 dB (typical); Output 1 dB compression power (Rx) 20 dBm (typical); Output 1 dB compression power (Tx) 20 dBm (typical).

Operating frequency: Symbol: f; Minimum: 6000; Maximum: 18000; Value: 6000–18000; Unit: MHz

Small-signal gain (Rx): Symbol: Gain; Typical: 18; Unit: dB; Notes: RX

Small-signal gain (Tx): Symbol: Gain; Typical: 18; Unit: dB; Notes: TX

Output 1 dB compression power (Rx): Symbol: P_1; Typical: 20; Unit: dBm; Notes: RX

TA = +25 °C; VD = +5 V; Pin = -20 dBm

Product details Product datasheet

Bare Die and Chip-Scale RF Devices



LCI-LIM-12000-18000-PIP43MAX

12000–18000 MHz GaAs PIN RF Limiter Die

Insertion loss: 0.6 dB (typical) / 0.7 dB (maximum); Limiting level: 16.5 dBm (typical) / 17.5 dBm (maximum); Maximum pulsed input power: 43 dBm (maximum) (τ = 1 ms; D = 20%). Die dimensions: 1.4 × 0.8 × 0.1 mm.

Operating frequency: Minimum: 12000; Maximum: 18000; Value: 12000–18000; Unit: MHz

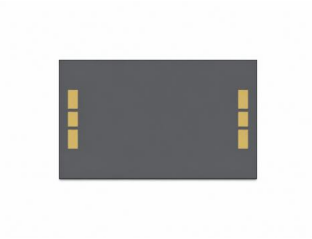
Insertion loss: Typical: 0.6; Maximum: 0.7; Unit: dB

Input VSWR: Typical: 1.4

Output VSWR: Typical: 1.4

TA = +25 °C

Product details Product datasheet



LCI-LIM-5000-6000

5000–6000 MHz GaAs PIN RF Limiter Die

Insertion loss: 0.45 dB (typical) / 0.5 dB (maximum); Limiting level: 18.5 dBm (typical) / 19.5 dBm (maximum); Maximum pulsed input power: 49 dBm (maximum) (τ = 2 ms; D = 20%); Maximum pulsed input power: 50 dBm (maximum) (τ = 300 µs; D = 30%). Die dimensions: 2 × 1.2 × 0.1 mm.

Operating frequency: Minimum: 5000; Maximum: 6000; Value: 5000–6000; Unit: MHz

Insertion loss: Typical: 0.45; Maximum: 0.5; Unit: dB

Input VSWR: Typical: 1.2; Maximum: 1.3

Output VSWR: Typical: 1.2; Maximum: 1.3

TA = +25 °C

Product details Product datasheet



LCI-LIM-8000-12000-PIP42MAX

8000–12000 MHz GaAs PIN RF Limiter Die

Insertion loss: 0.5 dB (typical); Limiting level: 16 dBm (typical) / 17 dBm (maximum); Maximum pulsed input power: 42 dBm (maximum) (τ = 300 µs; D = 30%). Die dimensions: 2 × 1.2 × 0.1 mm.

Operating frequency: Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

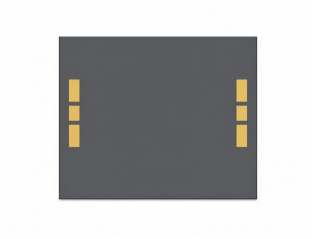
Insertion loss: Typical: 0.5; Unit: dB

Input VSWR: Typical: 1.3

Output VSWR: Typical: 1.3

TA = +25 °C

Product details Product datasheet



LCI-LIM-2000-6000-PIP43MAX

2000–6000 MHz GaAs PIN RF Limiter Die

Insertion loss: 0.3 dB (typical) / 0.4 dB (maximum); Limiting level: 15 dBm (typical) / 16 dBm (maximum); Maximum pulsed input power: 43 dBm (maximum) (τ = 200 µs; D = 20%). Die dimensions: 1.8 × 1.5 × 0.1 mm.

Operating frequency: Minimum: 2000; Maximum: 6000; Value: 2000–6000; Unit: MHz

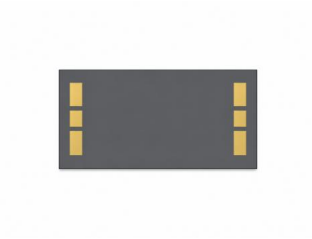
Insertion loss: Typical: 0.3; Maximum: 0.4; Unit: dB

Input VSWR: Typical: 1.4

Output VSWR: Typical: 1.4

TA = +25 °C

Product details Product datasheet



LCI-LIM-6000-18000-PIP42MAX

6000–18000 MHz GaAs PIN RF Limiter Die

Insertion loss: 0.8 dB (typical); Limiting level: 16.5 dBm (typical) / 17.5 dBm (maximum); Maximum pulsed input power: 42 dBm (maximum) (τ = 300 µs; D = 30%). Die dimensions: 1.6 × 0.8 × 0.1 mm.

Operating frequency: Minimum: 6000; Maximum: 18000; Value: 6000–18000; Unit: MHz

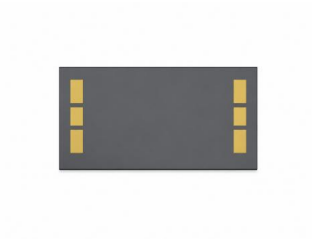
Insertion loss: Typical: 0.8; Unit: dB

Input VSWR: Typical: 1.6

Output VSWR: Typical: 1.6

TA = +25 °C

Product details Product datasheet



LCI-LIM-6000-18000-PIP41MAX

6000–18000 MHz GaAs PIN RF Limiter Die

Insertion loss: 0.6 dB (typical); Limiting level: 16 dBm (typical) / 17 dBm (maximum); Maximum pulsed input power: 41 dBm (maximum) (τ = 300 µs; D = 30%). Die dimensions: 1.6 × 0.85 × 0.1 mm.

Operating frequency: Minimum: 6000; Maximum: 18000; Value: 6000–18000; Unit: MHz

Insertion loss: Typical: 0.6; Unit: dB

Input VSWR: Typical: 1.5

Output VSWR: Typical: 1.5

TA = +25 °C

Product details Product datasheet



LCI-LIM-8000-12000-PIP48MAX

8000–12000 MHz GaAs PIN RF Limiter Die

Insertion loss: 0.8 dB (typical); Limiting level: 16 dBm (typical) / 17 dBm (maximum); Maximum pulsed input power: 48 dBm (maximum) (τ = 300 µs; D = 30%); Maximum input power: 46 dBm (maximum) (CW). Die dimensions: 1.85 × 1.1 × 0.1 mm.

Operating frequency: Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

Insertion loss: Typical: 0.8; Unit: dB

Input VSWR: Typical: 1.5

Output VSWR: Typical: 1.5

TA = +25 °C

Product details Product datasheet



LCI-LIM-DC-14000-PICW37MAX

DC–14000 MHz GaAs PIN RF Limiter Die

Insertion loss: 0.4 dB (typical) / 0.5 dB (maximum); Limiting level: 16 dBm (typical) / 17 dBm (maximum); Maximum input power: 37 dBm (maximum) (CW). Die dimensions: 1.25 × 0.65 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 14000; Value: DC–14000; Unit: MHz

Insertion loss: Typical: 0.4; Maximum: 0.5; Unit: dB

Input VSWR: Typical: 1.3

Output VSWR: Typical: 1.3

TA = +25 °C

Product details Product datasheet



LCI-LIM-8000-12000-PIP45MAX

8000–12000 MHz GaAs PIN RF Limiter Die

Insertion loss: 0.6 dB (typical) / 0.7 dB (maximum); Limiting level: 15 dBm (typical) / 16 dBm (maximum); Maximum pulsed input power: 45 dBm (maximum) (τ = 300 µs; D = 30%). Die dimensions: 2 × 1.1 × 0.1 mm.

Operating frequency: Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

Insertion loss: Typical: 0.6; Maximum: 0.7; Unit: dB

Input VSWR: Typical: 1.6

Output VSWR: Typical: 1.6

TA = +25 °C

Product details Product datasheet



LCI-LIM-8000-12000-PIP37MAX

8000–12000 MHz GaAs PIN RF Limiter Die

Insertion loss: 0.3 dB (typical); Limiting level: 17 dBm (typical) / 18 dBm (maximum); Maximum pulsed input power: 37 dBm (maximum) (τ = 300 µs; D = 30%). Die dimensions: 1.6 × 0.9 × 0.1 mm.

Operating frequency: Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

Insertion loss: Typical: 0.3; Unit: dB

Input VSWR: Typical: 1.2; Maximum: 1.3

Output VSWR: Typical: 1.2; Maximum: 1.3

TA = +25 °C

Product details Product datasheet



LCI-LIM-8000-12000-PIP37MAX-M

8000–12000 MHz GaAs PIN RF Limiter Die

Insertion loss: 0.3 dB (typical); Limiting level: 17 dBm (typical) / 18 dBm (maximum); Maximum pulsed input power: 37 dBm (maximum) (τ = 300 µs; D = 30%). Die dimensions: 1.6 × 0.9 × 0.1 mm.

Operating frequency: Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

Insertion loss: Typical: 0.3; Unit: dB

Input VSWR: Typical: 1.2; Maximum: 1.3

Output VSWR: Typical: 1.2; Maximum: 1.3

TA = +25 °C

Product details Product datasheet



LCI-LIM-10000-18000-PIP45MAX

10000–18000 MHz GaAs PIN RF Limiter Die

Insertion loss: 0.8 dB (typical); Limiting level: 17 dBm (typical) / 18 dBm (maximum); Maximum pulsed input power: 45 dBm (maximum) (τ = 200 µs; D = 30%). Die dimensions: 1.6 × 0.85 × 0.1 mm.

Operating frequency: Minimum: 10000; Maximum: 18000; Value: 10000–18000; Unit: MHz

Insertion loss: Typical: 0.8; Unit: dB

Input VSWR: Typical: 1.6; Maximum: 1.8

Output VSWR: Typical: 1.6; Maximum: 1.8

TA = +25 °C

Product details Product datasheet



LCI-LIM-DC-6000-PIP45MAX

DC–6000 MHz GaAs PIN RF Limiter Die

Insertion loss: 0.35 dB (typical) / 0.4 dB (maximum); Limiting level: 15 dBm (typical) / 16 dBm (maximum); Maximum pulsed input power: 45 dBm (maximum) (τ = 300 µs; D = 30%). Die dimensions: 2.1 × 1.25 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 6000; Value: DC–6000; Unit: MHz

Insertion loss: Typical: 0.35; Maximum: 0.4; Unit: dB

Input VSWR: Typical: 1.4; Maximum: 1.5

Output VSWR: Typical: 1.4; Maximum: 1.5

TA = +25 °C

Product details Product datasheet



LCI-LIM-2000-4000-PIP51MAX

2000–4000 MHz GaAs PIN RF Limiter Die

Insertion loss: 0.4 dB (typical); Limiting level: 16 dBm (typical) / 17 dBm (maximum); Maximum pulsed input power: 51 dBm (maximum) (τ = 100 µs; D = 10%); Maximum input power: 48 dBm (maximum) (CW). Die dimensions: 2.6 × 1.5 × 0.1 mm.

Operating frequency: Minimum: 2000; Maximum: 4000; Value: 2000–4000; Unit: MHz

Insertion loss: Typical: 0.4; Unit: dB

Input VSWR: Typical: 1.3

Output VSWR: Typical: 1.3

TA = +25 °C

Product details Product datasheet



LCRES-R15OHM

15 Ω GaAs thin-film resistor die

Resistance: 15 Ω (typical); Linear operating current: 0.35 A (typical); Maximum allowable current: 0.8 A (maximum). Plan-view die dimensions: 0.5 × 0.5 mm.

Resistor count: Value: 1

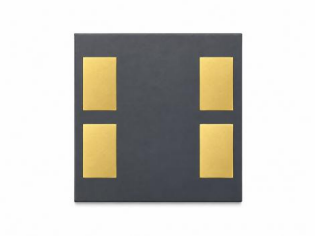
Terminal count: Value: 2

Resistance: Typical: 15; Unit: Ω

Resistance tolerance: Typical: ±5; Unit: %

TA = +25 °C

Product details Product datasheet



LCRES-N2-R20OHM

2 × 20 Ω GaAs thin-film resistor die

Resistance: 20 / 20 Ω (typical); Linear operating current: 0.165 / 0.165 A (typical); Maximum allowable current: 0.33 A (maximum). Plan-view die dimensions: 0.5 × 0.5 mm.

Resistor count: Value: 2

Terminal count: Value: 4

Resistance: Typical: 20 / 20; Unit: Ω

Resistance tolerance: Typical: ±5; Unit: %

TA = +25 °C

Product details Product datasheet



LCRES-R50OHM

50 Ω GaAs thin-film resistor die

Resistance: 50 Ω (typical); Linear operating current: 0.2 A (typical); Maximum allowable current: 0.6 A (maximum). Plan-view die dimensions: 0.5 × 0.5 mm.

Resistor count: Value: 1

Terminal count: Value: 2

Resistance: Typical: 50; Unit: Ω

Resistance tolerance: Typical: ±5; Unit: %

TA = +25 °C

Product details Product datasheet



LCRES-R1000OHM

1000 Ω GaAs thin-film resistor die

Resistance: 1000 Ω (typical); Linear operating current: 0.04 A (typical); Maximum allowable current: 0.08 A (maximum). Plan-view die dimensions: 0.5 × 0.5 mm.

Resistor count: Value: 1

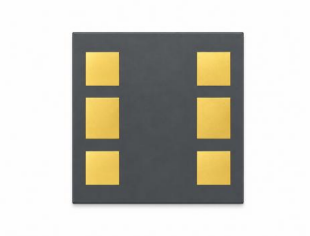
Terminal count: Value: 2

Resistance: Typical: 1000; Unit: Ω

Resistance tolerance: Typical: ±5; Unit: %

TA = +25 °C

Product details Product datasheet



LCCAP-C10PF

10 pF GaAs capacitor die

Capacitance: 10 pF (typical); Withstand voltage: 50 V (typical). Die dimensions: 0.5 × 0.5 × 0.1 mm.

Capacitance: Typical: 10; Unit: pF; TA = +25 °C

Withstand voltage: Typical: 50; Unit: V; TA = +25 °C

Breakdown voltage: Value: 80 (Vb); Unit: V

Storage temperature: Minimum: -65; Maximum: 150; Unit: °C

Product details Product datasheet



LCEQ-8000-12000-D

8000–12000 MHz GaAs slope equalizer die

Equalization amount: 2 dB; Insertion loss @ 8000 MHz: 2.6 dB; Insertion loss @ 12000 MHz: 0.7 dB. Die dimensions: 0.8 × 0.8 × 0.1 mm.

Operating frequency: Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

Equalization amount: Value: 2; Unit: dB

Insertion loss @ 8000 MHz: Value: 2.6; Unit: dB

Insertion loss @ 12000 MHz: Value: 0.7; Unit: dB

Product details Product datasheet



LCEQ-2000-6000-D

2000–6000 MHz GaAs slope equalizer die

Equalization amount: 5.5 dB; Insertion loss @ 2000 MHz: 0.6 dB; Insertion loss @ 6000 MHz: 6.1 dB. Die dimensions: 0.8 × 0.9 × 0.1 mm.

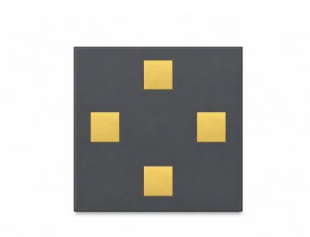
Operating frequency: Minimum: 2000; Maximum: 6000; Value: 2000–6000; Unit: MHz

Equalization amount: Value: 5.5; Unit: dB

Insertion loss @ 2000 MHz: Value: 0.6; Unit: dB

Insertion loss @ 6000 MHz: Value: 6.1; Unit: dB

Product details Product datasheet



LCXOV-DC-40000-D

DC–40000 MHz GaAs RF crossover die

Insertion loss: 0.4 dB (typical); Isolation: 30 dB (typical); Return loss: 20 dB (typical). Die dimensions: 0.6 × 0.6 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 40000; Value: DC–40000; Unit: MHz

Insertion loss: Typical: 0.4; Unit: dB

Isolation: Typical: 30; Unit: dB

Return loss: Typical: 20; Unit: dB

TA = +25 °C

Product details Product datasheet



LCBPF-17000-19000

17000–19000 MHz GaAs Bandpass Filter Die — IL 2.7 dB (typical)

17000–19000 MHz; Insertion loss 2.7 dB (typical).

Operating frequency: Symbol: f; Minimum: 17000; Maximum: 19000; Value: 17000–19000; Unit: MHz

Center frequency: Typical: 18000; Unit: MHz

Insertion loss: Typical: 2.7; Unit: dB

Passband ripple: Typical: 0.5; Unit: dB

TA = +25 °C

Product details Product datasheet

RF Switch ICs



LCI-SW-1000-12000-SPDT

1000–12000 MHz GaN SPDT MMIC Switch Die

Insertion loss: 1 dB (typical); Isolation: 34 dB (minimum) / 63 dB (maximum); Input power at 0.2 dB compression: 43 dBm (typical). Die dimensions: 2.45 × 1.2 × 0.1 mm.

Operating frequency: Minimum: 1000; Maximum: 12000; Value: 1000–12000; Unit: MHz

Insertion loss: Typical: 1; Unit: dB

Isolation: Minimum: 34; Maximum: 63; Unit: dB

Input power at 0.2 dB compression: Typical: 43; Unit: dBm

TA = +25 °C

Product details Product datasheet



LCI-SW-12000-18000-SPDT

12000–18000 MHz GaN SPDT MMIC Switch Die — IL 1 dB (typical)

12000–18000 MHz; Insertion loss 1 dB (typical); Isolation 38 dB (typical); P0.2dB 44 dBm (typical).

Operating frequency: Symbol: f; Minimum: 12000; Maximum: 18000; Value: 12000–18000; Unit: MHz

Insertion loss: Typical: 1; Maximum: 1.2; Unit: dB

Isolation: Minimum: 36; Typical: 38; Unit: dB

Input power at 0.2 dB compression: Typical: 44; Unit: dBm

TA = +25 °C

Product details Product datasheet



LCI-SW-32000-38000-SPDT

32000–38000 MHz SPDT MMIC Switch Die — IL 1 dB (typical)

32000–38000 MHz; Insertion loss 1 dB (typical); Isolation 20 dB (typical); P0.2dB 42 dBm (typical).

Operating frequency: Symbol: f; Minimum: 32000; Maximum: 38000; Value: 32000–38000; Unit: MHz

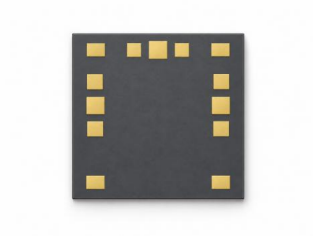
Insertion loss: Typical: 1; Unit: dB

Isolation: Typical: 20; Unit: dB

Input power at 0.2 dB compression: Typical: 42; Unit: dBm

Von = -28 V; Voff = 0 V; TA = +25 °C

Product details Product datasheet



LCI-SW-2000-18000-SPDT

2000–18000 MHz SPDT MMIC Switch Die — IL 0.9 dB (typical)

2000–18000 MHz; Insertion loss 0.9 dB (typical); Isolation 23 dB (typical); P0.2dB 37 dBm (typical).

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 18000; Value: 2000–18000; Unit: MHz

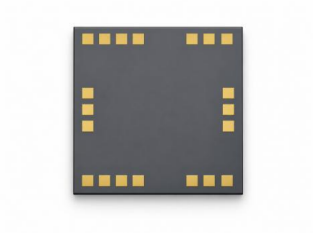
Insertion loss: Typical: 0.9; Unit: dB

Isolation: Typical: 23; Unit: dB

Input power at 0.2 dB compression: Typical: 37; Unit: dBm

Von = +28 V; Voff = 0 V; TA = +25 °C

Product details Product datasheet



LCI-SW-100-20000-SP3T-D

100–20000 MHz GaAs SP3T MMIC Switch Die — IL ≤ 2.8 dB (2000–20000 MHz)

100–20000 MHz; Insertion loss (100–2000 MHz) ≤ 1.4 dB; Isolation (100–2000 MHz) ≤ 65 dB.

Operating frequency: Symbol: f; Minimum: 100; Maximum: 20000; Value: 100–20000; Unit: MHz

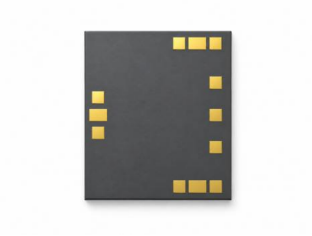
Insertion loss (100–2000 MHz): Maximum: 1.4; Value: f = 100–2000 MHz; Unit: dB

Insertion loss (2000–20000 MHz): Maximum: 2.8; Value: f = 2000–20000 MHz; Unit: dB

Isolation (100–2000 MHz): Maximum: 65; Value: f = 100–2000 MHz; Unit: dB

TA = +25 °C

Product details Product datasheet



LCI-SW-100-20000-SPDT-D-IL1p6T

100–20000 MHz GaAs SPDT MMIC Switch Die — IL 1.6 dB (typical)

100–20000 MHz; Insertion loss 1.6 dB (typical); Isolation 45 dB (typical).

Operating frequency: Symbol: f; Minimum: 100; Maximum: 20000; Value: 100–20000; Unit: MHz; TA = +25 °C

Insertion loss: Typical: 1.6; Unit: dB; TA = +25 °C

Isolation: Typical: 45; Unit: dB; TA = +25 °C

Negative-supply quiescent current: Typical: 0.0012; Unit: A

Product details Product datasheet



LCI-SW-8000-12000-SPDT

8000–12000 MHz GaN SPDT MMIC Switch Die — IL 0.9 dB (typical)

8000–12000 MHz; Insertion loss 0.9 dB (typical); Isolation 45 dB (typical); P0.2dB 46 dBm (typical).

Operating frequency: Symbol: f; Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

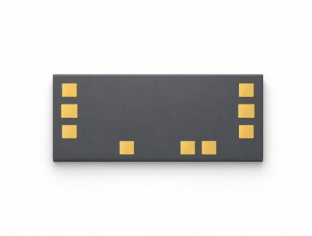
Insertion loss: Typical: 0.9; Unit: dB

Isolation: Typical: 45; Maximum: 50; Unit: dB

Input power at 0.2 dB compression: Typical: 46; Unit: dBm

TA = +25 °C

Product details Product datasheet



LCI-SW-100-20000-SPST-D

100–20000 MHz GaAs SPST MMIC Switch Die — IL ≤ 1.2 dB

100–20000 MHz; Insertion loss ≤ 1.2 dB; Isolation 60 dB (typical).

Operating frequency: Symbol: f; Minimum: 100; Maximum: 20000; Value: 100–20000; Unit: MHz

Insertion loss: Maximum: 1.2; Unit: dB

Isolation: Typical: 60; Unit: dB

Input/output VSWR (on): Typical: 1.1

TA = +25 °C

Product details Product datasheet



LCI-SW-2700-3500-SPDT

2700–3500 MHz GaN SPDT MMIC Switch Die — IL 0.7 dB (typical)

2700–3500 MHz; Insertion loss 0.7 dB (typical); Isolation 41 dB (typical); P0.2dB 51 dBm (typical).

Operating frequency: Symbol: f; Minimum: 2700; Maximum: 3500; Value: 2700–3500; Unit: MHz

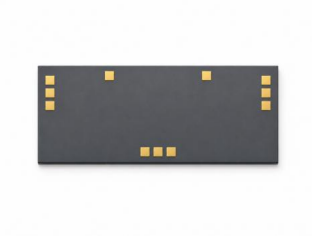
Insertion loss: Typical: 0.7; Unit: dB

Isolation: Typical: 41; Maximum: 43; Unit: dB

Input power at 0.2 dB compression: Typical: 51; Unit: dBm

TA = +25 °C

Product details Product datasheet



LCI-SW-100-6000-SPDT

100–6000 MHz GaN SPDT MMIC Switch Die — IL 0.7 dB (typical)

100–6000 MHz; Insertion loss 0.7 dB (typical); Isolation 45 dB (typical); P0.2dB 47 dBm (typical).

Operating frequency: Symbol: f; Minimum: 100; Maximum: 6000; Value: 100–6000; Unit: MHz

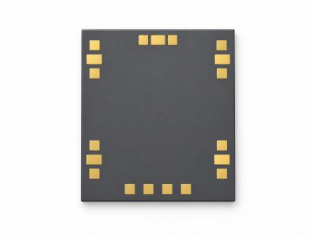
Insertion loss: Typical: 0.7; Maximum: 0.8; Unit: dB

Isolation: Typical: 45; Unit: dB

Input power at 0.2 dB compression: Typical: 47; Unit: dBm

TA = +25 °C

Product details Product datasheet



LCI-SW-100-20000-SP4T-D

100–20000 MHz GaAs SP4T MMIC Switch Die — IL −2 dB (typical)

100–20000 MHz; Insertion loss -2 dB (typical); Isolation -50 dB (typical).

Operating frequency: Symbol: f; Minimum: 100; Maximum: 20000; Value: 100–20000; Unit: MHz

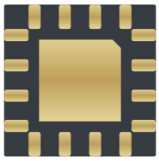
Insertion loss: Typical: -2; Unit: dB

Isolation: Typical: -50; Unit: dB

Input VSWR: Typical: 1.3

TA = +25 °C

Product details Product datasheet



LCI-SW-100-20000-SPST-C

100–20000 MHz RF Switch IC — SPST; TTL

100–20000 MHz; SPST; Insertion loss -1.8 dB (typical); Isolation 60 dB (typical).

Operating frequency: Symbol: f; Minimum: 100; Maximum: 20000; Value: 100–20000; Unit: MHz

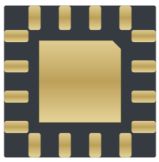
Insertion loss: Symbol: IL; Typical: -1.8; Unit: dB

Isolation: Symbol: ISO; Typical: 60; Unit: dB

Input/output VSWR (on): Typical: 1.14

TA = +25 °C

Product details Product datasheet



LCI-SW-100-20000-SP3T-C

100–20000 MHz RF Switch IC — SP3T; TTL

100–20000 MHz; SP3T; Insertion loss -3.1 dB (typical); Isolation 50 dB (typical).

Operating frequency: Symbol: f; Minimum: 100; Maximum: 20000; Value: 100–20000; Unit: MHz

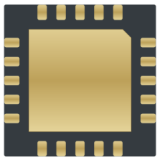
Insertion loss: Symbol: IL; Typical: -3.1; Unit: dB

Isolation: Symbol: ISO; Typical: 50; Unit: dB

Input/output VSWR (on): Typical: 1.14

TA = +25 °C

Product details Product datasheet



LCI-SW-100-20000-SP4T-C

100–20000 MHz RF Switch IC — SP4T; TTL

100–20000 MHz; SP4T; Insertion loss -2.6 dB (typical); Isolation -50 dB (typical).

Operating frequency: Symbol: f; Minimum: 100; Maximum: 20000; Value: 100–20000; Unit: MHz

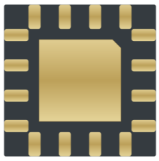
Insertion loss: Symbol: IL; Typical: -2.6; Unit: dB

Isolation: Symbol: ISO; Typical: -50; Unit: dB

Input VSWR: Typical: 1.3

TA = +25 °C

Product details Product datasheet



LCI-SW-100-20000-SPDT-C

100–20000 MHz RF Switch IC — SPDT; TTL

100–20000 MHz; SPDT; Insertion loss -2.2 dB (typical); Isolation -45 dB (typical).

Operating frequency: Symbol: f; Minimum: 100; Maximum: 20000; Value: 100–20000; Unit: MHz

Insertion loss: Symbol: IL; Typical: -2.2; Unit: dB

Isolation: Symbol: ISO; Typical: -45; Unit: dB

Input VSWR: Typical: 1.22

TA = +25 °C

Product details Product datasheet

RF Beamformer ICs



LCI-BF-14000-18000-4CH

14000–18000 MHz Four-Channel SiGe T/R Beamformer Die

Phase step: 5.625 °; Attenuation range: 0–31.5 dB; Switching time: 100 ns (maximum). Plan-view die dimensions: 5 × 6.2 mm.

Operating frequency: Minimum: 14000; Maximum: 18000; Value: 14000–18000; Unit: MHz

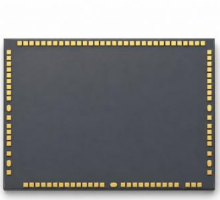
Input/output VSWR: Typical: 1.8

RMS phase error: Maximum: 3; Unit: °

RMS attenuation error: Maximum: 0.3; Unit: dB

TA = +25 °C

Product details Product datasheet



LCI-BF-8000-12000-2CH

8000–12000 MHz Dual-Channel Si T/R Beamformer Die

Phase step: 5.625 ° (typical); Attenuation step: 0.5 dB (typical). Die dimensions: 3.6 × 2.7 × 0.15 mm.

Operating frequency: Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

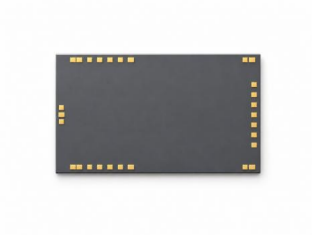
Phase-control resolution: Value: 6; Unit: bit

Attenuation-control resolution: Value: 6; Unit: bit

Phase shift range: Minimum: 0; Maximum: 360; Unit: °

CLK = 50 MHz; RFVDD = AVDD = DVDD = 3.3 V; TA = +27 °C

Product details Product datasheet



LCI-BF-3700-5000-2CH

3700–5000 MHz Dual-Channel GaAs MMIC Phase and Attenuation Control Die — 2 × 6-bit ϕ / 6-bit ATT

3700–5000 MHz; Insertion loss -13 dB (typical); 64-state RMS attenuation error 0.2 dB (typical); 64-state RMS phase error 2 ° (typical).

Operating frequency: Symbol: f; Minimum: 3700; Maximum: 5000; Value: 3700–5000; Unit: MHz

Insertion loss: Typical: -13; Unit: dB

Attenuation range: Maximum: 31.5; Unit: dB

64-state RMS attenuation error: Typical: 0.2; Unit: dB

TA = +25 °C; VEE = -5 V; Vd = +5 V

Product details Product datasheet

RF Phase Shifter ICs



LCI-PS-1200-1400-6B-D

1200–1400 MHz 6-Bit GaAs MMIC Digital Phase Shifter Die

RMS phase error: 0.5 ° (minimum) / 0.7 ° (typical) / 1 ° (maximum); Phase shift range: 5.625 ° (minimum) / 354.375 ° (maximum); Insertion loss: ≈5 dB. Die dimensions: 4 × 1.7 × 0.1 mm.

Operating frequency: Minimum: 1200; Maximum: 1400; Value: 1200–1400; Unit: MHz

Phase shift range: Minimum: 5.625; Maximum: 354.375; Unit: °

RMS phase error: Minimum: 0.5; Typical: 0.7; Maximum: 1; Unit: °

Phase-induced amplitude variation: Typical: ±0.5; Unit: dB

TA = +25 °C

Product details Product datasheet



LCI-PS-5000-6000-6B

5000–6000 MHz 6-Bit GaAs MMIC Digital Phase Shifter Die

RMS phase error: 1 ° (typical); Insertion loss: 7 dB (typical); Phase shift range: 5.625 ° (minimum) / 354.375 ° (maximum). Die dimensions: 3.1 × 1.5 × 0.1 mm.

Operating frequency: Minimum: 5000; Maximum: 6000; Value: 5000–6000; Unit: MHz

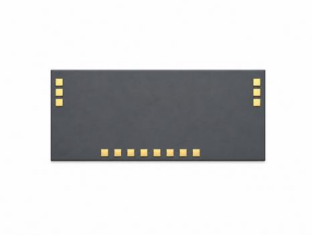
Insertion loss: Typical: 7; Unit: dB

Phase shift range: Minimum: 5.625; Maximum: 354.375; Unit: °

RMS phase error: Typical: 1; Unit: °

TA = +25 °C; VEE = -5 V

Product details Product datasheet



LCI-PS-2700-3500-6B

2700–3500 MHz 6-Bit GaAs MMIC Digital Phase Shifter Die

RMS phase error: 1 ° (typical); Insertion loss: 5.5 dB (typical); Phase shift range: 5.625 ° (minimum) / 354.375 ° (maximum). Die dimensions: 3.3 × 1.5 × 0.1 mm.

Operating frequency: Minimum: 2700; Maximum: 3500; Value: 2700–3500; Unit: MHz

Insertion loss: Typical: 5.5; Unit: dB

Phase shift range: Minimum: 5.625; Maximum: 354.375; Unit: °

RMS phase error: Typical: 1; Unit: °

TA = +25 °C; VEE = -5 V

Product details Product datasheet



LCI-PS-15000-23000-6B

15000–23000 MHz 6-Bit GaAs MMIC Digital Phase Shifter Die

RMS phase error: 1.4 ° (typical); Insertion loss: 9.5 dB (typical); Phase shift range: 5.625 ° (minimum) / 354.375 ° (maximum). Die dimensions: 3.1 × 1.1 × 0.1 mm.

Operating frequency: Minimum: 15000; Maximum: 23000; Value: 15000–23000; Unit: MHz

Insertion loss: Typical: 9.5; Unit: dB

Phase shift range: Minimum: 5.625; Maximum: 354.375; Unit: °

RMS phase error: Typical: 1.4; Unit: °

TA = +25 °C

Product details Product datasheet



LCI-PS-25000-33000-6B

25000–33000 MHz 6-Bit GaAs MMIC Digital Phase Shifter Die

RMS phase error: 1.6 ° (typical); Insertion loss: 9.5 dB (typical); Phase shift range: 5.625 ° (minimum) / 354.375 ° (maximum). Die dimensions: 3.1 × 1.1 × 0.1 mm.

Operating frequency: Minimum: 25000; Maximum: 33000; Value: 25000–33000; Unit: MHz

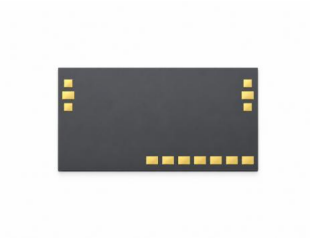
Insertion loss: Typical: 9.5; Unit: dB

Phase shift range: Minimum: 5.625; Maximum: 354.375; Unit: °

RMS phase error: Typical: 1.6; Unit: °

TA = +25 °C

Product details Product datasheet



LCI-PS-14000-18000-6B-D

14000–18000 MHz 6-Bit GaAs MMIC Digital Phase Shifter Die

RMS phase error: 1.2 ° (typical); Insertion loss: 7 dB (typical); Phase shift range: 5.625 ° (minimum) / 354.375 ° (maximum). Die dimensions: 2.5 × 1.3 × 0.1 mm.

Operating frequency: Minimum: 14000; Maximum: 18000; Value: 14000–18000; Unit: MHz

Insertion loss: Typical: 7; Unit: dB

Phase shift range: Minimum: 5.625; Maximum: 354.375; Unit: °

RMS phase error: Typical: 1.2; Unit: °

TA = +25 °C

Product details Product datasheet



LCI-PS-900-1400-6B-D

900–1400 MHz 6-Bit GaAs MMIC Digital Phase Shifter Die

RMS phase error: 1.5 ° (typical); Insertion loss: 5 dB (typical); Phase shift range: 5.625 ° (minimum) / 354.375 ° (maximum). Die dimensions: 3.6 × 1.3 × 0.1 mm.

Operating frequency: Minimum: 900; Maximum: 1400; Value: 900–1400; Unit: MHz

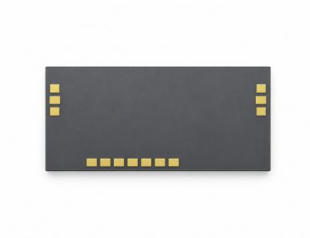
Insertion loss: Typical: 5; Unit: dB

Phase shift range: Minimum: 5.625; Maximum: 354.375; Unit: °

RMS phase error: Typical: 1.5; Unit: °

TA = +25 °C

Product details Product datasheet



LCI-PS-1200-1600-6B-D

1200–1600 MHz 6-Bit GaAs MMIC Digital Phase Shifter Die

RMS phase error: 0.8 ° (typical); Insertion loss: 4.3 dB (typical); Phase shift range: 5.625 ° (minimum) / 354.375 ° (maximum). Die dimensions: 3.3 × 1.6 × 0.1 mm.

Operating frequency: Minimum: 1200; Maximum: 1600; Value: 1200–1600; Unit: MHz

Insertion loss: Typical: 4.3; Unit: dB

Phase shift range: Minimum: 5.625; Maximum: 354.375; Unit: °

RMS phase error: Typical: 0.8; Unit: °

TA = +25 °C

Product details Product datasheet



LCI-PS-2000-8000-6B

2000–8000 MHz 6-Bit GaAs MMIC Digital Phase Shifter Die

RMS phase error: 2.2 ° (typical) / 3 ° (maximum); Insertion loss: 10 dB (typical) / 11.5 dB (maximum); Phase shift range: 5.625 ° (minimum) / 354.375 ° (maximum). Die dimensions: 5 × 1.75 × 0.1 mm.

Operating frequency: Minimum: 2000; Maximum: 8000; Value: 2000–8000; Unit: MHz

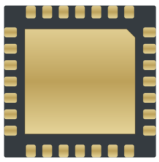
Insertion loss: Typical: 10; Maximum: 11.5; Unit: dB

Phase shift range: Minimum: 5.625; Maximum: 354.375; Unit: °

RMS phase error: Typical: 2.2; Maximum: 3; Unit: °

TA = +25 °C

Product details Product datasheet



LCI-PS-900-1400-6B-C

900–1400 MHz Digital Phase Shifter IC — 6-bit; RMS 1.5° (typical)

900–1400 MHz; 64-state RMS phase error 1.5 ° (typical); Phase-induced amplitude variation ±0.4 dB (typical); Input VSWR 1.5 (typical); Output VSWR 1.4 (typical).

Operating frequency: Symbol: f; Minimum: 900; Maximum: 1400; Value: 900–1400; Unit: MHz

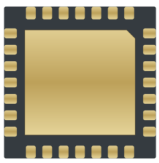
Phase shift range: Minimum: 5.625; Maximum: 354.375; Unit: °

Insertion loss: Typical: -5.4; Unit: dB

64-state RMS phase error: Typical: 1.5; Unit: °

TA = +25 °C

Product details Product datasheet



LCI-PS-1200-1400-6B-C

1200–1400 MHz Digital Phase Shifter IC — 6-bit; RMS 0.7° (typical)

1200–1400 MHz; 64-state RMS phase error 0.7 ° (typical); Phase-induced amplitude variation ±0.5 dB (typical); Input VSWR 1.4 (typical); Output VSWR 1.4 (typical).

Operating frequency: Symbol: f; Minimum: 1200; Maximum: 1400; Value: 1200–1400; Unit: MHz

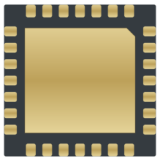
Phase shift range: Minimum: 5.625; Maximum: 354.375; Unit: °

Insertion loss: Typical: -5.4; Unit: dB

64-state RMS phase error: Typical: 0.7; Unit: °

TA = +25 °C

Product details Product datasheet



LCI-PS-1200-1600-6B-C

1200–1600 MHz Digital Phase Shifter IC — 6-bit; RMS 0.8° (typical)

1200–1600 MHz; 64-state RMS phase error 0.8 ° (typical); Phase-induced amplitude variation ±0.4 dB (typical); Input VSWR 1.4 (typical); Output VSWR 1.4 (typical).

Operating frequency: Symbol: f; Minimum: 1200; Maximum: 1600; Value: 1200–1600; Unit: MHz

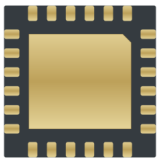
Phase shift range: Minimum: 5.625; Maximum: 354.375; Unit: °

Insertion loss: Typical: -4.7; Unit: dB

64-state RMS phase error: Typical: 0.8; Unit: °

TA = +25 °C

Product details Product datasheet



LCI-PS-14000-18000-6B-C

14000–18000 MHz Digital Phase Shifter IC — 6-bit; RMS 1.2° (typical)

14000–18000 MHz; 64-state RMS phase error 1.2 ° (typical); Phase-induced amplitude variation ±0.3 dB (typical); Input VSWR 1.5 (typical); Output VSWR 1.3 (typical).

Operating frequency: Symbol: f; Minimum: 14000; Maximum: 18000; Value: 14000–18000; Unit: MHz

Phase shift range: Minimum: 5.625; Unit: °

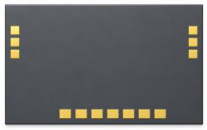
Insertion loss: Typical: -7.4; Unit: dB

64-state RMS phase error: Typical: 1.2; Unit: °

TA = +25 °C

Product details Product datasheet

Digital Attenuator ICs



LCI-ATT-14000-18000-6B-D

14000–18000 MHz 6-Bit GaAs MMIC Digital Attenuator Die

RMS attenuation error: 0.3 dB (typical); Insertion loss: 4 dB (maximum); Attenuation range: 0.5 dB (minimum) / 31.5 dB (maximum). Die dimensions: 2.5 × 1.5 × 0.1 mm.

Operating frequency: Minimum: 14000; Maximum: 18000; Value: 14000–18000; Unit: MHz

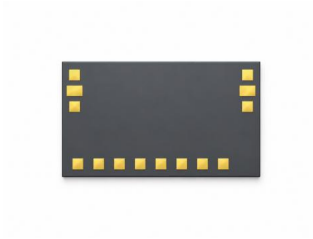
Insertion loss: Maximum: 4; Unit: dB

Attenuation range: Minimum: 0.5; Maximum: 31.5; Unit: dB

RMS attenuation error: Typical: 0.3; Unit: dB

TA = +25 °C

Product details Product datasheet



LCI-ATT-DC-8000-6B

DC–8000 MHz 6-Bit GaAs MMIC Digital Attenuator Die

RMS attenuation error: 0.2 dB (typical); Insertion loss: 1.6 dB (typical); Attenuation range: 0.5 dB (minimum) / 31.5 dB (maximum). Die dimensions: 1.9 × 1.1 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 8000; Value: DC–8000; Unit: MHz

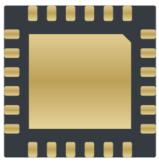
Insertion loss: Typical: 1.6; Unit: dB

Attenuation range: Minimum: 0.5; Maximum: 31.5; Unit: dB

RMS attenuation error: Typical: 0.2; Unit: dB

TA = +25 °C

Product details Product datasheet



LCI-ATT-100-8000-6B

100–8000 MHz Digital Step Attenuator IC — 6-bit; 0.5 dB

100–8000 MHz; Attenuation range 0.5–31.5 dB; Attenuation accuracy 0.2 dB (typical); Insertion loss 2 dB (typical).

Operating frequency: Symbol: f; Minimum: 100; Maximum: 8000; Value: 100–8000; Unit: MHz

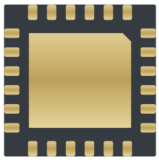
Insertion loss: Typical: 2; Unit: dB

Attenuation range: Minimum: 0.5; Maximum: 31.5; Unit: dB

Attenuation accuracy: Typical: 0.2; Unit: dB

TA = +25 °C

Product details Product datasheet



LCI-ATT-14000-18000-6B-C

14000–18000 MHz Digital Step Attenuator IC — 6-bit; 0.5 dB

14000–18000 MHz; Attenuation range 0.5–31.5 dB; Attenuation accuracy 0.3 dB (typical); Insertion loss 2 dB (typical).

Operating frequency: Symbol: f; Minimum: 14000; Maximum: 18000; Value: 14000–18000; Unit: MHz

Insertion loss: Typical: 2; Unit: dB

Attenuation range: Minimum: 0.5; Maximum: 31.5; Unit: dB

Attenuation accuracy: Typical: 0.3; Unit: dB

TA = +25 °C

Product details Product datasheet



LCI-TTD-5000-6000-4B

5000–6000 MHz 4-Bit GaAs MMIC Digital Time Delay Die

Time delay: 92.5 ps (typical) (T1; t_nom = 92.59 ps); Time delay: 737 ps (typical) (T4; t_nom = 740.74 ps); Insertion loss: 12 dB (typical) / 13 dB (maximum). Die dimensions: 4.5 × 4 × 0.1 mm.

Operating frequency: Minimum: 5000; Maximum: 6000; Value: 5000–6000; Unit: MHz

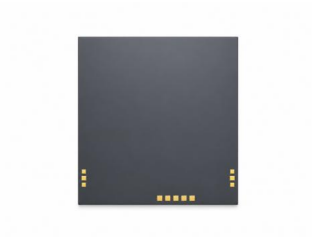
Insertion loss: Typical: 12; Maximum: 13; Unit: dB

Time delay (T1): Typical: 92.5; Value: T1; t_nom = 92.59 ps; Unit: ps

Time delay (T2): Typical: 184; Value: T2; t_nom = 185.185 ps; Unit: ps

TA = +25 °C; VEE = -5 V

Product details Product datasheet



LCI-TTD-8500-10500-4B

8500–10500 MHz 4-Bit GaAs MMIC Digital Time Delay Die

Time delay: 52.7 ps (typical) (T1; t_nom = 52 ps); Time delay: 416 ps (typical) (T4; t_nom = 416 ps); Insertion loss: 12 dB (typical) / 13 dB (maximum). Die dimensions: 4 × 4.2 × 0.1 mm.

Operating frequency: Minimum: 8500; Maximum: 10500; Value: 8500–10500; Unit: MHz

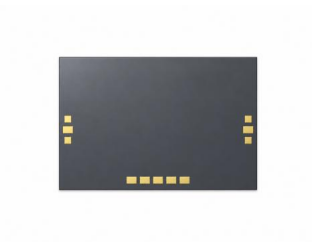
Insertion loss: Typical: 12; Maximum: 13; Unit: dB

Time delay (T1): Typical: 52.7; Value: T1; t_nom = 52 ps; Unit: ps

Time delay (T2): Typical: 102; Value: T2; t_nom = 104 ps; Unit: ps

TA = +25 °C; VEE = -5 V

Product details Product datasheet



LCI-TTD-8000-12000-3B

8000–12000 MHz 3-Bit GaAs MMIC Digital Time Delay Die

Time delay: 25 ps (typical) (T1; t_nom = 25 ps); Time delay: 102 ps (typical) (T3; t_nom = 100 ps); Insertion loss: 6 dB (typical) / 7 dB (maximum). Die dimensions: 3 × 2 × 0.1 mm.

Operating frequency: Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

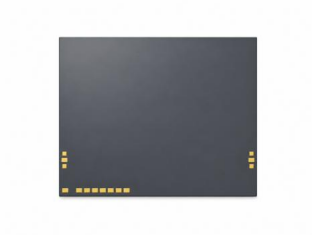
Insertion loss: Typical: 6; Maximum: 7; Unit: dB

Time delay (T1): Typical: 25; Value: T1; t_nom = 25 ps; Unit: ps

Time delay (T2): Typical: 49.5; Value: T2; t_nom = 50 ps; Unit: ps

TA = +25 °C; VEE = -5 V

Product details Product datasheet



LCI-TTD-200-2000-6B

200–2000 MHz 6-Bit GaAs MMIC Digital Time Delay Die

Time delay: 25 ps (typical) (T1; t_nom = 25 ps); Time delay: 800 ps (typical) (T6; t_nom = 800 ps); Insertion loss: 11 dB (maximum). Die dimensions: 5 × 4 × 0.1 mm.

Operating frequency: Minimum: 200; Maximum: 2000; Value: 200–2000; Unit: MHz

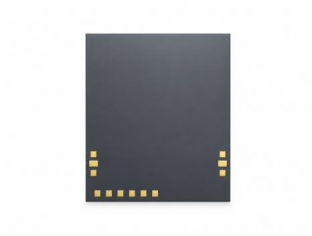
Insertion loss: Maximum: 11; Unit: dB

Time delay (T1): Typical: 25; Unit: ps; Notes: T1; t_nom = 25 ps

Time delay (T2): Typical: 50; Unit: ps; Notes: T2; t_nom = 50 ps

TA = +25 °C; VEE = -5 V

Product details Product datasheet



LCI-TTD-7000-13000-3B

7000–13000 MHz 3-Bit GaAs MMIC Digital Time Delay Die

Time delay: 52 ps (typical) (T1; t_nom = 52 ps); Time delay: 208 ps (typical) (T3; t_nom = 208 ps); Insertion loss: 9 dB (typical). Die dimensions: 2.5 × 2.9 × 0.1 mm.

Operating frequency: Minimum: 7000; Maximum: 13000; Value: 7000–13000; Unit: MHz

Insertion loss: Typical: 9; Unit: dB

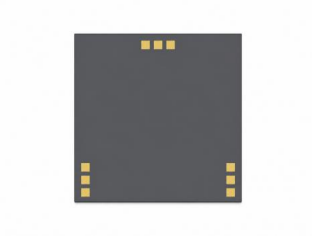
Time delay (T1): Typical: 52; Value: T1; t_nom = 52 ps; Unit: ps

Time delay (T2): Typical: 104; Value: T2; t_nom = 104 ps; Unit: ps

TA = +25 °C; VEE = -5 V

Product details Product datasheet

Integrated Passive Devices



LCDIV-2000-18000-2WAY-D-S2X2

2000–18000 MHz GaAs IPD 2-way 0° power divider die

Isolation: 20 dB (typical); Input VSWR: 1.3 (typical); Output VSWR: 1.3 (typical). Die dimensions: 2 × 2 × 0.1 mm.

Operating frequency: Minimum: 2000; Maximum: 18000; Value: 2000–18000; Unit: MHz

Isolation: Typical: 20; Unit: dB

Input VSWR: Typical: 1.3

Output VSWR: Typical: 1.3

TA = +25 °C

Product details Product datasheet



LCDIV-3700-5000-2WAY

3700–5000 MHz GaAs IPD 2-way 0° power divider die

Isolation: 20 dB (typical); Input VSWR: 1.2 (typical); Output VSWR: 1.2 (typical). Die dimensions: 0.8 × 1.3 × 0.1 mm.

Operating frequency: Minimum: 3700; Maximum: 5000; Value: 3700–5000; Unit: MHz

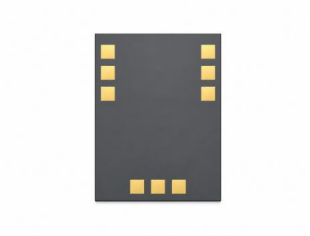
Isolation: Typical: 20; Unit: dB

Input VSWR: Typical: 1.2

Output VSWR: Typical: 1.2

TA = +25 °C

Product details Product datasheet



LCDIV-500-2700-2WAY

500–2700 MHz GaAs IPD 2-way 0° power divider die

Isolation: 14 dB (typical); Input VSWR: 1.3 (typical); Output VSWR: 1.3 (typical). Die dimensions: 0.9 × 1.2 × 0.1 mm.

Operating frequency: Minimum: 500; Maximum: 2700; Value: 500–2700; Unit: MHz

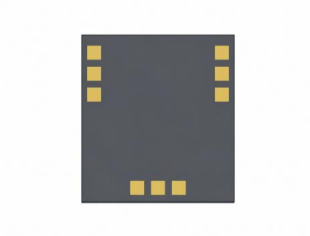
Isolation: Typical: 14; Unit: dB

Input VSWR: Typical: 1.3

Output VSWR: Typical: 1.3

TA = +25 °C

Product details Product datasheet



LCDIV-800-2000-2WAY

800–2000 MHz GaAs IPD 2-way 0° power divider die

Isolation: 18 dB (typical); Input VSWR: 1.3 (typical); Output VSWR: 1.3 (typical). Die dimensions: 1.1 × 1.2 × 0.1 mm.

Operating frequency: Minimum: 800; Maximum: 2000; Value: 800–2000; Unit: MHz

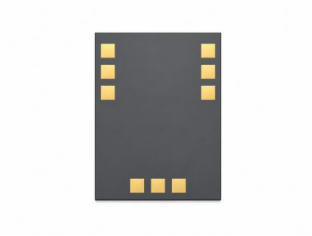
Isolation: Typical: 18; Unit: dB

Input VSWR: Typical: 1.3

Output VSWR: Typical: 1.3

TA = +25 °C

Product details Product datasheet



LCDIV-1000-4000-2WAY

1000–4000 MHz GaAs IPD 2-way 0° power divider die

Isolation: 18 dB (typical); Input VSWR: 1.4 (typical); Output VSWR: 1.4 (typical). Die dimensions: 0.9 × 1.2 × 0.1 mm.

Operating frequency: Minimum: 1000; Maximum: 4000; Value: 1000–4000; Unit: MHz

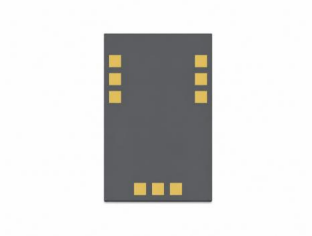
Isolation: Typical: 18; Unit: dB

Input VSWR: Typical: 1.4

Output VSWR: Typical: 1.4

TA = +25 °C

Product details Product datasheet



LCDIV-2000-6000-2WAY

2000–6000 MHz GaAs IPD 2-way 0° power divider die

Isolation: 20 dB (typical); Input VSWR: 1.3 (typical); Output VSWR: 1.2 (typical). Die dimensions: 0.9 × 1.4 × 0.1 mm.

Operating frequency: Minimum: 2000; Maximum: 6000; Value: 2000–6000; Unit: MHz

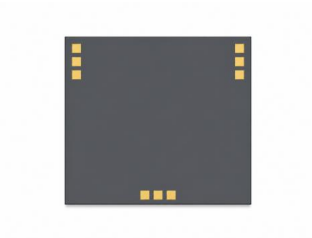
Isolation: Typical: 20; Unit: dB

Input VSWR: Typical: 1.3

Output VSWR: Typical: 1.2

TA = +25 °C

Product details Product datasheet



LCDIV-2000-18000-2WAY-D-S2p12X1p9

2000–18000 MHz GaAs IPD 2-way 0° power divider die

Isolation: 20 dB (typical); Input VSWR: 1.3 (typical); Output VSWR: 1.3 (typical). Die dimensions: 2.12 × 1.9 × 0.1 mm.

Operating frequency: Minimum: 2000; Maximum: 18000; Value: 2000–18000; Unit: MHz

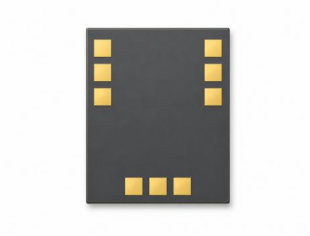
Isolation: Typical: 20; Unit: dB

Input VSWR: Typical: 1.3

Output VSWR: Typical: 1.3

TA = +25 °C

Product details Product datasheet



LCDIV-2700-3500-2WAY

2700–3500 MHz GaAs IPD 2-way 0° power divider die

Isolation: 30 dB (typical); Input VSWR: 1.1 (typical); Output VSWR: 1.1 (typical). Die dimensions: 0.9 × 1.1 × 0.1 mm.

Operating frequency: Minimum: 2700; Maximum: 3500; Value: 2700–3500; Unit: MHz

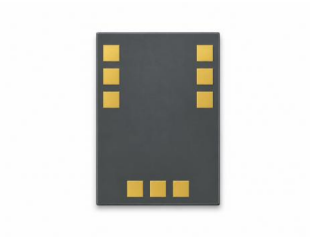
Isolation: Typical: 30; Unit: dB

Input VSWR: Typical: 1.1

Output VSWR: Typical: 1.1

TA = +25 °C

Product details Product datasheet



LCDIV-5000-7000-2WAY

5000–7000 MHz GaAs IPD 2-way 0° power divider die

Isolation: 25 dB (typical); Input VSWR: 1.1 (typical); Output VSWR: 1.1 (typical). Die dimensions: 0.8 × 1.1 × 0.1 mm.

Operating frequency: Minimum: 5000; Maximum: 7000; Value: 5000–7000; Unit: MHz

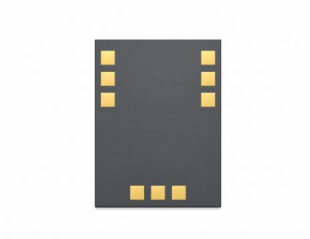
Isolation: Typical: 25; Unit: dB

Input VSWR: Typical: 1.1

Output VSWR: Typical: 1.1

TA = +25 °C

Product details Product datasheet



LCDIV-5000-13000-2WAY

5000–13000 MHz GaAs IPD 2-way 0° power divider die

Isolation: 25 dB (typical); Input VSWR: 1.3 (typical); Output VSWR: 1.2 (typical). Die dimensions: 0.9 × 1.2 × 0.1 mm.

Operating frequency: Minimum: 5000; Maximum: 13000; Value: 5000–13000; Unit: MHz

Isolation: Typical: 25; Unit: dB

Input VSWR: Typical: 1.3

Output VSWR: Typical: 1.2

TA = +25 °C

Product details Product datasheet



LCDIV-6000-18000-2WAY

6000–18000 MHz GaAs IPD 2-way 0° power divider die

Isolation: 20 dB (typical); Input VSWR: 1.2 (typical); Output VSWR: 1.2 (typical). Die dimensions: 0.8 × 1.3 × 0.1 mm.

Operating frequency: Minimum: 6000; Maximum: 18000; Value: 6000–18000; Unit: MHz

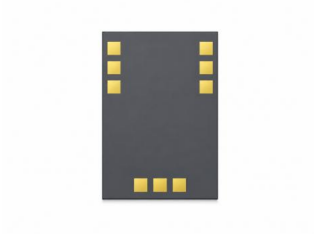
Isolation: Typical: 20; Unit: dB

Input VSWR: Typical: 1.2

Output VSWR: Typical: 1.2

TA = +25 °C

Product details Product datasheet



LCDIV-7000-13000-2WAY

7000–13000 MHz GaAs IPD 2-way 0° power divider die

Isolation: 25 dB (typical); Input VSWR: 1.2 (typical); Output VSWR: 1.2 (typical). Die dimensions: 0.9 × 1.3 × 0.1 mm.

Operating frequency: Minimum: 7000; Maximum: 13000; Value: 7000–13000; Unit: MHz

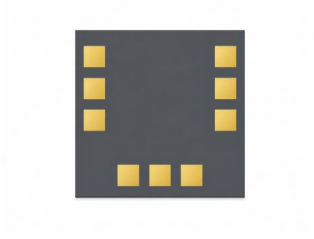
Isolation: Typical: 25; Unit: dB

Input VSWR: Typical: 1.2

Output VSWR: Typical: 1.2

TA = +25 °C

Product details Product datasheet



LCDIV-8000-12000-2WAY

8000–12000 MHz GaAs IPD 2-way 0° power divider die

Isolation: 20 dB (typical); Input VSWR: 1.2 (typical); Output VSWR: 1.1 (typical). Die dimensions: 0.8 × 0.8 × 0.1 mm.

Operating frequency: Minimum: 8000; Maximum: 12000; Value: 8000–12000; Unit: MHz

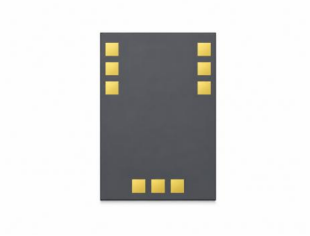
Isolation: Typical: 20; Unit: dB

Input VSWR: Typical: 1.2

Output VSWR: Typical: 1.1

TA = +25 °C

Product details Product datasheet



LCDIV-10000-20000-2WAY

10000–20000 MHz GaAs IPD 2-way 0° power divider die

Isolation: 30 dB (typical); Input VSWR: 1.2 (typical); Output VSWR: 1.2 (typical). Die dimensions: 0.9 × 1.3 × 0.1 mm.

Operating frequency: Minimum: 10000; Maximum: 20000; Value: 10000–20000; Unit: MHz

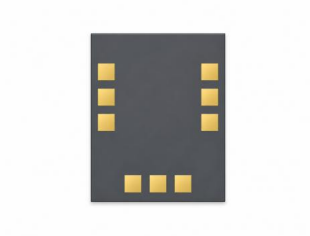
Isolation: Typical: 30; Unit: dB

Input VSWR: Typical: 1.2

Output VSWR: Typical: 1.2

TA = +25 °C

Product details Product datasheet



LCDIV-12000-18000-2WAY

12000–18000 MHz GaAs IPD 2-way 0° power divider die

Isolation: 25 dB (typical); Input VSWR: 1.2 (typical); Output VSWR: 1.1 (typical). Die dimensions: 0.8 × 1 × 0.1 mm.

Operating frequency: Minimum: 12000; Maximum: 18000; Value: 12000–18000; Unit: MHz

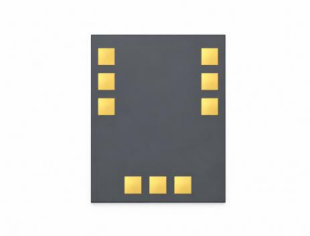
Isolation: Typical: 25; Unit: dB

Input VSWR: Typical: 1.2

Output VSWR: Typical: 1.1

TA = +25 °C

Product details Product datasheet



LCDIV-30000-40000-2WAY

30000–40000 MHz GaAs IPD 2-way 0° power divider die

Isolation: 20 dB (typical); Input VSWR: 1.3 (typical); Output VSWR: 1.3 (typical). Die dimensions: 0.8 × 1 × 0.1 mm.

Operating frequency: Minimum: 30000; Maximum: 40000; Value: 30000–40000; Unit: MHz

Isolation: Typical: 20; Unit: dB

Input VSWR: Typical: 1.3

Output VSWR: Typical: 1.3

TA = +25 °C

Product details Product datasheet



LCATT-DC-30000-A0-S0p35X0p35

DC–30000 MHz 0 dB GaAs IPD fixed attenuator die

Attenuation: 0 dB; Input/output VSWR: 1.2 ; Attenuation flatness: ±0.5 dB. Die dimensions: 0.35 × 0.35 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 30000; Value: DC–30000; Unit: MHz

Attenuation: Value: 0; Unit: dB

Input/output VSWR: Value: 1.2

Attenuation flatness: Value: ±0.5; Unit: dB

TA = +25 °C

Product details Product datasheet



LCATT-DC-30000-A1-S0p35X0p35

DC–30000 MHz 1 dB GaAs IPD fixed attenuator die

Attenuation: 1 dB; Input/output VSWR: 1.3 ; Attenuation flatness: ±0.5 dB. Die dimensions: 0.35 × 0.35 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 30000; Value: DC–30000; Unit: MHz

Attenuation: Value: 1; Unit: dB

Input/output VSWR: Value: 1.3

Attenuation flatness: Value: ±0.5; Unit: dB

TA = +25 °C

Product details Product datasheet



LCATT-DC-30000-A2-S0p35X0p35

DC–30000 MHz 2 dB GaAs IPD fixed attenuator die

Attenuation: 2 dB; Input/output VSWR: 1.3 ; Attenuation flatness: ±0.4 dB. Die dimensions: 0.35 × 0.35 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 30000; Value: DC–30000; Unit: MHz

Attenuation: Value: 2; Unit: dB

Input/output VSWR: Value: 1.3

Attenuation flatness: Value: ±0.4; Unit: dB

TA = +25 °C

Product details Product datasheet



LCATT-DC-30000-A3-S0p35X0p35

DC–30000 MHz 3 dB GaAs IPD fixed attenuator die

Attenuation: 3 dB; Input/output VSWR: 1.3 ; Attenuation flatness: ±0.4 dB. Die dimensions: 0.35 × 0.35 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 30000; Value: DC–30000; Unit: MHz

Attenuation: Value: 3; Unit: dB

Input/output VSWR: Value: 1.3

Attenuation flatness: Value: ±0.4; Unit: dB

TA = +25 °C

Product details Product datasheet



LCATT-DC-30000-A4

DC–30000 MHz 4 dB GaAs IPD fixed attenuator die

Attenuation: 4 dB; Input/output VSWR: 1.3 ; Attenuation flatness: ±0.4 dB. Die dimensions: 0.35 × 0.35 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 30000; Value: DC–30000; Unit: MHz

Attenuation: Value: 4; Unit: dB

Input/output VSWR: Value: 1.3

Attenuation flatness: Value: ±0.4; Unit: dB

TA = +25 °C

Product details Product datasheet



LCATT-DC-30000-A8-S0p35X0p35

DC–30000 MHz 8 dB GaAs IPD fixed attenuator die

Attenuation: 8 dB; Input/output VSWR: 1.3 ; Attenuation flatness: ±0.3 dB. Die dimensions: 0.35 × 0.35 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 30000; Value: DC–30000; Unit: MHz

Attenuation: Value: 8; Unit: dB

Input/output VSWR: Value: 1.3

Attenuation flatness: Value: ±0.3; Unit: dB

TA = +25 °C

Product details Product datasheet



LCATT-DC-30000-A16

DC–30000 MHz 16 dB GaAs IPD fixed attenuator die

Attenuation: 16 dB; Input/output VSWR: 1.3 ; Attenuation flatness: ±0.3 dB. Die dimensions: 0.35 × 0.35 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 30000; Value: DC–30000; Unit: MHz

Attenuation: Value: 16; Unit: dB

Input/output VSWR: Value: 1.3

Attenuation flatness: Value: ±0.3; Unit: dB

TA = +25 °C

Product details Product datasheet



LCATT-DC-30000-A0-S0p5X0p35

DC–30000 MHz 0 dB GaAs IPD fixed attenuator die

Attenuation: 0 dB; Input/output VSWR: 1.3 ; Attenuation flatness: ±0.6 dB. Die dimensions: 0.5 × 0.35 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 30000; Value: DC–30000; Unit: MHz

Attenuation: Value: 0; Unit: dB

Input/output VSWR: Value: 1.3

Attenuation flatness: Value: ±0.6; Unit: dB

TA = +25 °C

Product details Product datasheet



LCATT-DC-30000-A1-S0p5X0p35

DC–30000 MHz 1 dB GaAs IPD fixed attenuator die

Attenuation: 1 dB; Input/output VSWR: 1.4 ; Attenuation flatness: ±0.5 dB. Die dimensions: 0.5 × 0.35 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 30000; Value: DC–30000; Unit: MHz

Attenuation: Value: 1; Unit: dB

Input/output VSWR: Value: 1.4

Attenuation flatness: Value: ±0.5; Unit: dB

TA = +25 °C

Product details Product datasheet



LCATT-DC-30000-A2-S0p5X0p35

DC–30000 MHz 2 dB GaAs IPD fixed attenuator die

Attenuation: 2 dB; Input/output VSWR: 1.35 ; Attenuation flatness: ±0.5 dB. Die dimensions: 0.5 × 0.35 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 30000; Value: DC–30000; Unit: MHz

Attenuation: Value: 2; Unit: dB

Input/output VSWR: Value: 1.35

Attenuation flatness: Value: ±0.5; Unit: dB

TA = +25 °C

Product details Product datasheet



LCATT-DC-30000-A3-S0p5X0p35

DC–30000 MHz 3 dB GaAs IPD fixed attenuator die

Attenuation: 3 dB; Input/output VSWR: 1.35 ; Attenuation flatness: ±0.5 dB. Die dimensions: 0.5 × 0.35 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 30000; Value: DC–30000; Unit: MHz

Attenuation: Value: 3; Unit: dB

Input/output VSWR: Value: 1.35

Attenuation flatness: Value: ±0.5; Unit: dB

TA = +25 °C

Product details Product datasheet



LCATT-DC-30000-A5

DC–30000 MHz 5 dB GaAs IPD fixed attenuator die

Attenuation: 5 dB; Input/output VSWR: 1.3 ; Attenuation flatness: ±0.5 dB. Die dimensions: 0.5 × 0.35 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 30000; Value: DC–30000; Unit: MHz

Attenuation: Value: 5; Unit: dB

Input/output VSWR: Value: 1.3

Attenuation flatness: Value: ±0.5; Unit: dB

TA = +25 °C

Product details Product datasheet



LCATT-DC-30000-A6

DC–30000 MHz 6 dB GaAs IPD fixed attenuator die

Attenuation: 6 dB; Input/output VSWR: 1.35 ; Attenuation flatness: ±0.4 dB. Die dimensions: 0.5 × 0.35 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 30000; Value: DC–30000; Unit: MHz

Attenuation: Value: 6; Unit: dB

Input/output VSWR: Value: 1.35

Attenuation flatness: Value: ±0.4; Unit: dB

TA = +25 °C

Product details Product datasheet



LCATT-DC-30000-A8-S0p5X0p35

DC–30000 MHz 8 dB GaAs IPD fixed attenuator die

Attenuation: 8 dB; Input/output VSWR: 1.3 ; Attenuation flatness: ±0.3 dB. Die dimensions: 0.5 × 0.35 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 30000; Value: DC–30000; Unit: MHz

Attenuation: Value: 8; Unit: dB

Input/output VSWR: Value: 1.3

Attenuation flatness: Value: ±0.3; Unit: dB

TA = +25 °C

Product details Product datasheet



LCATT-DC-30000-A10

DC–30000 MHz 10 dB GaAs IPD fixed attenuator die

Attenuation: 10 dB; Input/output VSWR: 1.3 ; Attenuation flatness: ±0.5 dB. Die dimensions: 0.5 × 0.35 × 0.1 mm.

Operating frequency: Minimum: 0; Maximum: 30000; Value: DC–30000; Unit: MHz

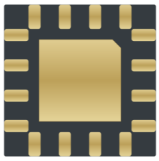
Attenuation: Value: 10; Unit: dB

Input/output VSWR: Value: 1.3

Attenuation flatness: Value: ±0.5; Unit: dB

TA = +25 °C

Product details Product datasheet



LCXOV-DC-40000-C

DC–40000 MHz Packaged RF Crossover — ISO 30 dB (typical)

DC–40000 MHz; Insertion loss -1.4 dB (typical); Isolation 30 dB (typical).

Operating frequency: Symbol: f; Minimum: DC; Maximum: 40000; Value: DC–40000; Unit: MHz

Insertion loss: Typical: -1.4; Unit: dB

Isolation: Typical: 30; Unit: dB

Input/output VSWR: Typical: 1.2

TA = +25 °C

Product details Product datasheet

Mixer and Converter ICs



LCI-MIX-500-2000-D

500–2000 MHz GaAs MMIC Passive Double-Balanced Mixer Die

Conversion loss: 9 dB (typical); LO power: 15 dBm; Operating frequency (IF): 0 MHz (minimum) / 900 MHz (maximum) / DC–900 MHz. Die dimensions: 2.1 × 1.45 × 0.1 mm.

Operating frequency: Minimum: 500; Maximum: 2000; Value: 500–2000 (RF / LO); Unit: MHz

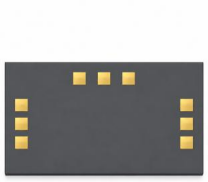
Operating frequency (IF): Minimum: 0; Maximum: 900; Value: DC–900; Unit: MHz

Conversion loss: Typical: 9; Unit: dB

Isolation (LO / RF): Typical: 45; Unit: dB

TA = +25 °C

Product details Product datasheet



LCI-MIX-7000-10000-D

7000–10000 MHz GaAs MMIC Passive Double-Balanced Mixer Die

Conversion loss: 8.5 dB (typical); LO power: 14 dBm; Operating frequency (IF): 1400 MHz (minimum) / 3000 MHz (maximum) / 1400–3000 MHz. Die dimensions: 1.6 × 0.9 × 0.1 mm.

Operating frequency: Minimum: 7000; Maximum: 10000; Value: 7000–10000 (RF); Unit: MHz

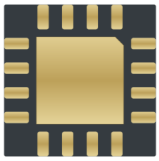
Operating frequency (LO): Minimum: 5000; Maximum: 9000; Value: 5000–9000; Unit: MHz

Operating frequency (IF): Minimum: 1400; Maximum: 3000; Value: 1400–3000; Unit: MHz

Conversion loss: Typical: 8.5; Unit: dB

TA = +25 °C

Product details Product datasheet



LCI-MIX-500-2000-C

500–2000 MHz Packaged Passive Double-Balanced Mixer — LO +14 dBm; IL -9 dB (typical)

500–2000 MHz; IF DC–900 MHz; Conversion loss -9 dB (typical); LOin = 14 dBm.

Operating frequency: Symbol: f; Minimum: 500; Maximum: 2000; Value: 500–2000; Unit: MHz

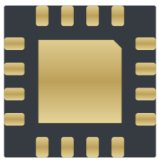
IF frequency range: Minimum: DC; Maximum: 900; Unit: MHz

Conversion loss: Symbol: IL; Typical: -9; Unit: dB

LO–RF isolation: Symbol: ISOL-R; Typical: -40; Unit: dB

TA = +25 °C; LOin = 14 dBm; RFin = -10 dBm

Product details Product datasheet



LCI-MIX-7000-10000-C

7000–10000 MHz Packaged Passive Double-Balanced Mixer — LO +14 dBm; IL -9 dB (typical)

7000–10000 MHz; IF 1400–3400 MHz; Conversion loss -9 dB (typical); LOin = 14 dBm.

Operating frequency: Symbol: f; Minimum: 7000; Maximum: 10000; Value: 7000–10000; Unit: MHz

IF frequency range: Minimum: 1400; Maximum: 3400; Unit: MHz

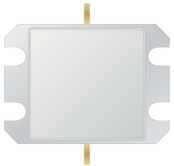
Conversion loss: Symbol: IL; Typical: -9; Unit: dB

LO–RF isolation: Symbol: ISOL-R; Typical: -40; Unit: dB

TA = +25 °C; LOin = 14 dBm; RFin = -10 dBm

Product details Product datasheet

RF Power Transistors



LCT-5700-7100-PS51T

5700–7100 MHz GaN Internally Matched Power Transistor — PSAT 51 dBm (typical)

5700–7100 MHz; PSAT 51 dBm (typical); Power gain 11 dB (typical); PAE 45 % (typical).

Operating frequency: Symbol: f; Minimum: 5700; Maximum: 7100; Value: 5700–7100; Unit: MHz

Saturated output power: Minimum: 50.5; Typical: 51; Unit: dBm

Power gain: Minimum: 10.5; Typical: 11; Unit: dB

Power-added efficiency: Minimum: 40; Typical: 45; Unit: %

TA = +25 °C; VDS = 28 V; VGS ∈ [-3.2, -2.4] V; Pin = 40 dBm; D = 10%; PW = 100 µs

Product details Product datasheet



LCT-2700-3500-PS56p5T

2700–3500 MHz GaN Internally Matched Power Transistor — PSAT 56.5 dBm (typical)

2700–3500 MHz; PSAT 56.5 dBm (typical); Power gain 13.5 dB (typical); PAE 55 % (typical).

Operating frequency: Symbol: f; Minimum: 2700; Maximum: 3500; Value: 2700–3500; Unit: MHz

Saturated output power: Minimum: 56; Typical: 56.5; Unit: dBm

Power gain: Minimum: 13; Typical: 13.5; Unit: dB

Power-added efficiency: Minimum: 50; Typical: 55; Unit: %

TA = +25 °C; VDS = 44 V; VGS ∈ [-4, -2] V; IDS = (0.2–0.5) IDSS; PW = 300 µs; D = 10%

Product details Product datasheet



LCT-5300-5900-PS56p5T

5300–5900 MHz GaN Internally Matched Power Transistor — PSAT 56.5 dBm (typical)

5300–5900 MHz; PSAT 56.5 dBm (typical); Power gain 12.5 dB (typical); PAE 45 % (typical).

Operating frequency: Symbol: f; Minimum: 5300; Maximum: 5900; Value: 5300–5900; Unit: MHz

Saturated output power: Minimum: 56; Typical: 56.5; Unit: dBm

Power gain: Minimum: 12; Typical: 12.5; Unit: dB

Power-added efficiency: Minimum: 40; Typical: 45; Unit: %

TA = +25 °C; VDS = 40 V; VGS ∈ [-4, -2] V; IDS = (0.2–0.5) IDSS; PW = 10 µs; D = 1%

Product details Product datasheet



LCT-2700-3900-PS48p5T

2700–3900 MHz GaN Internally Matched Power Transistor — PSAT 48.5 dBm (typical)

2700–3900 MHz; PSAT 48.5 dBm (typical); Power gain 12.5 dB (typical); PAE 50 % (typical).

Operating frequency: Symbol: f; Minimum: 2700; Maximum: 3900; Value: 2700–3900; Unit: MHz

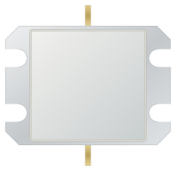
Saturated output power: Minimum: 48; Typical: 48.5; Unit: dBm

Power gain: Minimum: 12; Typical: 12.5; Unit: dB

Power-added efficiency: Minimum: 45; Typical: 50; Unit: %

TA = +25 °C; VDS = 24–28 V; VGS ∈ [-4, -2] V; IDS = (0.2–0.5) IDSS

Product details Product datasheet



LCT-2700-3500-PS53p5T

2700–3500 MHz GaN Internally Matched Power Transistor — PSAT 53.5 dBm (typical)

2700–3500 MHz; PSAT 53.5 dBm (typical); Power gain 13.5 dB (typical); PAE 65 % (typical).

Operating frequency: Symbol: f; Minimum: 2700; Maximum: 3500; Value: 2700–3500; Unit: MHz

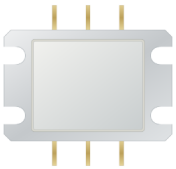
Saturated output power: Minimum: 53; Typical: 53.5; Unit: dBm

Power gain: Minimum: 13; Typical: 13.5; Unit: dB

Power-added efficiency: Minimum: 60; Typical: 65; Unit: %

TA = +25 °C; VDS = 28 V; VGS ∈ [-4, -2] V; Pin = 40 dBm; D = 10%; PW = 100 µs

Product details Product datasheet



LCT-2300-3900-PS50T

2300–3900 MHz GaN Internally Matched Power Transistor — PSAT 50 dBm (typical)

2300–3900 MHz; PSAT 50 dBm (typical); Power gain 12 dB (typical); PAE 50 % (typical).

Operating frequency: Symbol: f; Minimum: 2300; Maximum: 3900; Value: 2300–3900; Unit: MHz

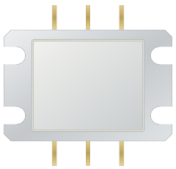
Saturated output power: Minimum: 49; Typical: 50; Unit: dBm

Power gain: Minimum: 11; Typical: 12; Unit: dB

Power-added efficiency: Minimum: 45; Typical: 50; Unit: %

TA = +25 °C; VGS ∈ [-4, -2] V; VDS = 24–28 V; IDS = (0.2–0.5) IDSS

Product details Product datasheet



LCT-2600-3700-PS49T

2600–3700 MHz GaN Internally Matched Power Transistor — PSAT 49 dBm (typical)

2600–3700 MHz; PSAT 49 dBm (typical); Power gain 13 dB (typical); PAE 50 % (typical).

Operating frequency: Symbol: f; Minimum: 2600; Maximum: 3700; Value: 2600–3700; Unit: MHz

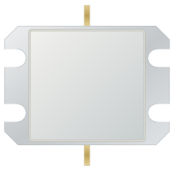
Saturated output power: Minimum: 48; Typical: 49; Unit: dBm

Power gain: Minimum: 12; Typical: 13; Unit: dB

Power-added efficiency: Minimum: 45; Typical: 50; Unit: %

TA = +25 °C; VDS = 28 V; VGS ∈ [-3.2, -2.2] V; Pin = 36 dBm; CW

Product details Product datasheet



LCT-8500-9600-PS51T

8500–9600 MHz GaN Internally Matched Power Transistor — PSAT 51 dBm (typical)

8500–9600 MHz; PSAT 51 dBm (typical); Power gain 9 dB (typical); PAE 38 % (typical).

Operating frequency: Symbol: f; Minimum: 8500; Maximum: 9600; Value: 8500–9600; Unit: MHz

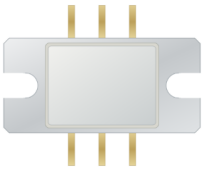
Saturated output power: Minimum: 50; Typical: 51; Unit: dBm

Power gain: Minimum: 8; Typical: 9; Unit: dB

Power-added efficiency: Typical: 38; Unit: %

Vd = +28 V; Vg = -3 V; PW = 100 µs; D = 10%; Pin = 42 dBm

Product details Product datasheet



LCT-2000-6000-PO45p51T

2000–6000 MHz GaN Internally Matched Power Transistor — Pout 45.51 dBm @ 6000 MHz (typical)

2000–6000 MHz; Reference output power 45.51 dBm (typical); Power gain 19.51 dB (typical); Drain efficiency 39.82 % (typical) @ 6000 MHz.

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 6000; Value: 2000–6000; Unit: MHz

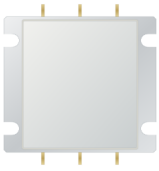
Reference output power: Typical: 45.51; Unit: dBm; Notes: f = 6000 MHz

Power gain: Typical: 19.51; Unit: dB; Notes: f = 6000 MHz

Drain efficiency: Symbol: ηD; Typical: 39.82; Unit: %; Notes: f = 6000 MHz

TA = +25 °C; VDS = 28 V; IDQ = 1.3 A; CW; f = 6000 MHz; Pin = 26 dBm

Product details Product datasheet



LCT-700-6200-PS49T

700–6200 MHz GaN Internally Matched Power Transistor — PSAT 49 dBm @ 6000 MHz (typical)

700–6200 MHz; Saturated output power 49 dBm (typical); Power gain 7 dB (typical); Drain efficiency 35 % (typical) @ 6000 MHz.

Operating frequency: Symbol: f; Minimum: 700; Maximum: 6200; Value: 700–6200; Unit: MHz

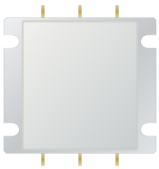
Saturated output power: Symbol: Psat; Typical: 49; Unit: dBm; Notes: f = 6000 MHz

Power gain: Typical: 7; Unit: dB; Notes: f = 6000 MHz

Drain efficiency: Symbol: ηD; Typical: 35; Unit: %; Notes: f = 6000 MHz

TA = +25 °C; VDS = 28 V; IDQ = 1 A; CW; f = 6000 MHz

Product details Product datasheet



LCT-2000-6200-PO50p1T

2000–6200 MHz GaN Internally Matched Power Transistor — Pout 50.1 dBm @ 6000 MHz (typical)

2000–6200 MHz; Reference output power 50.1 dBm (typical); Power gain 8.6 dB (typical); Drain efficiency 52.4 % (typical) @ 6000 MHz.

Operating frequency: Symbol: f; Minimum: 2000; Maximum: 6200; Value: 2000–6200; Unit: MHz

Reference output power: Typical: 50.1; Unit: dBm; Notes: f = 6000 MHz

Power gain: Typical: 8.6; Unit: dB; Notes: f = 6000 MHz

Drain efficiency: Symbol: ηD; Typical: 52.4; Unit: %; Notes: f = 6000 MHz

TA = +25 °C; VDS = 28 V; IDQ = 0.5 A; CW; f = 6000 MHz; Pin = 41.5 dBm

Product details Product datasheet

Document notice

Specifications are subject to revision. Before design release, confirm the current document revision and product-specific requirements with LCRF. The approved quotation and order documentation define the supplied configuration.